



电子元器件系列 (中国.厦门)

www.rf-china.com F-Micom co.,Ltd

厦门电话:0592-5713956

EMail:sales@rf-china.com

Tel:0086-592-5713956 Fax:0592-5201617

Microwave Diodes

Schottky

Varactor

PIN

Step Recovery

Planar Tunnel

MOS / MIS Capacitors

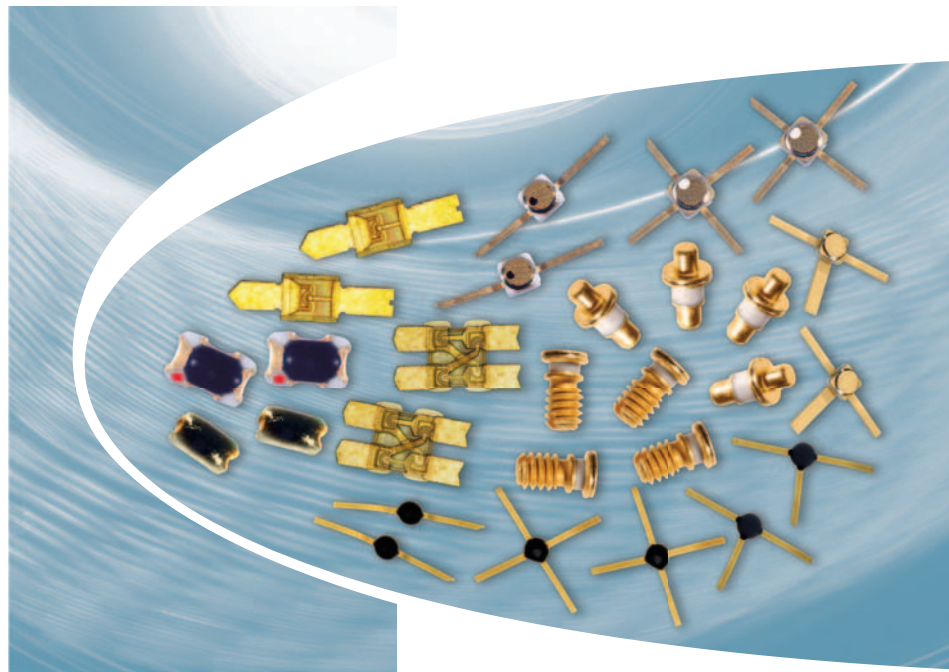


Table of Contents

Silicon Schottky Diodes	4
GaAs Schottky Diodes	18
GaAs Abrupt Varactor Diodes	19
GaAs Hyperabrupt Varactor Diodes	20
Silicon Abrupt Varactor Diodes	21
Silicon PIN Diodes	26
Silicon NIP Diodes	33
Silicon Step Recovery Diodes	35
Planar Back (Tunnel) Diodes	38
MIS / MOS Capacitors	40
Sampling Phase Detectors	43
Outline Drawings	44
Index	54

Silicon Schottky Diodes

Schottky Diodes for Detector Applications

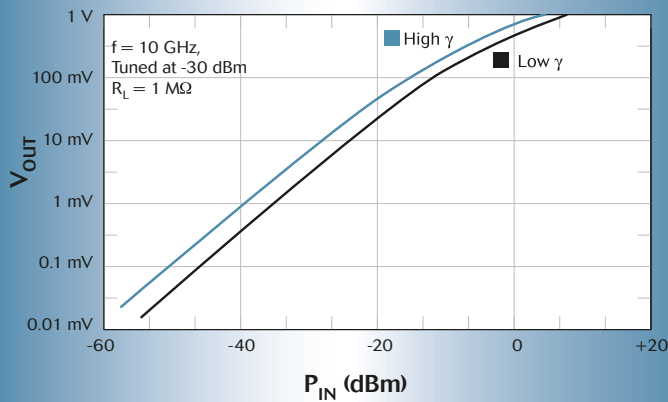
These diodes are fabricated on P-Type substrates for low 1/f noise and are optimized for either zero-bias (MSS20,XXX series) or biased (MSS39,XXX) operation. Zero-biased devices are processed to yield two distinct video impedance classes, one 1,500 Ohms typical and the other 4,000 Ohms typical. Applications requiring maximum stability and sensitivity will favor the higher video impedance. Biased detector operation offers the designer improved temperature stability and video impedance flexibility via bias current selection.

Zero Bias, $V_{BR} = 0.8 \text{ V min.}$

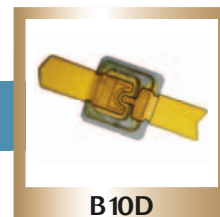
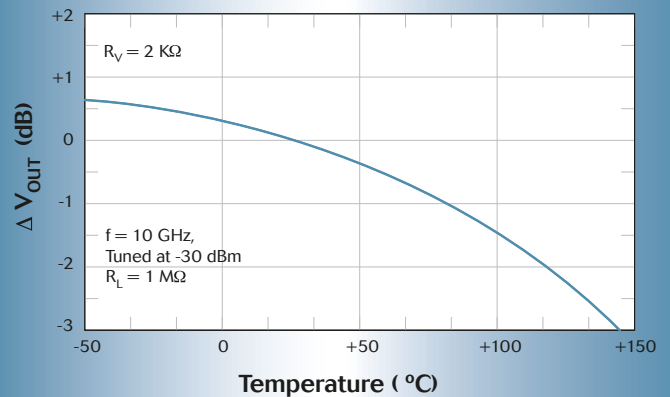
Chip and Beam Lead

Model	C_j		γ TYP mV / mW	R_v		T_{ss} TYP dBm	$F_{req.}$ TYP GHz	Package
	TYP pF	MAX pF		TYP Ω	MAX Ω			
MSS20,046-C15	0.08	0.10	5,000	1,500	2,000	-58	18	C15p
MSS20,047-C15	0.08	0.10	8,000	4,000	6,000	-59	18	C15p
MSS20,050-C15	0.12	0.15	5,000	1,500	2,000	-58	12	C15p
MSS20,051-C15	0.12	0.15	8,000	4,000	6,000	-59	12	C15p
MSS20,054-C15	0.18	0.20	5,000	1,500	2,000	-58	8	C15p
MSS20,055-C15	0.18	0.20	8,000	4,000	6,000	-59	8	C15p
MSS20,140-B10D	0.06	0.08	5,000	1,500	2,000	-58	40	B10D
MSS20,141-B10D	0.06	0.08	8,000	4,000	6,000	-59	40	B10D
MSS20,142-B10D	0.08	0.10	5,000	1,500	2,000	-58	26	B10D
MSS20,143-B10D	0.08	0.10	8,000	4,000	6,000	-59	26	B10D
MSS20,145-B10D	0.10	0.12	5,000	1,500	2,000	-58	18	B10D
MSS20,146-B10D	0.10	0.12	8,000	4,000	6,000	-59	18	B10D
Test Conditions	$V_R = 0.5 \text{ V}$ $F = 1 \text{ MHz}$		$F = 10 \text{ GHz}$ $P_{IN} = -30 \text{ dBm}$ $R_L = 1 \text{ M}\Omega$ Video BW = 500 KHz NF = 3 dB					

Detected Output vs. RF Input Power



Detector Output vs. Temperature



Silicon Schottky Diodes

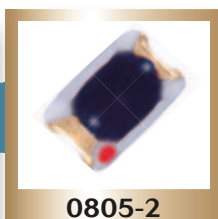
Zero Bias, $V_{BR} = 0.8 \text{ V min.}$

Packaged

Model	C_T		γ TYP mV / mW	R_V		T_{SS} TYP dBm	C_P TYP pF	L_P TYP nH	$F_{req.}$ MAX GHz	Package
	TYP pF	MAX pF		TYP Ω	MAX Ω					
MSS20,140-0402	0.12	0.15	5,000	1,500	2,000	-58	0.05	0.25	26	0402
MSS20,141-0402	0.12	0.15	8,000	4,000	6,000	-59	0.05	0.25	26	0402
MSS20,142-0402	0.15	0.18	5,000	1,500	2,000	-58	0.05	0.25	20	0402
MSS20,143-0402	0.15	0.18	8,000	4,000	6,000	-59	0.05	0.25	20	0402
MSS20,145-0402	0.18	0.20	5,000	1,500	2,000	-58	0.05	0.25	18	0402
MSS20,146-0402	0.18	0.20	8,000	4,000	6,000	-59	0.05	0.25	18	0402
MSS20,046-H27	0.20	0.25	5,000	1,500	2,000	-58	0.12	0.4	18	H27
MSS20,046-E25	0.15	0.20	5,000	1,500	2,000	-58	0.07	0.4	18	E25
MSS20,046-T86	0.26	0.31	5,000	1,500	2,000	-58	0.18	1.0	12	T86p
MSS20,046-0805-2	0.14	0.20	5,000	1,500	2,000	-58	0.06	0.4	20	0805-2
MSS20,047-H27	0.20	0.25	8,000	4,000	6,000	-59	0.12	0.4	18	H27
MSS20,047-E25	0.15	0.20	8,000	4,000	6,000	-59	0.07	0.4	18	E25
MSS20,047-T86	0.26	0.31	8,000	4,000	6,000	-59	0.18	1.0	12	T86p
MSS20,047-0805-2	0.14	0.20	8,000	4,000	6,000	-59	0.06	0.4	20	0805-2
MSS20,050-H27	0.24	0.30	5,000	1,500	2,000	-58	0.12	0.4	12	H27
MSS20,050-E25	0.20	0.25	5,000	1,500	2,000	-58	0.07	0.4	12	E25
MSS20,050-T86	0.30	0.36	5,000	1,500	2,000	-58	0.18	1.0	12	T86p
MSS20,050-0805-2	0.18	0.25	5,000	1,500	2,000	-58	0.06	0.4	18	0805-2
MSS20,051-H27	0.24	0.30	8,000	4,000	6,000	-59	0.12	0.4	12	H27
MSS20,051-E25	0.20	0.25	8,000	4,000	6,000	-59	0.07	0.4	12	E25
MSS20,051-T86	0.30	0.36	8,000	4,000	6,000	-59	0.18	1.0	12	T86p
MSS20,051-0805-2	0.18	0.25	8,000	4,000	6,000	-59	0.06	0.4	18	0805-2
MSS20,054-H27	0.30	0.35	5,000	1,500	2,000	-58	0.12	0.4	8	H27
MSS20,054-E25	0.25	0.30	5,000	1,500	2,000	-58	0.07	0.4	8	E25
MSS20,054-T86	0.36	0.41	5,000	1,500	2,000	-58	0.18	1.0	8	T86p
MSS20,054-0805-2	0.24	0.30	5,000	1,500	2,000	-58	0.06	0.4	12	0805-2
MSS20,055-H27	0.30	0.35	8,000	4,000	6,000	-59	0.12	0.4	8	H27
MSS20,055-E25	0.25	0.30	8,000	4,000	6,000	-59	0.07	0.4	8	E25
MSS20,055-T86	0.36	0.41	8,000	4,000	6,000	-59	0.18	1.0	8	T86p
MSS20,055-0805-2	0.24	0.30	8,000	4,000	6,000	-59	0.06	0.4	12	0805-2
Test Conditions	$V_R = 0.5 \text{ V}$ $F = 1 \text{ MHz}$		$F = 10 \text{ GHz}$ $P_{IN} = -30 \text{ dBm}$ $R_L = 1 \text{ M}\Omega$ Video BW = 500 KHz NF = 3 dB							



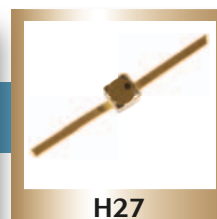
0402



0805-2



E25



H27



T86p

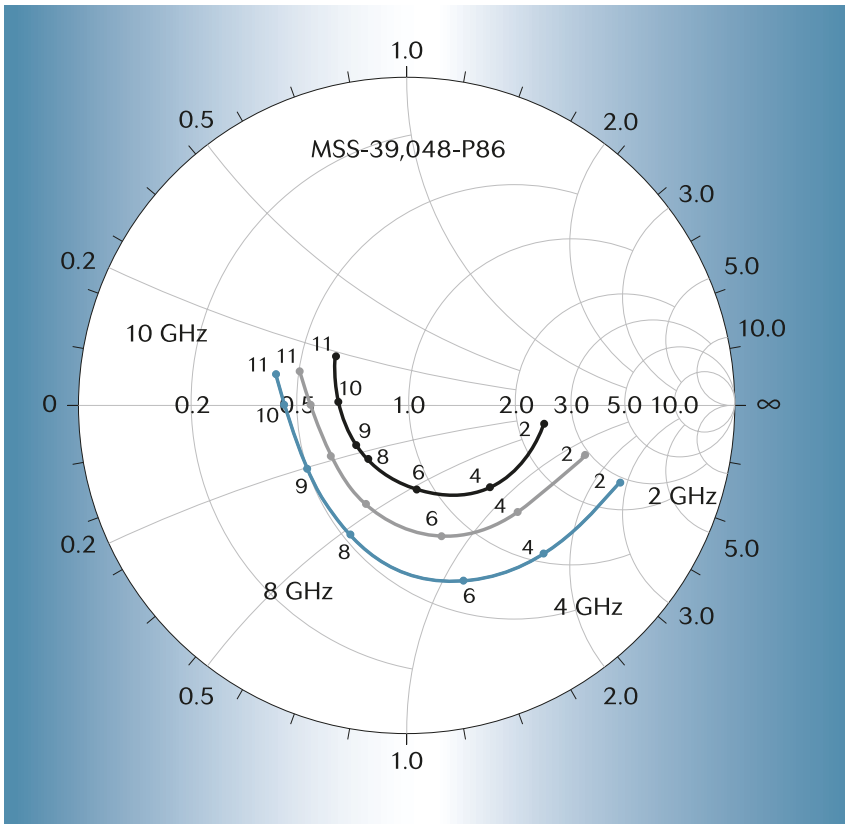
Silicon Schottky Diodes

Schottky Diodes for Detector Applications

Biased P-Type, $V_F = 350 \sim 450 \text{ mV}$

Chip and Beam Lead							
Model	V_{BR} MIN V	C_J		γ TYP mV / mW	T_{SS} TYP dBm	$F_{req.}$ TYP GHz	Package
		TYP pF	MAX pF				
MSS39,045-C15	5.0	0.08	0.10	5,000	-58	18	C15P
MSS39,048-C15	5.0	0.12	0.15	5,000	-58	12	C15P
MSS39,144-B10B	3.5	0.06	0.08	5,000	-58	40	B10B
MSS39,146-B10B	3.5	0.08	0.10	5,000	-58	26	B10B
MSS39,148-B10B	3.5	0.10	0.12	5,000	-58	20	B10B
MSS39,152-B10B	3.5	0.15	0.18	5,000	-58	18	B10B
Test Conditions	$I_R = 10 \mu A$	$V_R = 0 \text{ V}$ $F = 1 \text{ MHz}$		$F = 10 \text{ GHz}$ DC BIAS = $20 \mu A$ Video BW = 2 MHz $R_L = 100 \text{ k}\Omega$			

Smith Chart - 50 Ω Reference



- $I_{RECT} = 1 \text{ mA}, +1/2 \text{ dBm}$
- $I_{RECT} = 2 \text{ mA}, +3 \text{ dBm}$
- $I_{RECT} = 4 \text{ mA}, +6 \text{ dBm}$



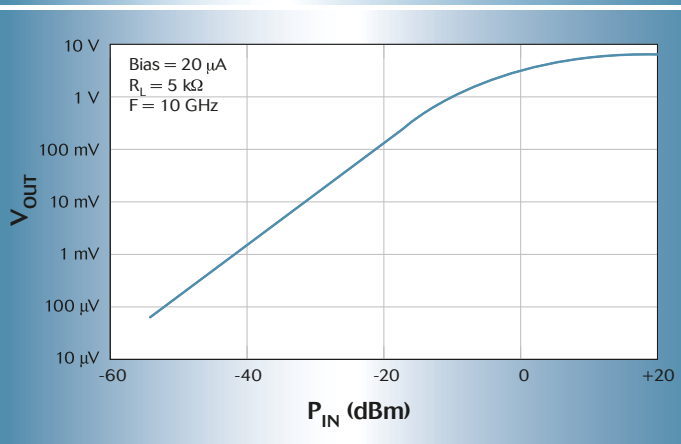
Silicon Schottky Diodes

Biased P-Type, $V_F = 350 \sim 450$ mV

Packaged

Model	C_T		γ TYP mV / mW	T_{ss} TYP dBm	C_P TYP pF	L_P TYP nH	Package
	TYP pF	MAX pF					
MSS39,045-P55	0.21	0.26	5,000	-58	0.13	0.35	P55p
MSS39,045-P86	0.23	0.23	5,000	-58	0.15	1.0	P86p
MSS39,048-P55	0.25	0.31	5,000	-58	0.13	0.35	P55p
MSS39,048-P86	0.27	0.33	5,000	-58	0.15	1.0	P86p
MSS39,144-H27	0.18	0.24	5,000	-58	0.12	0.4	H27
MSS39,144-0402	0.11	0.16	5,000	-58	0.05	0.25	0402
MSS39,144-0805-2	0.12	0.17	5,000	-58	0.06	0.4	0805-2
MSS39,146-H27	0.20	0.25	5,000	-58	0.12	0.4	H27
MSS39,146-0402	0.13	0.18	5,000	-58	0.05	0.25	0402
MSS39,146-0805-2	0.14	0.20	5,000	-58	0.06	0.4	0805-2
MSS39,148-E25	0.17	0.22	5,000	-58	0.07	0.4	E25
MSS39,148-H20	0.28	0.33	5,000	-58	0.18	0.5	H20
MSS39,148-0402	0.15	0.20	5,000	-58	0.05	0.25	0402
MSS39,148-0805-2	0.16	0.22	5,000	-58	0.06	0.4	0805-2
MSS39,152-E25	0.22	0.28	5,000	-58	0.07	0.4	E25
MSS39,152-H20	0.33	0.39	5,000	-58	0.18	0.5	H20
MSS39,152-0402	0.20	0.25	5,000	-58	0.05	0.25	0402
MSS39,152-0805-2	0.21	0.27	5,000	-58	0.06	0.4	0805-2
Test Conditions	$V_R = 0$ V $F = 1$ MHz		$F = 10$ GHz DC BIAS = $20 \mu A$ Video BW = 2 MHz $R_L = 100 \text{ k}\Omega$				

Detector Output Curve



0402



0805-2



E25



H20



H27



P55p

Silicon Schottky Diodes

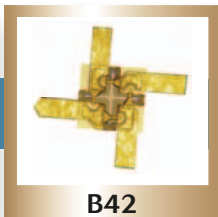
Schottky Diodes for Mixer Applications

Industry leading, state-of-the-art performance in five barrier heights and ten configurations featuring Aeroflex / Metelics dual passivation and tri-metalization for ultra-reliability. Designs supporting doubler, limiter, mixer and sampler applications up to 40+ GHz. Chip, beam lead and packaged diodes for commercial, aerospace and defense environments. Parametric selection / matching as well as screening per MIL-PRF-19500 and MIL-PRF-38534 is available.

Low Barrier, $V_F = 230 \sim 350 \text{ mV}$, $V_{BR} = 2 \text{ V min.}$

Chip and Beam Lead

Model	Configuration	C_j		R_D MAX Ω	R_S TYP Ω	F_{co} TYP GHz	Package
		TYP pF	MAX pF				
MSS30,046-C15	Single Junction	0.10	0.12	18	10	160	C15
MSS30,050-C15	Single Junction	0.15	0.18	15	6	175	C15
MSS30,142-B10B	Single Junction	0.07	0.10	22	13	175	B10B
MSS30,148-B10B	Single Junction	0.12	0.15	15	7	190	B10B
MSS30,154-B10B	Single Junction	0.22	0.25	12	3	240	B10B
MSS30,242-B20	Series Tee	0.07	0.10	22	13	175	B20
MSS30,248-B20	Series Tee	0.12	0.15	15	7	190	B20
MSS30,254-B20	Series Tee	0.22	0.25	12	3	240	B20
MSS30,346-B21	Anti-Parallel Pair	0.27	0.30	16	11	55	B21
MSS30,442-B42	Ring Quad	0.07	0.10	22	13	175	B42
MSS30,448-B42	Ring Quad	0.12	0.15	15	7	190	B42
MSS30,454-B40	Ring Quad	0.22	0.25	12	3	240	B40
MSS30,B46-B45	Bridge Quad	0.10	0.125	25	15	80	B45
MSS30,B53-B45	Bridge Quad	0.20	0.25	15	5	80	B45
MSS30,CR46-B49	Crossover Ring Quad	0.09	0.125	22	10	118	B49
MSS30,CR53-B49	Crossover Ring Quad	0.15	0.250	15	5	106	B49
MSS30,PCB46-B48	Coplanar Bridge Quad	0.08	0.12	20	7	166	B48
MSS30,PCR46-B47	Coplanar Ring Quad	0.07	0.13	22	10	152	B47
MSS30,PCR53-B47	Coplanar Ring Quad	0.15	0.25	15	5	106	B47
Test Conditions		$V_R = 0 \text{ V}$ $F = 1 \text{ MHz}$		$I_F = 5 \text{ mA}$			

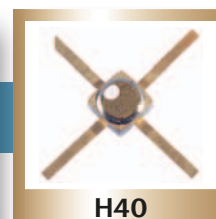
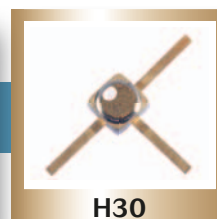
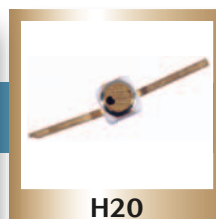
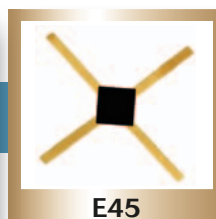


Silicon Schottky Diodes

Low Barrier, $V_F = 230 \sim 350 \text{ mV}$, $V_{BR} = 2 \text{ V min.}$

Packaged

Model	Configuration	C_T		R_D MAX Ω	C_P TYP pF	L_P TYP nH	Package
		TYP pF	MAX pF				
MSS30,046-P55	Single Junction	0.23	0.30	18	0.13	0.35	P55
MSS30,046-P86	Single Junction	0.25	0.33	18	0.15	1.0	P86
MSS30,050-P55	Single Junction	0.28	0.35	15	0.13	0.35	P55
MSS30,050-P86	Single Junction	0.30	0.38	15	0.15	1.0	P86
MSS30,142-E25	Single Junction	0.14	0.26	22	0.07	0.4	E25
MSS30,142-H20	Single Junction	0.25	0.31	22	0.18	0.5	H20
MSS30,148-E25	Single Junction	0.21	0.31	15	0.07	0.4	E25
MSS30,148-H20	Single Junction	0.30	0.36	15	0.18	0.5	H20
MSS30,154-E25	Single Junction	0.30	0.41	12	0.07	0.4	E25
MSS30,154-H20	Single Junction	0.40	0.46	12	0.18	0.5	H20
MSS30,242-E35	Series Tee	0.15	0.21	22	0.07	0.4	E35
MSS30,242-H30	Series Tee	0.25	0.31	22	0.18	0.5	H30
MSS30,248-E35	Series Tee	0.20	0.25	15	0.07	0.4	E35
MSS30,248-H30	Series Tee	0.30	0.36	15	0.18	0.5	H30
MSS30,254-E35	Series Tee	0.30	0.35	12	0.07	0.4	E35
MSS30,254-H30	Series Tee	0.40	0.46	12	0.18	0.5	H30
MSS30,346-E25	Anti-Parallel Pair	0.35	0.40	16	0.07	0.4	E25
MSS30,346-H20	Anti-Parallel Pair	0.45	0.50	16	0.18	0.5	H20
MSS30,442-E45	Ring Quad	0.15	0.21	22	0.07	0.4	E45
MSS30,442-H40	Ring Quad	0.25	0.33	22	0.18	0.5	H40
MSS30,448-E45	Ring Quad	0.20	0.26	15	0.07	0.4	E45
MSS30,448-H40	Ring Quad	0.30	0.35	15	0.18	0.5	H40
MSS30,454-E45	Ring Quad	0.30	0.35	12	0.07	0.4	E45
MSS30,454-H40	Ring Quad	0.40	0.46	12	0.18	0.5	H40
MSS30,B46-E45	Bridge Quad	0.17	0.25	25	0.07	0.4	E45
MSS30,B46-H40	Bridge Quad	0.28	0.35	25	0.18	0.5	H40
MSS30,B53-E45	Bridge Quad	0.27	0.35	15	0.07	0.4	E45
MSS30,B53-H40	Bridge Quad	0.38	0.46	15	0.18	0.5	H40
MSS30,CR46-E45	Crossover Ring Quad	0.16	0.22	22	0.07	0.4	E45
MSS30,CR46-H40	Crossover Ring Quad	0.27	0.33	22	0.18	0.5	H40
MSS30,CR53-E45	Crossover Ring Quad	0.22	0.35	15	0.07	0.4	E45
MSS30,CR53-H40	Crossover Ring Quad	0.33	0.45	15	0.18	0.5	H40
Test Conditions		$V_R = 0 \text{ V}$ $F = 1 \text{ MHz}$		$I_F = 5 \text{ mA}$			



Silicon Schottky Diodes

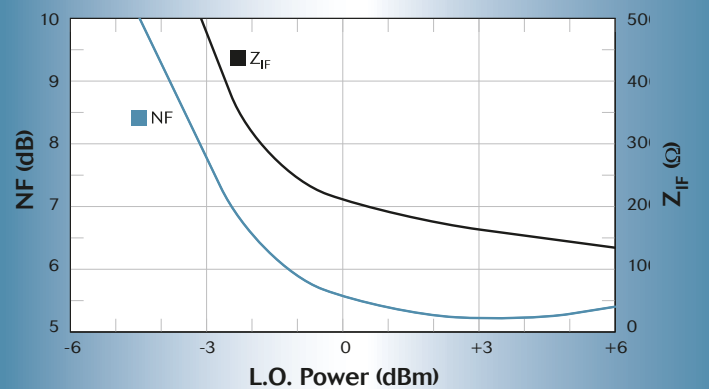
Schottky Diodes for Mixer Applications

Medium Barrier, $V_F = 350 \sim 450$ mV, $V_{BR} = 3$ V min.

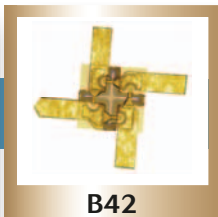
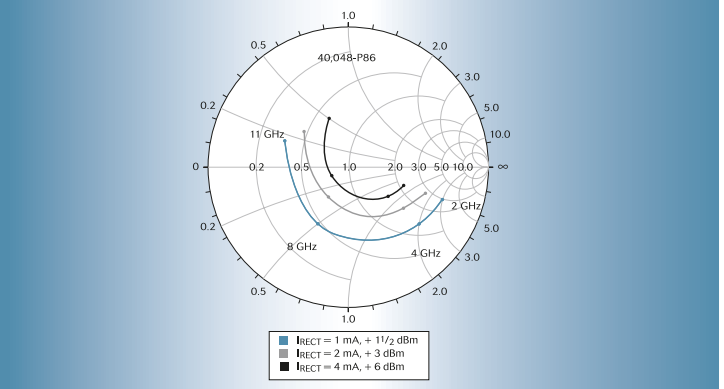
Chip and Beam Lead

Model	Configuration	C_j		R_D MAX Ω	R_S TYP Ω	F_{CO} TYP GHz	Package
		TYP pF	MAX pF				
MSS40,045-C15	Single Junction	0.09	0.12	15	7	253	C15
MSS40,048-C15	Single Junction	0.12	0.15	15	7	190	C15
MSS40,141-B10B	Single Junction	0.06	0.10	22	10	265	B10B
MSS40,148-B10B	Single Junction	0.12	0.15	17	7	190	B10B
MSS40,155-B10B	Single Junction	0.25	0.30	13	5	127	B10B
MSS40,244-B20	Series Tee	0.08	0.12	22	19	105	B20
MSS40,248-B20	Series Tee	0.12	0.15	17	10	133	B20
MSS40,255-B20	Series Tee	0.25	0.30	15	5	127	B20
MSS40,448-B42	Ring Quad	0.12	0.15	17	7	190	B42
MSS40,455-B40	Ring Quad	0.25	0.30	17	5	127	B40
MSS40,B46-B45	Bridge Quad	0.10	0.13	25	15	106	B45
MSS40,B53-B45	Bridge Quad	0.20	0.25	15	5	160	B45
MSS40,CR46-B49	Crossover Ring Quad	0.09	0.125	22	10	177	B49
MSS40,CR53-B49	Crossover Ring Quad	0.15	0.25	15	5	212	B49
MSS40,PCR46-B47	Coplanar Ring Quad	0.07	0.13	22	10	227	B47
MSS40,PCR53-B47	Coplanar Ring Quad	0.15	0.25	15	5	212	B47
MSS40,PCB46-B48	Coplanar Bridge Quad	0.08	0.12	20	7	190	B48
Test Conditions		$V_R = 0$ V $F = 1$ MHz		$I_F = 5$ mA			

NF & Z_{IF} vs. LO Power



Smith Chart - 50 Ω Reference

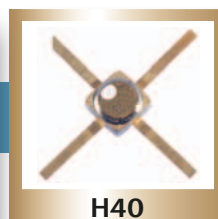
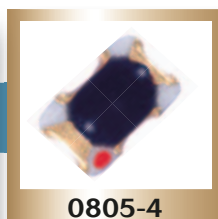


Silicon Schottky Diodes

Medium Barrier, $V_F = 350 \sim 450$ mV, $V_{BR} = 3$ V min.

Packaged

Model	Configuration	C_T		R_D MAX Ω	C_P TYP pF	L_P TYP nH	Package
		TYP pF	MAX pF				
MSS40,045-P55	Single Junction	0.22	0.28	15	0.13	0.35	P55
MSS40,045-P86	Single Junction	0.24	0.30	15	0.15	1.0	P86
MSS40,048-P55	Single Junction	0.25	0.30	15	0.13	0.35	P55
MSS40,048-P86	Single Junction	0.27	0.33	15	0.15	1.0	P86
MSS40,141-E25	Single Junction	0.13	0.22	18	0.07	0.4	E25
MSS40,141-H20	Single Junction	0.24	0.30	18	0.18	0.5	H20
MSS40,141-0402	Single Junction	0.11	0.18	18	0.05	0.25	0402
MSS40,148-E25	Single Junction	0.19	0.28	15	0.07	0.4	E25
MSS40,148-H20	Single Junction	0.30	0.36	15	0.18	0.5	H20
MSS40,148-0402	Single Junction	0.17	0.24	15	0.05	0.25	0402
MSS40,155-E25	Single Junction	0.32	0.41	14	0.07	0.4	E25
MSS40,155-H20	Single Junction	0.43	0.51	14	0.18	0.5	H20
MSS40,155-0402	Single Junction	0.30	0.38	14	0.05	0.25	0402
MSS40,244-E35	Series Tee	0.15	0.24	28	0.07	0.4	E35
MSS40,244-0805-4	Series Tee	0.29	0.36	28	0.06	0.4	0805-4
MSS40,248-E35	Series Tee	0.19	0.28	18	0.07	0.4	E35
MSS40,248-0805-4	Series Tee	0.18	0.25	18	0.06	0.4	0805-4
MSS40,255-E35	Series Tee	0.32	0.41	14	0.07	0.4	E35
MSS40,255-0805-4	Series Tee	0.17	0.40	14	0.06	0.4	0805-4
MSS40,448-E45	Ring Quad	0.19	0.25	15	0.07	0.4	E45
MSS40,448-H40	Ring Quad	0.30	0.36	15	0.18	0.5	H40
MSS40,455-E45	Ring Quad	0.32	0.40	14	0.07	0.4	E45
MSS40,455-H40	Ring Quad	0.42	0.52	14	0.18	0.5	H40
MSS40,B46-E45	Bridge Quad	0.17	0.24	25	0.07	0.4	E45
MSS40,B53-E45	Bridge Quad	0.27	0.36	15	0.07	0.4	E45
MSS40,CR46-E45	Crossover Ring Quad	0.16	0.23	15	0.07	0.4	E45
MSS40,CR46-H40	Crossover Ring Quad	0.27	0.35	15	0.18	0.5	H40
MSS40,CR53-E45	Crossover Ring Quad	0.22	0.35	15	0.07	0.4	E45
MSS40,CR53-H40	Crossover Ring Quad	0.33	0.46	15	0.18	0.5	H40
Test Conditions		$V_R = 0$ V $F = 1$ MHz		$I_F = 5$ mA			



Silicon Schottky Diodes

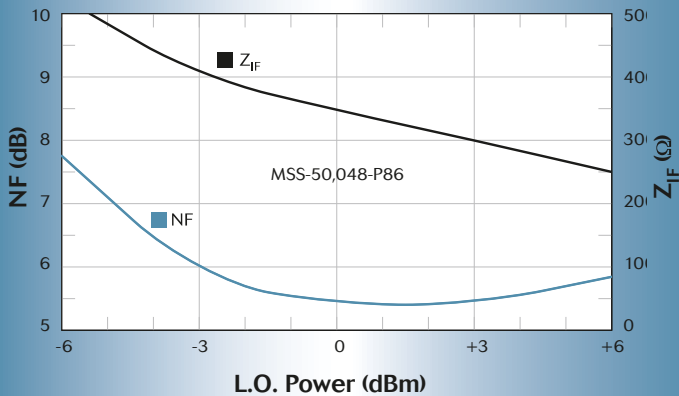
Schottky Diodes for Mixer Applications

High Barrier, $V_F = 450 \sim 550$ mV, $V_{BR} = 4$ V min.

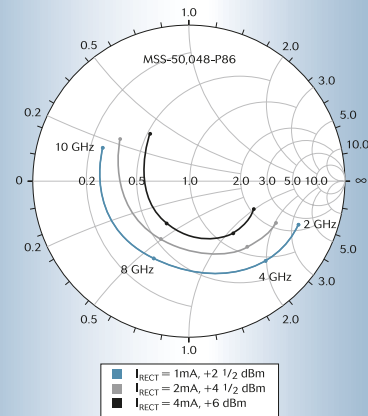
Chip and Beam Lead

Model	Configuration	C_J		R_D MAX Ω	R_S TYP Ω	F_{CO} TYP GHz	Package
		TYP pF	MAX pF				
MSS50,048-C15	Single Junction	0.12	0.15	15	7	190	C15
MSS50,062-C16	Single Junction	0.50	0.55	12	2	160	C16
MSS50,146-B10B	Single Junction	0.07	0.12	18	9	253	B10B
MSS50,155-B10B	Single Junction	0.25	0.30	15	7	90	B10B
MSS50,244-B20	Series Tee	0.15	0.20	16	7	183	B20
MSS50,341-B21	Anti-Parallel Pair	0.20	0.26	16	7	114	B21
MSS50,448-B40	Ring Quad	0.20	0.25	14	6	133	B40
MSS50,B46-B45	Bridge Quad	0.10	0.13	20	10	159	B45
MSS50,B53-B45	Bridge Quad	0.20	0.25	15	5	159	B45
MSS50,CR46-B49	Crossover Ring Quad	0.09	0.125	22	10	177	B49
MSS50,CR53-B49	Crossover Ring Quad	0.15	0.25	15	5	212	B49
MSS50,PCB46-B48	Coplanar Bridge Quad	0.08	0.12	20	7	284	B48
MSS50,PCR46-B47	Coplanar Ring Quad	0.07	0.13	22	10	227	B47
MSS50,PCR53-B48	Coplanar Ring Quad	0.15	0.25	15	5	212	B47
Test Conditions		$V_R = 0$ V $F = 1$ MHz		$I_F = 5$ mA			

NF & Z_{IF} vs. LO Power



Smith Chart - 50 Ω Reference

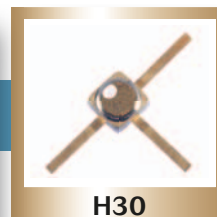


Silicon Schottky Diodes

High Barrier, $V_F = 450 \sim 550$ mV, $V_{BR} = 4$ V min.

Packaged

Model	Configuration	C_T		R_D MAX Ω	C_P TYP pF	L_P TYP nH	Package
		TYP pF	MAX pF				
MSS50,048-P55	Single Junction	0.25	0.31	15	0.13	0.35	P55
MSS50,048-P86	Single Junction	0.27	0.33	15	0.15	1.0	P86
MSS50,062-P55	Single Junction	0.63	0.75	12	0.13	0.35	P55
MSS50,062-P86	Single Junction	0.65	0.78	12	0.15	1.0	P86
MSS50,146-E25	Single Junction	0.14	0.24	18	0.07	0.4	E25
MSS50,146-H20	Single Junction	0.25	0.34	18	0.18	0.5	H20
MSS50,146-0402	Single Junction	0.11	0.20	18	0.05	0.25	0402
MSS50,146-0805-2	Single Junction	0.12	0.22	18	0.06	0.4	0805-2
MSS50,155-E25	Single Junction	0.32	0.41	15	0.07	0.4	E25
MSS50,155-H20	Single Junction	0.43	0.51	15	0.18	0.5	H20
MSS50,155-0402	Single Junction	0.30	0.38	15	0.05	0.25	0402
MSS50,155-0805-2	Single Junction	0.31	0.40	15	0.06	0.4	0805-2
MSS50,244-E35	Series Tee	0.22	0.31	16	0.07	0.4	E35
MSS50,244-H30	Series Tee	0.33	0.42	16	0.18	0.5	H30
MSS50,244-0805-4	Series Tee	0.34	0.44	16	0.06	0.4	0805-4
MSS50,341-E25	Anti-Parallel Pair	0.27	0.36	16	0.07	0.4	E25
MSS50,341-H20	Anti-Parallel Pair	0.38	0.48	16	0.18	0.5	H20
MSS50,448-E45	Ring Quad	0.27	0.36	10	0.07	0.4	E45
MSS50,448-H40	Ring Quad	0.38	0.48	10	0.18	0.5	H40
MSS50,448-0805-4	Ring Quad	0.26	0.35	10	0.06	0.4	0805-4
MSS50,B46-E45	Bridge Quad	0.17	0.25	20	0.07	0.4	E45
MSS50,B46-H40	Bridge Quad	0.28	0.35	20	0.18	0.5	H40
MSS50,B53-E45	Bridge Quad	0.27	0.36	15	0.07	0.4	E45
MSS50,B53-H40	Bridge Quad	0.38	0.48	15	0.18	0.5	H40
MSS50,CR46-E45	Crossover Ring Quad	0.16	0.25	22	0.07	0.4	E45
MSS50,CR46-H40	Crossover Ring Quad	0.27	0.36	22	0.18	0.5	H40
MSS50,CR53-E45	Crossover Ring Quad	0.22	0.36	15	0.07	0.4	E45
MSS50,CR53-H40	Crossover Ring Quad	0.33	0.46	15	0.18	0.5	H40
Test Conditions		$V_R = 0$ V $F = 1$ MHz		$I_F = 5$ mA			



Silicon Schottky Diodes

Schottky Diodes for Mixer Applications

Extra High Barrier, $V_F = 550 \sim 700$ mV, $V_{BR} = 3.5$ V min.

Chip and Beam Lead

Model	Configuration	C_j		R_D MAX Ω	R_S TYP Ω	F_{CO} TYP GHz	Package
		TYP pF	MAX pF				
MSS60,144-B10B	Single Junction	0.08	0.10	25	15	153	B10B
MSS60,148-B10B	Single Junction	0.12	0.15	18	10	133	B10B
MSS60,153-B10B	Single Junction	0.20	0.25	12	5	159	B10B
MSS60,244-B20	Series Tee	0.08	0.10	25	15	133	B20
MSS60,248-B20	Series Tee	0.12	0.15	18	7	133	B20
MSS60,253-B20	Series Tee	0.20	0.25	12	5	159	B20
MSS60,444-B42	Ring Quad	0.08	0.10	25	15	133	B42
MSS60,448-B42	Ring Quad	0.12	0.15	18	7	133	B42
MSS60,453-B41	Ring Quad	0.25	0.30	12	5	159	B41
MSS60,841-B80	8 Junction Ring Quad	0.06	0.08	28	18	133	B80
MSS60,846-B80	8 Junction Ring Quad	0.10	0.12	23	12	106	B80
MSS60,848-B80	8 Junction Ring Quad	0.12	0.15	18	7	133	B80
MSS60,B46-B45	Bridge Quad	0.10	0.13	25	15	106	B45
MSS60,B53-B45	Bridge Quad	0.20	0.25	18	7	114	B45
MSS60,CR46-B49	Crossover Ring Quad	0.09	0.125	22	10	177	B49
MSS60,CR53-B49	Crossover Ring Quad	0.15	0.25	15	7	152	B49
MSS60,PCB46-B48	Coplanar Bridge Quad	0.08	0.12	20	7	284	B48
MSS60,PCR46-B47	Coplanar Ring Quad	0.07	0.13	22	10	227	B47
MSS60,PCR53-B47	Coplanar Ring Quad	0.15	0.25	15	7	152	B47
Test Conditions		$V_R = 0$ V $F = 1$ MHz		$I_F = 5$ mA			



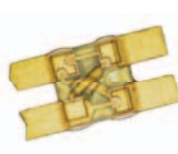
B42



B45



B47



B48



B49



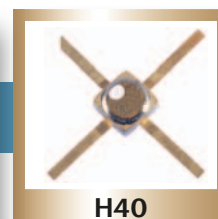
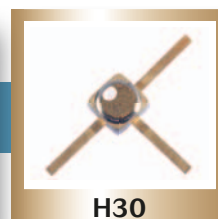
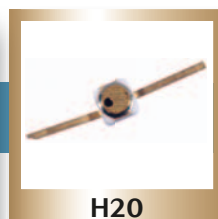
B80

Silicon Schottky Diodes

Extra High Barrier, $V_F = 550 \sim 700 \text{ mV}$, $V_{BR} = 3.5 \text{ V min.}$

Packaged

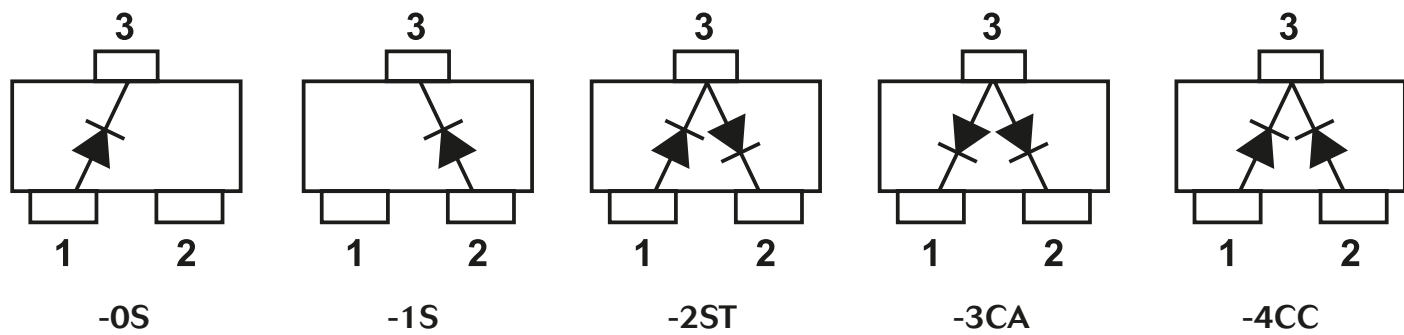
Model	Configuration	C_T		R_D MAX Ω	C_P TYP pF	L_P TYP nH	Package
		TYP pF	MAX pF				
MSS60,144-E25	Single Junction	0.15	0.22	25	0.07	0.4	E25
MSS60,144-H20	Single Junction	0.26	0.31	25	0.18	0.5	H20
MSS60,148-E25	Single Junction	0.19	0.28	18	0.07	0.4	E25
MSS60,148-H20	Single Junction	0.30	0.38	18	0.18	0.5	H20
MSS60,153-E25	Single Junction	0.27	0.36	12	0.07	0.4	E25
MSS60,153-H20	Single Junction	0.38	0.48	12	0.18	0.5	H20
MSS60,244-E35	Series Tee	0.15	0.22	25	0.07	0.4	E35
MSS60,244-H30	Series Tee	0.26	0.36	25	0.18	0.5	H30
MSS60,248-E35	Series Tee	0.19	0.28	18	0.07	0.4	E35
MSS60,248-H30	Series Tee	0.30	0.40	18	0.18	0.5	H30
MSS60,253-E35	Series Tee	0.27	0.37	12	0.07	0.4	E35
MSS60,253-H30	Series Tee	0.38	0.48	12	0.18	0.5	H30
MSS60,444-E45	Ring Quad	0.15	0.22	25	0.07	0.4	E45
MSS60,444-H40	Ring Quad	0.26	0.33	25	0.18	0.5	H40
MSS60,448-E45	Ring Quad	0.19	0.27	18	0.07	0.4	E45
MSS60,448-H40	Ring Quad	0.30	0.38	18	0.18	0.5	H40
MSS60,453-E45	Ring Quad	0.32	0.42	12	0.07	0.4	E45
MSS60,453-H40	Ring Quad	0.43	0.53	12	0.18	0.5	H40
MSS60,841-E45	8 Junction Ring Quad	0.13	0.20	28	0.07	0.4	E45
MSS60,841-H40	8 Junction Ring Quad	0.24	0.31	28	0.18	0.5	H40
MSS60,846-E45	8 Junction Ring Quad	0.17	0.24	23	0.07	0.4	E45
MSS60,846-H40	8 Junction Ring Quad	0.28	0.35	23	0.18	0.5	H40
MSS60,848-E45	8 Junction Ring Quad	0.19	0.27	18	0.07	0.4	E45
MSS60,848-H40	8 Junction Ring Quad	0.30	0.38	18	0.18	0.5	H40
MSS60,B46-E45	Bridge Quad	0.17	0.25	25	0.07	0.4	E45
MSS60,B46-H40	Bridge Quad	0.28	0.36	25	0.18	0.5	H40
MSS60,B53-E45	Bridge Quad	0.27	0.37	18	0.07	0.4	E45
MSS60,B53-H40	Bridge Quad	0.38	0.48	18	0.18	0.5	H40
MSS60,CR46-E45	Crossover Ring Quad	0.16	0.25	22	0.07	0.4	E45
MSS60,CR53-E45	Crossover Ring Quad	0.22	0.37	15	0.07	0.4	E45
Test Conditions		$V_R = 0 \text{ V}$ $F = 1 \text{ MHz}$		$I_F = 5 \text{ mA}$			



Silicon Schottky Diodes

Plastic Surface Mount Packages

Configuration Codes



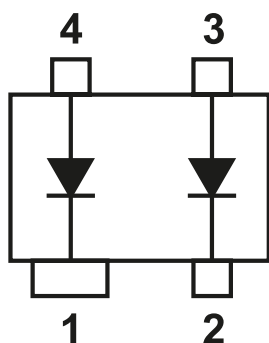
SOT23 & SOD323

Model	Configuration	V_{BR} MIN V	V_F TYP mV	C_T MAX pF	R_D MAX Ω	Package
SMST3012-SOT23	-0S, 1S, 2ST, 3CA, 4CC	2.0	270	0.25	15	SOT23
SMST4012-SOT23	-0S, 1S, 2ST, 3CA, 4CC	2.0	350	0.25	15	SOT23
SMST6012-SOT23	-0S, 1S, 2ST, 3CA, 4CC	2.0	630	0.25	15	SOT23
SMST3004-SOT23	-0S, 1S, 2ST, 3CA, 4CC	2.0	270	0.60	10	SOT23
SMST4004-SOT23	-0S, 1S, 2ST, 3CA, 4CC	2.0	350	0.60	10	SOT23
SMST6004-SOT23	-0S, 1S, 2ST, 3CA, 4CC	2.0	600	0.60	10	SOT23
SMSD3012-SOD323	---	2.0	270	0.25	15	SOD323
SMSD4012-SOD323	---	2.0	350	0.25	15	SOD323
SMSD6012-SOD323	---	2.0	630	0.25	15	SOD323
SMSD3004-SOD323	---	2.0	270	0.60	10	SOD323
SMSD4004-SOD323	---	2.0	350	0.60	10	SOD323
SMSD6004-SOD323	---	2.0	600	0.60	10	SOD323
Test Conditions		$I_R = 10 \mu A$	$I_F = 1 \text{ mA}$	$V_R = 0 \text{ V}$ $F = 1 \text{ MHz}$	$I_F = 10 \text{ mA}$	

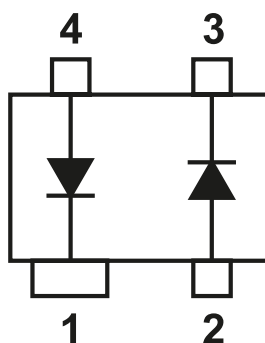


Silicon Schottky Diodes

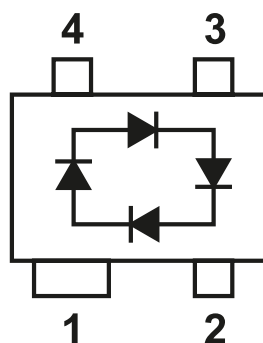
Configuration Codes



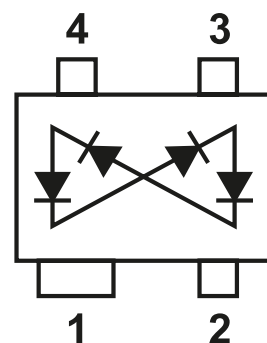
SMSP-



SMAP-



SMSRQ-



SMSCQ-

Plastic Packaged

Model	Configuration	V_{BR} MIN V	V_F TYP mV	C_T MAX pF	R_D MAX Ω	Package
SMSP3012-SOT143	Split Pair	2	270	0.40	15.0	SOT143
SMSP3004-SOT143	Split Pair	2	270	0.65	10.0	SOT143
SMAP3012-SOT143	Anti-Parallel Pair	2	270	0.40	15.0	SOT143
SMAP3004-SOT143	Anti-Parallel Pair	2	270	0.65	10.0	SOT143
SMSRQ1200-SOT143	Ring Quad	2	270	0.40	15.0	SOT143
SMSCQ1200-SOT143	Crossover Quad	2	270	0.40	15.0	SOT143
SMSRQ1500-SOT143	Ring Quad	2	270	0.65	8.0	SOT143
SMSCQ1500-SOT143	Crossover Quad	2	270	0.65	8.0	SOT143
SMSRQ2500-SOT143	Ring Quad	2	400	0.65	10.0	SOT143
SMSCQ2500-SOT143	Crossover Quad	2	400	0.65	10.0	SOT143
SMSRQ4500-SOT143	Ring Quad	3	600	0.65	8.0	SOT143
SMSCQ4500-SOT143	Crossover Quad	3	600	0.65	8.0	SOT143
SMSRQ5500-SOT143	Ring Quad	3	1,100	0.55	16.0	SOT143
SMSCQ5500-SOT143	Crossover Quad	3	1,100	0.55	16.0	SOT143
Test Conditions		$I_R = 10 \mu A$	$I_F = 1 \text{ mA}$	$V_R = 0 \text{ V}$ $F = 1 \text{ MHz}$	$I_F = 10 \text{ mA}$	



SOT143

GaAs Schottky Diodes

Millimeter wave performance in twelve configurations featuring double passivation and Aeroflex / Metelics' tri-metallization for ultra-reliable operation in the most demanding environments. Topologies supporting limiter, mixer, multiplier and sampler designs operating to 60+ GHz are available in flip chip, beam lead and packaged form. Screening per MIL-PRF-19500 and MIL-PRF-38534 is available.

Flip Chip

Model	Configuration	V_F		ΔV_F MAX mV	V_{BR} MIN V	C_J MAX pF	ΔC_J MAX pF	R_s MAX Ω	Package
		MIN mV	MAX mV						
MGS801	Single Junction	650	750	N/A	5	0.05	N/A	7	GC110
MGS801A	Single Junction	650	750	N/A	5	0.075	N/A	5	GC110
MGS802	Anti-parallel Pair	650	750	20	---	0.10	N/A	7	GC210
MGS802A	Anti-Parallel Pair	650	750	20	---	0.15	N/A	5	GC210
MGS803	Series Tee	650	750	20	5	0.06	0.02	7	GC310
Test Conditions		$I_F = 1 \text{ mA}$			$I_R = 10 \mu\text{A}$	$V_R = 0 \text{ V}$ $F = 1 \text{ MHz}$		$I_F = 5 \text{ mA}$	

Beam Lead

Model	Configuration	V_F		ΔV_F MAX mV	V_{BR} MIN V	C_J MAX pF	ΔC_J MAX pF	R_s MAX Ω	Package
		MIN mV	MAX mV						
MGS901	Single Junction	650	750	N/A	5	0.06	N/A	7	GB110
MGS902	Anti Parallel Pair	650	750	20	---	0.10	N/A	7	GB210
MGS903	Series Tee	650	750	20	5	0.06	0.02	7	GB310
MGS904	4 Junction Ring Quad	650	750	20	---	0.06	0.02	7	B85
MGS904A	4 Junction Ring Quad	650	750	20	---	0.08	0.02	5	B85
MGS905	4 Junction Bridge Quad	650	750	20	5	0.06	0.02	7	B86
MGS906	4 Junction Series Tee	1300	1500	40	10	0.04	0.02	14	B90
MGS907	8 Junction Ring Quad	1300	1500	40	---	0.04	0.02	14	B85
MGS907A	8 Junction Ring Quad	1300	1500	40	---	0.06	0.02	12	B85
MGS907B	8 Junction Ring Quad	1300	1500	40	---	0.08	0.02	10	B85
MGS908	8 Junction Bridge Quad	1300	1500	40	10	0.04	0.02	14	B86
MGS909	6 Junction Series Tee	1800	2100	60	15	0.10	0.03	21	B90
MGS910	12 Junction Ring Quad	1800	2100	60	---	0.10	0.03	21	B87
MGS911	12 Junction Bridge Quad	1800	2100	60	15	0.10	0.03	21	B88
MGS912	Four Junction	2500	2900	N/A	20	0.03	N/A	28	B89
Test Conditions		$I_F = 1 \text{ mA}$			$I_R = 10 \mu\text{A}$	$V_R = 0 \text{ V}$ $F = 1 \text{ MHz}$		$I_F = 5 \text{ mA}$	



GC110



GC210



GC310



B85



B88



B89

GaAs Abrupt Varactor Diodes

$$V_{BR} = 22 \text{ V min.}$$

Chips

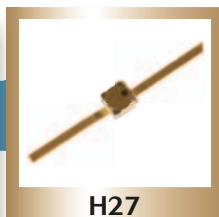
Model	Γ NOM	C_j			Tuning Ratio			Q MIN	Package
		MIN pF	NOM pF	MAX pF	MIN	TYP	MAX		
MGV050-18	0.50	0.25	0.30	0.35	4.0	4.7	5.5	4,000	C01A
MGV050-20	0.50	0.50	0.55	0.61	4.0	4.7	5.5	4,000	C01A
MGV050-22	0.50	0.90	1.00	1.10	4.0	4.7	5.5	3,000	C01A
MGV050-24	0.50	1.35	1.50	1.65	4.0	4.7	5.5	3,000	C01A
MGV050-26	0.50	1.80	2.00	2.20	4.0	4.7	5.5	3,000	C01A
Test Conditions	$V_R =$ 2 to 22 V	$V_R = 4 \text{ V}$ $F = 1 \text{ MHz}$			$V_R = 0 \text{ to } 22 \text{ V}$			$V_R = 4 \text{ V}$ $F = 50 \text{ MHz}$	

Packaged

Model	Γ NOM	C_T			Tuning Ratio			Q MIN	Package
		MIN pF	NOM pF	MAX pF	MIN	TYP	MAX		
MGV050-18-E28 / 28X	0.50	0.31	0.38	0.45	3.0	3.4	3.9	4,000	E28 / 28X
MGV050-18-H20	0.50	0.41	0.48	0.55	2.0	2.6	3.2	4,000	H20
MGV050-18-0805-2	0.50	0.29	0.36	0.43	3.0	3.6	4.2	4,000	0805-2
MGV050-20-E28 / 28X	0.50	0.55	0.63	0.71	3.3	3.9	4.5	4,000	E28 / 28X
MGV050-20-H20	0.50	0.64	0.73	0.82	2.8	3.2	3.7	4,000	H20
MGV050-20-0805-2	0.50	0.53	0.61	0.69	3.4	4.0	4.8	4,000	0805-2
MGV050-22-E28 / 28X	0.50	0.95	1.08	1.21	3.6	4.2	5.0	3,000	E28 / 28X
MGV050-22-H20	0.50	1.04	1.18	1.32	3.2	3.7	4.4	3,000	H20
MGV050-22-0805-2	0.50	0.93	1.06	1.19	3.7	4.3	5.1	3,000	0805-2
MGV050-24-E28 / 28X	0.50	1.40	1.58	1.76	3.7	4.2	5.3	3,000	E28 / 28X
MGV050-24-H20	0.50	1.49	1.68	1.87	3.4	3.7	4.7	3,000	H20
MGV050-24-0805-2	0.50	1.38	1.56	1.74	3.8	4.3	5.3	3,000	0805-2
MGV050-26-E28 / 28X	0.50	1.85	2.08	2.31	3.8	4.4	5.3	3,000	E28 / 28X
MGV050-26-H20	0.50	1.94	2.18	2.42	3.5	4.0	4.9	3,000	H20
MGV050-26-0805-2	0.50	1.83	2.06	2.29	3.8	4.5	5.4	3,000	0805-2
Test Conditions	$V_R =$ 0 to 22 V	$V_R = 4 \text{ V}$ $F = 1 \text{ MHz}$			$V_R = 0 \text{ to } 22 \text{ V}$			$V_R = 4 \text{ V}$ $F = 50 \text{ MHz}$	



0805-2



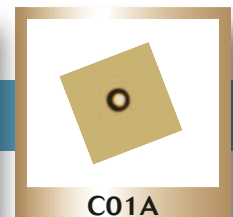
H27



E28



E28X



C01A

GaAs Hyperabrupt Varactor Diodes

The MGV series of hyperabrupt varactor diodes feature passivated mesa construction for low leakage and excellent post tuning drift. Available in three constant gamma families of 0.75, 1.0 and 1.25. These diodes will find application in tunable filters and oscillators up to 40 GHz. Optimum performance is obtained using die however packaged devices are available as well diodes screened per MIL-PRF-19500 and MIL-PRF-38534. Contact your representative for these and other options.

$$V_{BR} = 22 \text{ V min.}$$

Chips

Model	Γ NOM	C_j			Tuning Ratio			Q MIN	Package
		MIN pF	NOM pF	MAX pF	MIN	TYP	TYP		
MGV075-08	0.75	0.25	0.30	0.35	2.2	2.8	3.5	4,000	C01A
MGV075-09	0.75	0.35	0.40	0.45	2.2	2.8	3.5	4,000	C01A
MGV075-10	0.75	0.45	0.50	0.55	2.2	2.8	3.5	3,000	C01A
MGV075-11	0.75	0.63	0.70	0.77	2.2	2.8	3.5	3,000	C01A
MGV075-12	0.75	0.72	0.80	0.88	2.2	2.8	3.5	3,000	C01A
MGV075-13	0.75	0.90	1.00	1.10	2.2	2.8	3.5	3,000	C01A
MGV075-14	0.75	1.08	1.20	1.32	2.2	2.8	3.5	3,000	C01A
MGV075-15	0.75	1.35	1.50	1.65	2.2	2.8	3.5	3,000	C01A
MGV075-16	0.75	1.62	1.80	1.98	2.2	2.8	3.5	3,000	C01A
MGV075-17	0.75	1.80	2.00	2.20	2.2	2.8	3.5	3,000	C01A
MGV100-08	1.00	0.30	0.35	0.40	2.7	3.4	5.0	4,000	C01A
MGV100-09	1.00	0.40	0.45	0.50	2.7	3.4	5.0	4,000	C01A
MGV100-20	1.00	0.50	0.55	0.61	2.7	3.4	5.0	4,000	C01A
MGV100-21	1.00	0.58	0.65	0.72	2.7	3.4	5.0	4,000	C01A
MGV100-22	1.00	0.72	0.80	0.88	2.7	3.4	5.0	3,000	C01A
MGV100-23	1.00	0.90	1.00	1.10	2.7	3.4	5.0	3,000	C01A
MGV100-24	1.00	1.08	1.20	1.32	2.7	3.4	5.0	3,000	C01A
MGV100-25	1.00	1.35	1.50	1.65	2.7	3.4	5.0	3,000	C01A
MGV100-26	1.00	1.53	1.70	1.87	2.7	3.4	5.0	3,000	C01A
MGV100-27	1.00	1.80	2.00	2.20	2.7	3.4	5.0	3,000	C01A
MGV125-08	1.25	0.25	0.30	0.35	4.0	5.0	8.4	4,000	C01A
MGV125-09	1.25	0.35	0.40	0.45	4.0	5.0	8.5	4,000	C01A
MGV125-20	1.25	0.45	0.50	0.55	4.0	5.0	8.6	4,000	C01A
MGV125-21	1.25	0.63	0.70	0.77	4.0	5.0	8.8	4,000	C01A
MGV125-22	1.25	0.90	1.00	1.10	4.0	5.0	9.0	3,000	C01A
MGV125-23	1.25	1.08	1.20	1.32	4.0	5.0	9.5	3,000	C01A
MGV125-24	1.25	1.35	1.50	1.65	4.0	5.0	10	3,000	C01A
MGV125-25	1.25	1.53	1.70	1.87	4.0	5.0	10	3,000	C01A
MGV125-26	1.25	1.80	2.00	2.20	4.0	5.0	10	3,000	C01A
Test Conditions	$V_R =$ 2 to 20 V		$V_R = 4 \text{ V}$ $F = 1 \text{ MHz}$		$V_R = 2 \text{ to } 12 \text{ V}$		$V_R =$ 2 to 20 V	$V_R = 4 \text{ V}$ $F = 50 \text{ MHz}$	



C01A

Silicon Abrupt Varactor Diodes

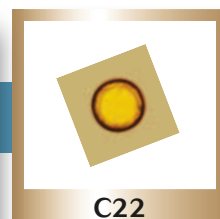
The work horse of varactors these diodes feature fully passivated mesa construction and Aeroflex / Metelics tri-metallization. Featuring a nominal gamma of 0.46 these find application in tunable filters and oscillators up to 18 GHz.

Chips

Model	V _{BR} MIN V	C _J			Tuning Ratio		Q MIN	R _s MAX Ω	Package
		MIN pF	NOM pF	MAX pF	MIN	TYP			
MSV34,060-C12	30	0.36	0.4	0.44	3.5	4.0	6,300	1.3	C12
MSV34,064-C12	30	0.54	0.6	0.66	3.5	4.0	5,300	1.0	C12
MSV34,067-C12	30	0.72	0.8	0.88	3.5	4.0	4,500	0.9	C12
MSV34,069-C12	30	0.90	1.0	1.10	4.0	4.7	4,000	0.8	C12
MSV34,075-C12	30	1.62	1.8	1.98	4.0	4.7	3,600	0.5	C12
MSV34,082-C12	30	3.42	3.8	4.18	4.0	4.7	2,700	0.3	C12
MSV34,087-C12	30	5.22	5.8	6.38	4.0	4.7	2,200	0.2	C12
MSV34,092-C22	30	8.82	9.8	10.78	4.0	4.7	2,000	0.2	C22
MSV38,060-C12	45	0.36	0.4	0.44	4.5	5.0	4,500	1.8	C12
MSV38,064-C12	45	0.54	0.6	0.66	4.5	5.0	3,200	1.7	C12
MSV38,067-C12	45	0.72	0.8	0.88	4.5	5.0	3,000	1.3	C12
MSV38,069-C12	45	0.90	1.0	1.10	5.0	5.5	2,800	1.0	C12
MSV38,075-C12	45	1.62	1.8	1.98	5.0	5.5	2,600	0.7	C12
MSV38,082-C12	45	3.42	3.8	4.18	5.0	5.5	2,100	0.4	C12
MSV38,087-C12	45	5.22	5.8	6.38	5.0	5.5	1,800	0.3	C12
MSV38,092-C22	45	8.82	9.8	10.78	5.0	5.5	1,800	0.2	C22
MSV40,060-C12	60	0.36	0.4	0.44	5.0	5.5	3,000	2.7	C12
MSV40,064-C12	60	0.54	0.6	0.66	5.0	5.5	2,600	2.0	C12
MSV40,067-C12	60	0.72	0.8	0.88	5.0	5.5	2,600	1.6	C12
MSV40,069-C12	60	0.90	1.0	1.10	6.0	6.5	2,400	1.2	C12
MSV40,075-C12	60	1.62	1.8	1.98	6.0	6.5	2,200	0.8	C12
MSV40,082-C12	60	3.42	3.8	4.18	6.0	6.5	1,500	0.5	C12
MSV40,087-C12	60	5.22	5.8	6.38	6.0	6.5	1,500	0.4	C12
MSV40,092-C22	60	8.82	9.8	10.78	6.0	6.5	1,500	0.3	C22
Test Conditions	I _R = 10 μA		V _R = 4 V F = 1 MHz		V _R = 0 V & V _R = V _{BR} F = 1 MHz		V _R = 4 V F = 50 MHz		



C12



C22

Silicon Abrupt Varactor Diodes

Packaged

Model	V _{BR} MIN V	C _T			Tuning Ratio MIN	Q MIN	C _p TYP pF	L _p TYP nH	Package
		MIN pF	NOM pF	MAX pF					
MSV34,060-E28 / 28 X	30	0.42	0.48	0.54	2.8	6,300	0.08	0.4	E28 / 28X
MSV34,060-H20	30	0.50	0.58	0.66	2.3	6,300	0.18	0.5	H20
MSV34,060-T86	30	0.50	0.58	0.66	2.3	6,300	0.18	1.0	T86
MSV34,060-0805-2	30	0.41	0.46	0.51	3.0	6,300	0.06	0.4	0805-2
MSV34,064-E28 / 28 X	30	0.60	0.68	0.76	3.0	5,300	0.08	0.4	E28 / 28X
MSV34,064-H20	30	0.68	0.78	0.88	2.6	5,300	0.18	0.5	H20
MSV34,064-T86	30	0.68	0.78	0.88	2.6	5,300	0.18	1.0	T86
MSV34,064-0805-2	30	0.59	0.66	0.73	3.0	5,300	0.06	0.4	0805-2
MSV34,067-E28 / 28 X	30	0.78	0.88	0.98	3.1	4,500	0.08	0.4	E28 / 28X
MSV34,067-H20	30	0.86	0.98	1.10	2.7	4,500	0.18	0.5	H20
MSV34,067-T86	30	0.86	0.98	1.10	2.7	4,500	0.18	1.0	T86
MSV34,067-0805-2	30	0.77	0.86	0.95	3.2	4,500	0.06	0.4	0805-2
MSV34,069-E28 / 28 X	30	0.96	1.08	1.20	4.0	4,000	0.08	0.4	E28 / 28X
MSV34,069-H20	30	1.04	1.18	1.32	3.5	4,000	0.18	0.5	H20
MSV34,069-T86	30	1.04	1.18	1.32	3.5	4,000	0.18	1.0	T86
MSV34,069-0805-2	30	0.95	1.06	1.17	4.1	4,000	0.06	0.4	0805-2
MSV34,075-E28 / 28 X	30	1.68	1.88	2.08	4.2	3,600	0.08	0.4	E28 / 28X
MSV34,075-H20	30	1.76	1.98	2.20	3.8	3,600	0.18	0.5	H20
MSV34,075-T86	30	1.76	1.98	2.20	3.8	3,600	0.18	1.0	T86
MSV34,075-0805-2	30	1.67	1.86	2.05	4.2	3,600	0.06	0.4	0805-2
MSV34,082-E28 / 28 X	30	3.48	3.88	4.28	4.3	2,700	0.08	0.4	E28 / 28X
MSV34,082-H20	30	3.56	3.98	4.40	4.1	2,700	0.18	0.5	H20
MSV34,082-T86	30	3.56	3.98	4.40	4.1	2,700	0.18	1.0	T86
MSV34,082-0805-2	30	3.47	3.86	4.25	4.4	2,700	0.06	0.4	0805-2
MSV34,087-E28 / 28 X	30	5.28	5.88	6.48	4.4	2,200	0.08	0.4	E28 / 28X
MSV34,087-H20	30	5.36	5.98	6.60	4.3	2,200	0.18	0.5	H20
MSV34,087-T86	30	5.36	5.98	6.60	4.3	2,200	0.18	1.0	T86
MSV34,087-0805-2	30	5.27	5.86	6.45	4.4	2,200	0.06	0.4	0805-2
MSV34,092-E28 / 28 X	30	8.88	9.88	10.88	4.4	2,000	0.08	0.4	E28 / 28X
MSV34,092-H20	30	8.96	9.98	11.00	4.3	2,000	0.18	0.5	H20
MSV34,092-T86	30	8.96	9.98	11.00	4.3	2,000	0.18	1.0	T86
MSV34,092-0805-2	30	8.87	9.86	10.85	4.4	2,000	0.06	0.4	0805-2
Test Conditions	I _R = 10 μ A		V _R = 4 V F = 1 MHz		V _R = 0 to 30 V F = 1 MHz	V _R = 4 V F = 50 MHz			



0805-2



H20



E28



E28X



T86

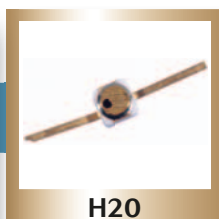
Silicon Abrupt Varactor Diodes

Packaged

Model	V_{BR}	C_T			Tuning Ratio	Q	C_P	L_P	Package
	MIN V	MIN pF	NOM pF	MAX pF					
MSV38,060-E28 / 28 X	45	0.42	0.48	0.54	3.4	4,500	0.08	0.4	E28 / 28X
MSV38,060-H20	45	0.50	0.58	0.66	2.7	4,500	0.18	0.5	H20
MSV38,060-T86	45	0.50	0.58	0.66	2.7	4,500	0.18	1.0	T86
MSV38,060-0805-2	45	0.41	0.46	0.51	3.6	4,500	0.06	0.4	0805-2
MSV38,064-E28 / 28 X	45	0.60	0.68	0.76	3.7	3,200	0.08	0.4	E28 / 28X
MSV38,064-H20	45	0.68	0.78	0.88	3.0	3,200	0.18	0.5	H20
MSV38,064-T86	45	0.68	0.78	0.88	3.0	3,200	0.18	1.0	T86
MSV38,064-0805-2	45	0.59	0.66	0.73	3.8	3,200	0.06	0.4	0805-2
MSV38,067-E28 / 28 X	45	0.78	0.88	0.98	3.8	3,000	0.08	0.4	E28 / 28X
MSV38,067-H20	45	0.86	0.98	1.10	3.3	3,000	0.18	0.5	H20
MSV38,067-T86	45	0.86	0.98	1.10	3.3	3,000	0.18	1.0	T86
MSV38,067-0805-2	45	0.77	0.86	0.95	4.0	3,000	0.06	0.4	0805-2
MSV38,069-E28 / 28 X	45	0.96	1.08	1.20	4.3	2,800	0.08	0.4	E28 / 28X
MSV38,069-H20	45	1.04	1.18	1.32	3.7	2,800	0.18	0.5	H20
MSV38,069-T86	45	1.04	1.18	1.32	3.7	2,800	0.18	1.0	T86
MSV38,069-0805-2	45	0.95	1.06	1.17	4.4	2,800	0.06	0.4	0805-2
MSV38,075-E28 / 28 X	45	1.68	1.88	2.08	4.5	2,600	0.08	0.4	E28 / 28X
MSV38,075-H20	45	1.76	1.98	2.20	4.2	2,600	0.18	0.5	H20
MSV38,075-T86	45	1.76	1.98	2.20	4.2	2,600	0.18	1.0	T86
MSV38,075-0805-2	45	1.67	1.86	2.05	4.7	2,600	0.06	0.4	0805-2
MSV38,082-E28 / 28 X	45	3.48	3.88	4.28	4.8	2,100	0.08	0.4	E28 / 28X
MSV38,082-H20	45	3.56	3.98	4.40	4.6	2,100	0.18	0.5	H20
MSV38,082-T86	45	3.56	3.98	4.40	4.6	2,100	0.18	1.0	T86
MSV38,082-0805-2	45	3.47	3.86	4.25	4.8	2,100	0.06	0.4	0805-2
MSV38,087-E28 / 28 X	45	5.28	5.88	6.48	4.8	1,800	0.08	0.4	E28 / 28X
MSV38,087-H20	45	5.36	5.98	6.60	4.7	1,800	0.18	0.5	H20
MSV38,087-T86	45	5.36	5.98	6.60	4.7	1,800	0.18	1.0	T86
MSV38,087-0805-2	45	5.27	5.86	6.45	4.9	1,800	0.06	0.4	0805-2
MSV38,092-E28 / 28 X	45	8.88	9.88	10.88	4.9	1,800	0.08	0.4	E28 / 28X
MSV38,092-H20	45	8.96	9.98	11.00	4.8	1,800	0.18	0.5	H20
MSV38,092-T86	45	8.96	9.98	11.00	4.8	1,800	0.18	1.0	T86
MSV38,092-0805-2	45	8.87	9.86	10.85	4.9	1,800	0.06	0.4	0805-2
Test Conditions	$I_R = 10 \mu A$		$V_R = 4 V$ $F = 1 MHz$		$V_R = 0 \text{ to } 45 V$ $F = 1 MHz$	$V_R = 4 V$ $F = 50 MHz$			



0805-2



H20



E28



E28X

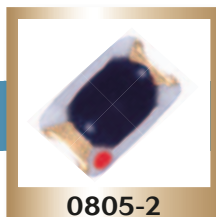


T86

Silicon Abrupt Varactor Diodes

Packaged

Model	V _{BR} MIN V	C _T			Tuning Ratio MIN	Q MIN	C _P TYP pF	L _P TYP nH	Package
		MIN pF	NOM pF	MAX pF					
MSV40,060-E28 / 28 X	60	0.42	0.48	0.54	3.6	3,000	0.08	0.4	E28 / 28X
MSV40,060-H20	60	0.50	0.58	0.66	2.8	3,000	0.18	0.5	H20
MSV40,060-T86	60	0.50	0.58	0.66	2.8	3,000	0.18	1.0	T86
MSV40,060-0805-2	60	0.41	0.46	0.51	3.9	3,000	0.06	0.4	0805-2
MSV40,064-E28 / 28 X	60	0.60	0.68	0.76	4.0	2,600	0.08	0.4	E28 / 28X
MSV40,064-H20	60	0.68	0.78	0.88	3.2	2,600	0.18	0.5	H20
MSV40,064-T86	60	0.68	0.78	0.88	3.2	2,600	0.18	1.0	T86
MSV40,064-0805-2	60	0.59	0.66	0.73	4.2	2,600	0.06	0.4	0805-2
MSV40,067-E28 / 28 X	60	0.78	0.88	0.98	4.2	2,600	0.08	0.4	E28 / 28X
MSV40,067-H20	60	0.86	0.98	1.10	3.5	2,600	0.18	0.5	H20
MSV40,067-T86	60	0.86	0.98	1.10	3.5	2,600	0.18	1.0	T86
MSV40,067-0805-2	60	0.77	0.86	0.95	4.3	2,600	0.06	0.4	0805-2
MSV40,069-E28 / 28 X	60	0.96	1.08	1.20	5.0	2,400	0.08	0.4	E28 / 28X
MSV40,069-H20	60	1.04	1.18	1.32	4.2	2,400	0.18	0.5	H20
MSV40,069-T86	60	1.04	1.18	1.32	4.2	2,400	0.18	1.0	T86
MSV40,069-0805-2	60	0.95	1.06	1.17	5.2	2,400	0.06	0.4	0805-2
MSV40,075-E28 / 28 X	60	1.68	1.88	2.08	5.4	2,200	0.08	0.4	E28 / 28X
MSV40,075-H20	60	1.76	1.98	2.20	4.8	2,200	0.18	0.5	H20
MSV40,075-T86	60	1.76	1.98	2.20	4.8	2,200	0.18	1.0	T86
MSV40,075-0805-2	60	1.67	1.86	2.05	5.5	2,200	0.06	0.4	0805-2
MSV40,082-E28 / 28 X	60	3.48	3.88	4.28	5.7	1,500	0.08	0.4	E28 / 28X
MSV40,082-H20	60	3.56	3.98	4.40	5.3	1,500	0.18	0.5	H20
MSV40,082-T86	60	3.56	3.98	4.40	5.3	1,500	0.18	1.0	T86
MSV40,082-0805-2	60	3.47	3.86	4.25	5.7	1,500	0.06	0.4	0805-2
MSV40,087-E28 / 28 X	60	5.28	5.88	6.48	5.8	1,500	0.08	0.4	E28 / 28X
MSV40,087-H20	60	5.36	5.98	6.60	5.5	1,500	0.18	0.5	H20
MSV40,087-T86	60	5.36	5.98	6.60	5.5	1,500	0.18	1.0	T86
MSV40,087-0805-2	60	5.27	5.86	6.45	5.8	1,500	0.06	0.4	0805-2
MSV40,092-E28 / 28 X	60	8.88	9.88	10.88	5.8	1,000	0.08	0.4	E28 / 28X
MSV40,092-H20	60	8.96	9.98	11.00	5.7	1,000	0.18	0.5	H20
MSV40,092-T86	60	8.96	9.98	11.00	5.7	1,000	0.18	1.0	T86
MSV40,092-0805-2	60	8.87	9.86	10.85	5.9	1,000	0.06	0.4	0805-2
Test Conditions	I _R = 10 μA	V _R = 4 V F = 1 MHz			V _R = 0 to 60 V F = 1 MHz	V _R = 4 V F = 50 MHz			



0805-2



H20



E28



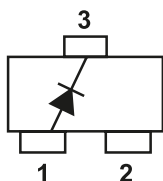
E28X



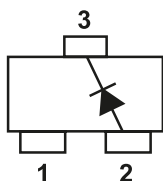
T86

Silicon Abrupt Varactor Diodes

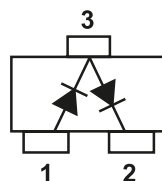
Configuration Codes



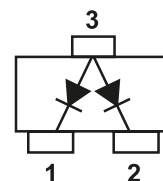
-0S



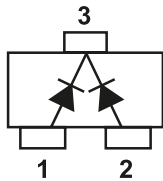
-1S



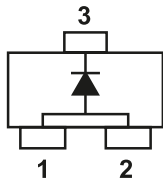
-2SF



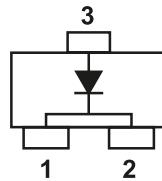
-3CA



-4CC



-5DA



-6DC

Plastic Packaged

Model	Configuration	C_T			Tuning Ratio MIN	Q MIN	Package
		MIN pF	NOM pF	MAX pF			
SMTV3001-SOT23	-0S, 1S, 2SF, 3CA, 4CC, 5DA, 6DC	0.8	1.0	1.2	3.5	3,000	SOT23
SMTV3002-SOT23	-0S, 1S, 2SF, 3CA, 4CC, 5DA, 6DC	1.6	2.0	2.4	3.6	2,800	SOT23
SMTV3004-SOT23	-0S, 1S, 2SF, 3CA, 4CC, 5DA, 6DC	3.2	4.0	4.8	4.2	2,400	SOT23
SMTV3006-SOT23	-0S, 1S, 2SF, 3CA, 4CC, 5DA, 6DC	4.8	6.0	7.2	4.3	2,100	SOT23
SMTV3008-SOT23	-0S, 1S, 2SF, 3CA, 4CC, 5DA, 6DC	6.4	8.0	9.6	4.3	1,800	SOT23
SMTV3010-SOT23	-0S, 1S, 2SF, 3CA, 4CC, 5DA, 6DC	8.0	10.0	12.0	4.4	1,600	SOT23
SMTD3001-SOD323	---	0.8	1.0	1.2	3.5	3,000	SOD323
SMTD3002-SOD323	---	1.6	2.0	2.4	3.6	2,800	SOD323
SMTD3004-SOD323	---	3.2	4.0	4.8	4.2	2,400	SOD323
SMTD3006-SOD323	---	4.8	6.0	7.2	4.3	2,100	SOD323
SMTD3008-SOD323	---	6.4	8.0	9.6	4.3	1,800	SOD323
SMTD3010-SOD323	---	8.0	10.0	12.0	4.4	1,600	SOD323
Test Conditions		$V_R = 4 \text{ V}$ $F = 1 \text{ MHz}$			$V_R = 0 \text{ V}$ $V_R = 30 \text{ V}$ $F = 1 \text{ MHz}$	$V_R = 4 \text{ V}$ $F = 50 \text{ MHz}$	



SOT23



SOD323

Silicon PIN Diodes

Beam Lead

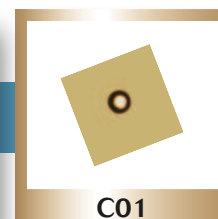
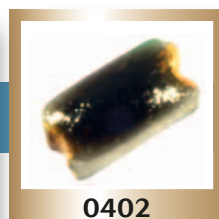
Beam Lead & Packaged Beam Lead

Model	V_{BR} MIN V	C_J		R_S		τ TYP ns	t_{rr} TYP ns	P_{DISS} MAX MW	Package
		TYP pF	MAX pF	TYP Ω	MAX Ω				
MBP1030-B11	100	0.020	0.025	5.5	6.5	35	5.0	250	B11
MBP1033-B11	100	0.025	0.030	4.0	5.0	40	5.0	250	B11
MBP1034-B11	100	0.025	0.030	6.0	7.0	25	5.5	250	B11
MBP1035-B11	60	0.030	0.040	3.5	4.0	30	2.5	250	B11
MBP1036-B11	60	0.040	0.050	2.5	3.0	40	2.5	250	B11
MBP2030-B11	60	0.023	0.025	6.0	7.0	20	4.0	250	B11
MBP2034-B11	60	0.026	0.030	5.0	6.0	20	3.0	250	B11
MPND4005-B15	100	0.018	0.020	5.5*	6.5*	125	---	250	B15
MPND4005-B16	100	0.018	0.020	5.5*	6.5*	125	---	250	B16
MPND4005-0402	100	0.070*	0.090*	5.5	6.5	125	---	250	0402
Test Conditions	$I_R = 10 \mu A$	$V_R = 10 V$ $F = 15 GHz$ * C_T		$I_F = 10 mA$ * $I_F = 20 mA$ $F = 3 GHz$		$I_F = 10 mA$ $I_R = 6 mA$	$I_F = 10 mA$ $V_R = 10 V$	$T_C = +25 ^\circ C$, Derate Linearly to $+175 ^\circ C$	

Low Capacitance, Fast Switching

Beam Lead & Packaged

Model	V_{BR} MIN V	C_J		R_S		τ TYP ns	Contact MIN mils	θ_{JC} MAX $^\circ C / W$	Package
		TYP pF	MAX pF	TYP Ω	MAX Ω				
MPN7302	20	0.08	0.12	1.2	1.5	8	1.5	60	C11
MPN7304	40	0.06	0.08	2.2	2.7	15	1.5	60	C11
MPN7304A	40	0.12	0.15	1.0	1.5	30	2.0	50	C12
MPN7306	70	0.08	0.10	1.2	1.2	50	2.0	50	C12
MPN7310	100	0.05	0.07	1.5	2.0	100	2.0	50	C12
MPN7310A	100	0.18	0.25	0.6	1.0	200	4.0	35	C12
MPN7312A	120	0.08	0.10	1.2*	1.5*	150	2.0	50	C12
MPN7312B	120	0.18	0.25	0.8*	1.0*	250	4.0	35	C12
MPN7315	150	0.08	0.12	1.2	1.5	180	2.0	50	C12
MPN7320	150	0.02	0.03	3.0	4.0	120	1.5	60	C01
Test Conditions	$I_R = 10 \mu A$	$V_R = 10 V$ $F = 1 MHz$		$I_F = 10 mA$ * $F = 100 MHz$ $F = 1 GHz$		$I_F = 10 mA$ $I_R = 6 mA$			



Silicon PIN Diodes

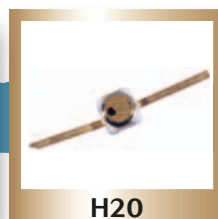
Low Capacitance, Fast Switching (Cont.)

Packaged

Model	V _{BR} MIN V	C _T		R _s		τ TYP ns	C _p TYP pF	L _p MAX nH	Package
		TYP pF	MAX pF	TYP Ω	MAX Ω				
MPN7302-E28 / 28X	20	0.16	0.24	1.2	1.5	8	0.08	0.4	E28 / 28X
MPN7302-H20	20	0.26	0.35	1.2	1.5	8	0.18	0.5	H20
MPN7302-0805-2	20	0.14	0.22	1.2	1.5	8	0.06	0.4	0805-2
MPN7304-E28 / 28X	40	0.14	0.22	2.2	2.7	15	0.08	0.4	E28 / 28X
MPN7304-H20	40	0.24	0.30	2.2	2.7	15	0.18	0.5	H20
MPN7304-0805-2	40	0.18	0.26	2.2	2.7	15	0.06	0.4	0805-2
MPN7304A-E28 / 28X	40	0.20	0.27	1.0	1.5	30	0.08	0.4	E28 / 28X
MPN7304A-H20	40	0.30	0.38	1.0	1.5	30	0.18	0.5	H20
MPN7304A-0805-2	40	0.18	0.23	1.0	1.5	30	0.06	0.4	0805-2
MPN7306-E28 / 28X	70	0.16	0.22	1.2	1.2	50	0.08	0.4	E28 / 28X
MPN7306-H20	70	0.26	0.33	1.2	1.2	50	0.18	0.5	H20
MPN7306-0805-2	70	0.14	0.20	1.2	1.2	50	0.06	0.4	0805-2
MPN7310-E28 / 28X	100	0.13	0.18	1.5	2.0	100	0.08	0.4	E28 / 28X
MPN7310-H20	100	0.23	0.29	1.5	2.0	100	0.18	0.5	H20
MPN7310-0805-2	100	0.11	0.17	1.5	2.0	100	0.06	0.4	0805-2
MPN7310A-E28 / 28X	100	0.26	0.36	0.6	1.0	200	0.08	0.4	E28 / 28X
MPN7310A-H20	100	0.36	0.57	0.6	1.0	200	0.18	0.5	H20
MPN7310A-0805-2	100	0.24	0.35	0.6	1.0	200	0.06	0.4	0805-2
MPN7312A-E28 / 28X	120	0.16	0.21	1.2*	1.5*	150	0.08	0.4	E28 / 28X
MPN7312A-H20	120	0.26	0.32	1.2*	1.5*	150	0.18	0.5	H20
MPN7312A-0805-2	120	0.14	0.20	1.2*	1.5*	150	0.06	0.4	0805-2
MPN7312B-E28 / 28X	120	0.26	0.36	0.8*	1.0*	250	0.08	0.4	E28 / 28X
MPN7312B-H20	120	0.36	0.57	0.8*	1.0*	250	0.18	0.5	H20
MPN7312B-0805-2	120	0.24	0.35	0.8*	1.0*	250	0.06	0.4	0805-2
MPN7315-E28 / 28X	150	0.16	0.23	1.2	1.5	180	0.08	0.4	E28 / 28X
MPN7315-H20	150	0.26	0.34	1.2	1.5	180	0.18	0.5	H20
MPN7315-0805-2	150	0.14	0.21	1.2	1.5	180	0.06	0.4	0805-2
MPN7320-E28 / 28X	150	0.10	0.14	3.0	4.0	120	0.08	0.4	E28 / 28X
MPN7320-H20	150	0.20	0.24	3.0	4.0	120	0.18	0.5	H20
MPN7320-0805-2	150	0.08	0.12	3.0	4.0	120	0.06	0.4	0805-2
Test Conditions	I _R = 10 μ A	V _R = 10 V F = 1 MHz		I _F = 10 mA * F = 100 MHz F = 1 GHz		I _F = 10 mA I _R = 6 mA			



0805-2



H20



E28



E28X

Silicon PIN Diodes

PIN Limiter Diodes

The MPN76XX series of PIN limiter diodes feature fully passivated, mesa construction with gold doping for low insertion loss and improved recovery. Available in seven I-layer and six mesa diameters for limiting thresholds from +7 dB to +23 dBm CW (P_{1dB}) and power handling up to +70 dBm pulsed ($1\mu s / 0.1\%$ DC). Available with screening per MIL-PRF-19500 and MIL-PRF-38534.

Chips

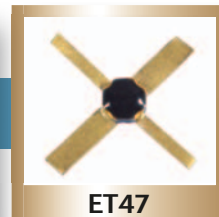
Model	V_{BR}		C_J MAX pF	R_s		τ TYP ns	I-layer NOM microns	Contact MIN mils	θ_{JC} MAX °C / W	Package
	MIN V	MAX V		TYP Ω	MAX Ω					
MPN7610	15	25	0.10	2.0	2.5	5	1	1.2	120	C11
MPN7610A	15	25	0.15	2.0	2.0	5	1	1.5	80	C11
MPN7620	20	45	0.15	1.5	2.0	5	2	1.5	100	C11
MPN7630	45	70	0.15	1.5	2.0	10	3	2.0	80	C12
MPN7640	75	100	0.15	1.5	2.0	30	4	2.5	60	C12
MPN7650	100	140	0.15	1.5	2.0	50	5	2.5	60	C12
MPN7670	120	160	0.15	1.5	2.0	80	7	3.0	40	C11
MPN7660	140	180	0.15*	1.5	2.0	100	10	3.0	40	C12
MPN7660A	140	180	0.50*	1.0	1.5	200	10	5.0	15	C12
Test Conditions	$I_R = 10 \mu A$		$V_R = 10 V$ * $V_R = 50 V$	$I_F = 10 mA$ $F = 1 GHz$		$I_F = 10 mA$ $I_R = 6 mA$				

Packaged

Model	V_{BR}		C_T MAX pF	R_s		τ TYP ns	I-layer NOM microns	Contact MIN mils	θ_{JC} MAX °C / W	Package
	MIN V	MAX V		TYP Ω	MAX Ω					
MPN7610-ET47	15	25	0.27	2.0	2.5	5	1	1.2	120	ET47
MPN7610-T55	15	25	0.27	2.0	2.5	5	1	1.2	120	T55
MPN7610A-ET47	15	25	0.33	2.0	2.0	5	1	1.5	80	ET47
MPN7610A-T55	15	25	0.33	2.0	2.0	5	1	1.5	80	T55
MPN7620-ET47	20	45	0.33	1.5	2.0	5	2	1.5	100	ET47
MPN7620-T55	20	45	0.33	1.5	2.0	5	2	1.5	100	T55
MPN7630-ET47	45	70	0.33	1.5	2.0	10	3	2.0	80	ET47
MPN7630-T55	45	70	0.33	1.5	2.0	10	3	2.0	80	T55
MPN7640-ET47	75	100	0.33	1.5	2.0	30	4	2.5	60	ET47
MPN7640-T55	75	100	0.33	1.5	2.0	30	4	2.5	60	T55
MPN7650-ET47	100	140	0.33	1.5	2.0	50	5	2.5	60	ET47
MPN7650-T55	100	140	0.33	1.5	2.0	50	5	2.5	60	T55
MPN7670-T55	120	160	0.33	1.5	2.0	80	7	3.0	40	T55
MPN7660-T55	140	180	0.33*	1.5	2.0	100	10	3.0	40	T55
MPN7660A-T55	140	180	0.33*	1.0	1.5	200	10	5.0	15	T55
Test Conditions	$I_R = 10 \mu A$		$V_R = 10 V$ * $V_R = 50 V$	$I_F = 10 mA$ $F = 1 GHz$		$I_F = 10 mA$ $I_R = 6 mA$				



C12



ET47



T55

Silicon PIN Diodes

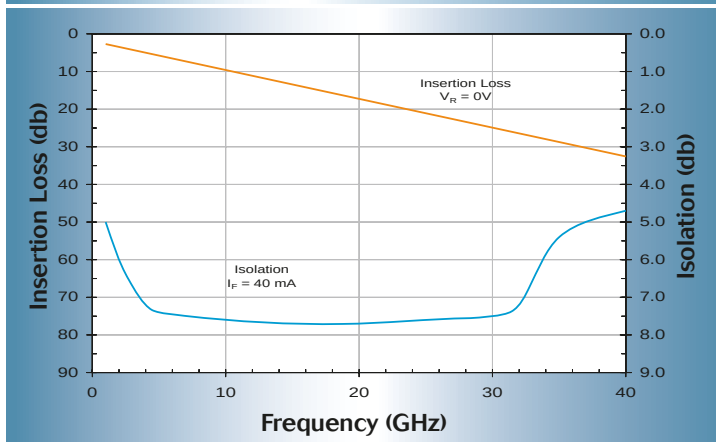
MicroStrip PIN Diodes

Aeroflex / Metelics MicroStrip PIN diode is designed as a 50 microstrip line when bias is at zero or at a negative bias. When forward biased the device is a reflective attenuator. Maximum isolation is achieved at 40mA forward bias.

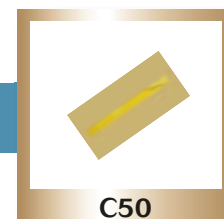
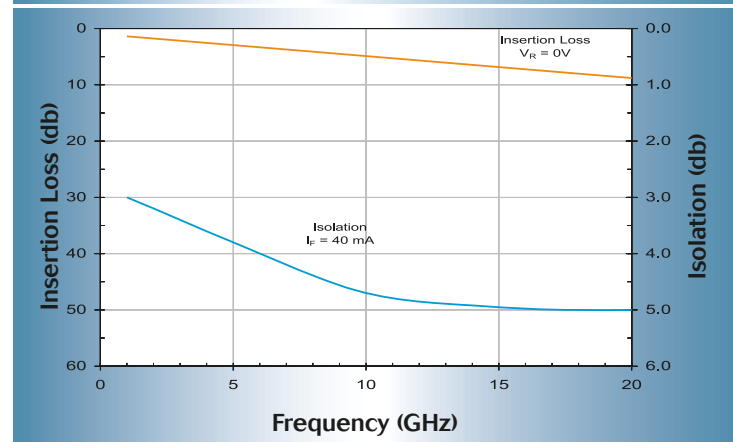
Chip

Model	Configuration	I_R MAX nA	V_{BR} MIN V	Insertion Loss MAX	Return Loss TYP	Isolation MIN	Package
MMPN-080150	MicroStrip PIN	100	200	4.0	12	-50	C51
MMPN-080045	MicroStrip PIN	100	200	1.0	12	-30	C50
Test Conditions		$V_R = 30\text{ V}$	$I_R = 10\text{ }\mu\text{A}$	$V_R = 30\text{ V}$ $F = 2 - 35\text{ GHz}$ $F = 2 - 20\text{ GHz}$		$I_F = 40\text{ mA}$ $F = 2 - 35\text{ GHz}$ $F = 2 - 20\text{ GHz}$	

MMPN-080150-C51 Insertion Loss & Isolation



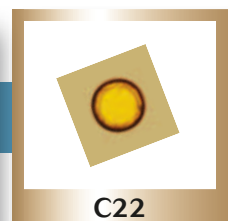
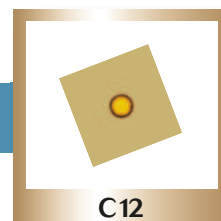
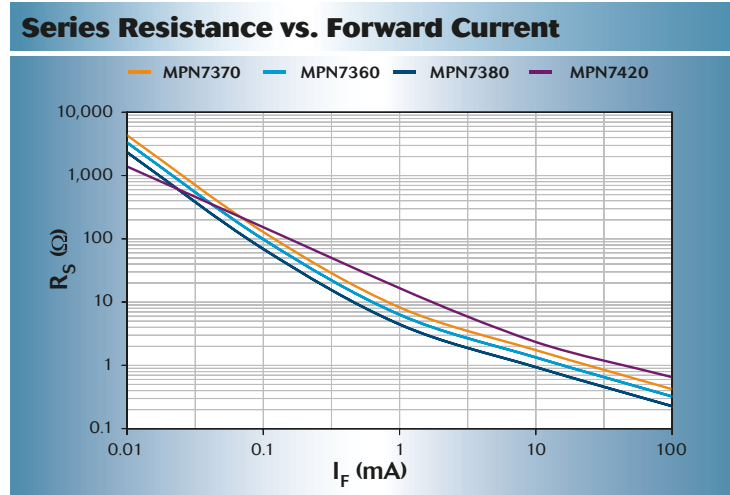
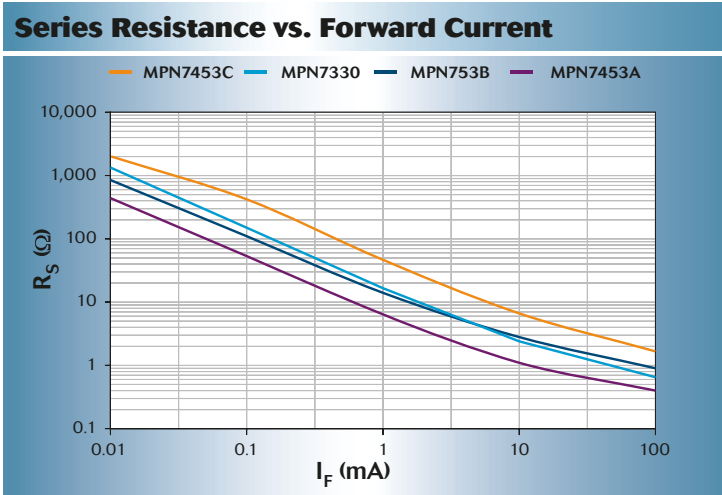
MMPN-080045-C50 Insertion Loss & Isolation



Silicon PIN Diodes

High Power Switching

Chips										
Model	V _{BR}	C _J		R _S		τ	I-layer	Contact	θ _{JC}	Package
	MIN V	TYP pF	MAX pF	TYP Ω	MAX Ω	TYP μs	NOM microns	MIN mils	MAX °C / W	
MPN7330	300	0.30	0.40	0.3	0.5	0.5	30	10	10	C40
MPN7345	300	0.30	0.40	0.3	0.5	0.5	45	10	10	C40
MPN7453A	300	0.10	0.15	0.7	1.0	0.7	60	8	20	C22
MPN7453B	400	0.15	0.2	0.6	0.9	2.5	60	8	20	C22
MPN7453C	300	0.18	0.25	0.4	0.7	1.0	60	8	15	C22
MPN7360	600	0.80	1.0	0.2	0.4	2.5	60	20	7	C37
MPN7370	700	2.00	2.3	0.2	0.3	5.0	70	40	5	C39
MPN7380	800	0.40	0.60	0.3	0.5	2.5	80	24	7	C38
MPN7420	400	0.06	0.08	1.0	1.5	1.0	100	5	30	C12
MPN73100	600	0.20	0.30	0.5	0.8	2.2	100	12	10	C32
MPN73120	700	0.30	0.40	0.5	0.8	3.5	120	15	10	C32
Test Conditions	I _R = 10 μA	V _R = 50 V F = 1 MHz		I _F = 100 mA F = 100 MHz		I _F = 10 mA I _R = 6 mA				



Silicon PIN Diodes

Glass Packaged

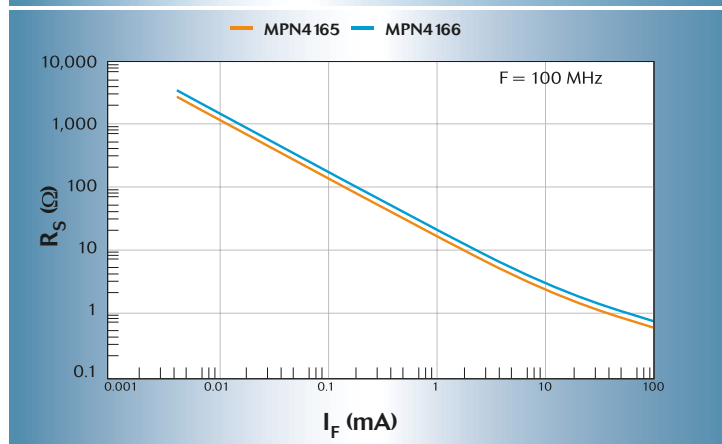
Switching

Model	V_{BR} MIN V	C_T		τ MIN ns	t_t TYP ns	R_s		Package
		TYP pF	MAX pF			TYP Ω	MAX Ω	
1N5719	150	0.25*	0.30*	100	100	1.0	1.25	A15
MPN3001	200	0.20	0.25	100	100	0.8	1.0	A15
MPN3002	300	0.20	0.25	100	100	0.8	1.0	A15
Test Conditions	$I_R = 10 \mu A$	$V_R = 50 V$ * $V_R = 100 V$ $F = 1 MHz$		$I_F = 250 mA$ $I_R = 50 mA$	$I_F = 20 mA$ $V_R = 10 V$	$I_F = 100 mA$ $F = 100 MHz$		

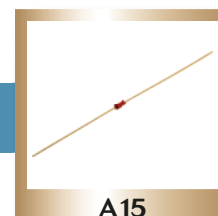
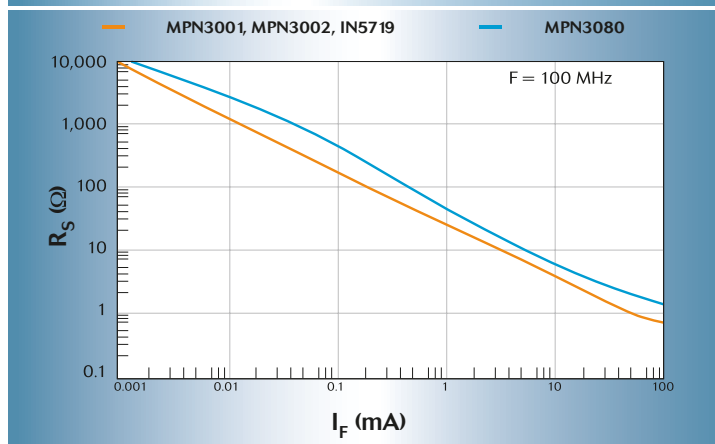
Attenuator

Model	V_{BR} MIN V	C_T MAX pF	τ MIN ns	R_s MAX pF	R_s		R_s		Package
					MIN Ω	MAX Ω	MIN Ω	MAX Ω	
MPN4165	100	0.30	100	1.5	1,100	1,660	16	24	A15
MPN4166	100	0.30	100	1.5	830	1,250	12	18	A15
MPN3080	100	0.40	2,000	2.5	1,000	---	---	8.0*	A15
MPN3081	100	0.40	2,500	3.5	1,500	---	---	8.0*	A15
1N5767	100	0.40	1,300	2.5	1,000	---	---	8.0*	A15
Test Conditions	$I_R = 10 \mu A$	$V_R = 50 V$ $F = 1 MHz$	$I_F = 100 mA$ $I_R = 50 mA$	$I_F = 100 mA$ $F = 100 MHz$	$I_F = 0.01 mA$ $F = 100 MHz$		$I_F = 1 mA$ * $I_F = 20 mA$ $F = 100 MHz$		

Series Resistance vs. Forward Current



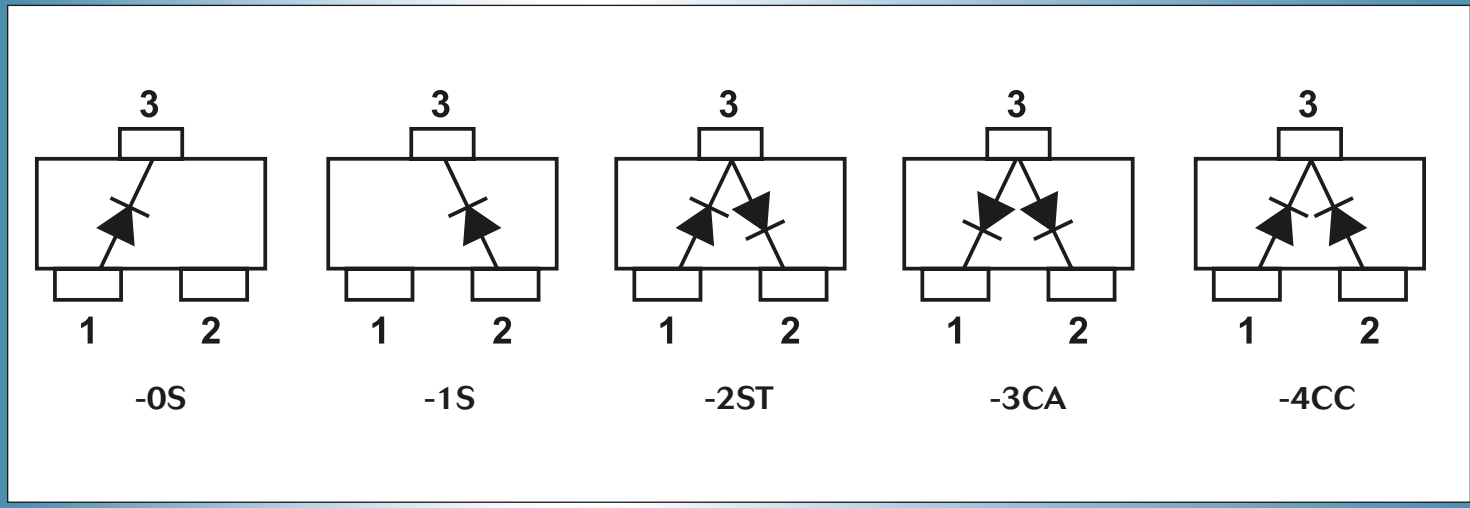
Series Resistance vs. Forward Current



Silicon PIN Diodes

Surface Mount Packages

Configuration Codes



SOT23 & SOD323

Model	Configuration	V _{BR} MIN V	C _T		R _s		τ TYP ns	Package
			TYP pF	MAX pF	TYP Ω	MAX Ω		
SMPN7453-SOT23	-0S, 1S, 2ST, 3CA, 4CC	200	0.25	0.35	4.0	4.5	2500	SOT23
SMPN7380-SOT23	-0S, 1S, 2ST, 3CA, 4CC	200	0.25	0.35	4.0	4.5	1500	SOT23
SMPN7310-SOT23	-0S, 1S, 2ST, 3CA, 4CC	100	0.40	0.50	0.60	1.2	120	SOT23
SMPN7316-SOT23	-0S, 1S, 2ST, 3CA, 4CC	100	0.25	0.55	0.60	1.0	200	SOT23
SMPN7335-SOT23	-0S, 1S, 2ST, 3CA, 4CC	200	0.30	0.40	1.50	2.0	500	SOT23
SMPN7320-SOT23	-0S, 1S, 2ST, 3CA, 4CC	100	0.20	0.30	2.00	4.5	170	SOT23
SMPN7453-SOD323	---	200	0.25	0.35	4.0	4.5	2500	SOD323
SMPN7380-SOD323	---	200	0.25	0.35	4.0	4.5	1500	SOD323
SMPN7310-SOD323	---	100	0.40	0.50	0.60	1.2	120	SOD323
SMPN7316-SOD323	---	100	0.25	0.55	0.60	1.0	200	SOD323
SMPN7335-SOD323	---	200	0.30	0.40	1.50	2.0	500	SOD323
SMPN7320-SOD323	---	100	0.20	0.30	2.00	4.5	170	SOD323
Test Conditions		I _R = 10 μA	V _R = 5 V _R = 10 V _R = 50		I _F = 10 mA F = 100 MHz		I _F = 10 mA I _R = 6 mA	



Silicon NIP Diodes

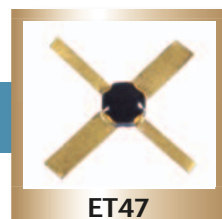
The MNP00XX series of NIP diodes are offered in four different I-layers and feature fully passivated, mesa construction for low leakage and reliability. Screening per MIL-PRF-19500 and MIL-PRF-3534 are available.

Chips

Model	V _{BR}	C _J		R _S		τ TYP ns	Contact MIN mils	I-Layer NOM microns	θ _{JC} MAX °C/W	Outline
	MIN V	TYP V	MAX pF	TYP Ω	MAX Ω					
MNP0008	100	0.08	0.12	2.0	2.5	150	2.0	10	50	C12P
MNP0010	150	0.08	0.12	2.0	2.5	300	3.0	20	50	C12P
MNP0012	300	0.08	0.12	3.5	4.0	350	4.0	40	40	C12P
MNP0012A	350	0.18	0.22	0.55	0.80	650	6.0	40	25	C22P
MNP0014	500	0.12	0.18	1.3	1.6	750	8.0	80	20	C22P
MNP0014A	500	0.18	0.22	0.8	1.2	1,400	10.0	80	10	C32P
Test Conditions	I _R = 10 μA		V _R = 10 V V _R = 50 V * F = 1 MHz		I _F = 10 mA I _F = 100 mA F = 1 GHz		I _F = 10 mA I _R = 6 mA 50% rec.			

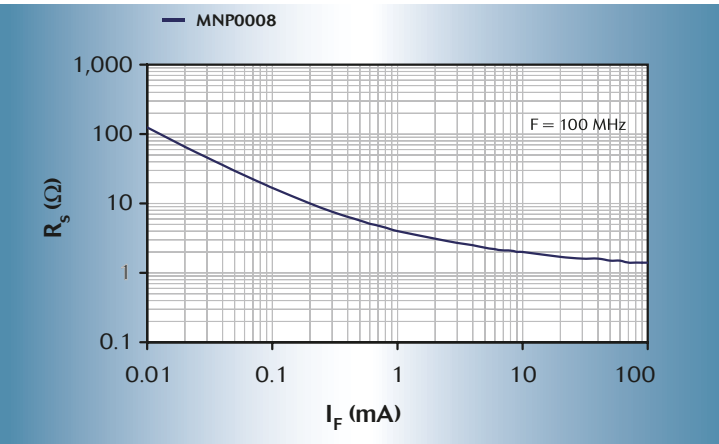
Packaged

Model	V _{BR}	C _T		R _S		τ	C _P	L _P	Outline
	MIN V	TYP pF	MAX pF	TYP Ω	MAX Ω	TYP ns	TYP pF	TYP nH	
MNP0008-ET47P	100	0.48	0.60	2.0	2.5	150	2 x 0.20	2 x 0.25	ET47P
MNP0008-T54P	100	0.28	0.37	2.0	2.5	150	0.20	0.4	T54P
MNP0008-T55P	100	0.21	0.29	2.0	2.5	150	.013	0.25	T55P
MNP0008-T89P	100	0.33	0.43	2.0	2.5	150	0.25	0.4	T89P
MNP0010-ET47P	150	.048	0.60	2.0	2.5	300	2 x 0.20	2 x 0.25	ET47P
MNP0010-T54P	150	0.28	0.37	2.0	2.5	300	0.20	0.4	T54P
MNP0010-T55P	150	0.21	0.29	2.0	2.5	300	.013	0.25	T55P
MNP0010-T89P	150	0.33	0.43	2.0	2.5	300	.025	0.4	T89P
MNP0012-ET47P	300	0.48	0.60	3.5	4.0	350	2 x 0.20	2 x 0.25	ET47P
MNP0012-T54P	300	0.28	0.37	3.5	4.0	350	0.20	0.4	T54P
MNP0012-T55P	300	0.21	0.29	3.5	4.0	350	0.13	0.25	T55P
MNP0012-T89P	300	0.33	0.43	3.5	4.0	350	0.25	0.4	T89P
MNP0012A-ET47P	350	0.58	0.72	0.55	0.8	650	2 x 0.20	2 x 0.25	ET47P
MNP0012A-T54P	350	0.36	0.47	0.55	0.8	650	0.20	0.4	T54P
MNP0012A-T55P	350	0.31	0.39	0.55	0.8	650	0.13	0.25	T55P
MNP0012A-T89P	350	0.43	0.53	0.55	0.8	650	0.25	0.4	T89P
MNP0014-ET47P	450	0.52	0.58	0.8	1.2	750	2 x 0.20	2 x 0.25	ET47P
MNP0014-T54P	450	0.32	0.48	0.8	1.2	750	0.20	0.4	T54P
MNP0014-T55P	450	0.25	0.35	0.8	1.2	750	0.13	0.25	T55P
MNP0014-T89P	450	0.37	0.50	0.8	1.2	750	0.25	0.4	T89P
Test Conditions	I _R = 10 μA	V _R = 10 V V _R = 50 V * F = 1 MHz		I _F = 10 mA I _F = 100 mA F = 1 GHz		I _F = 10 mA I _R = 6 mA 50% rec.			

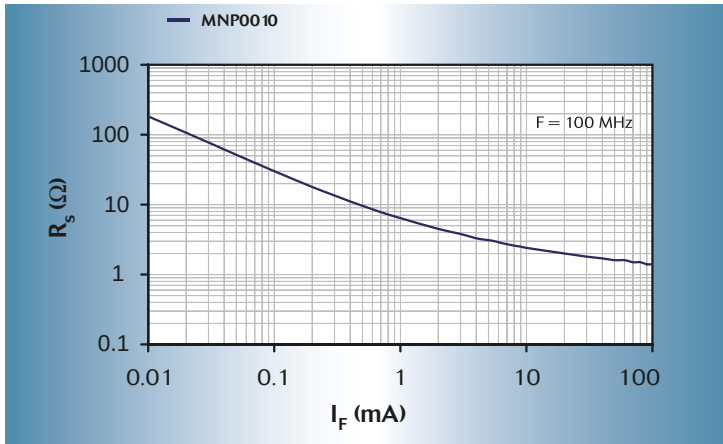


Silicon NIP Diodes

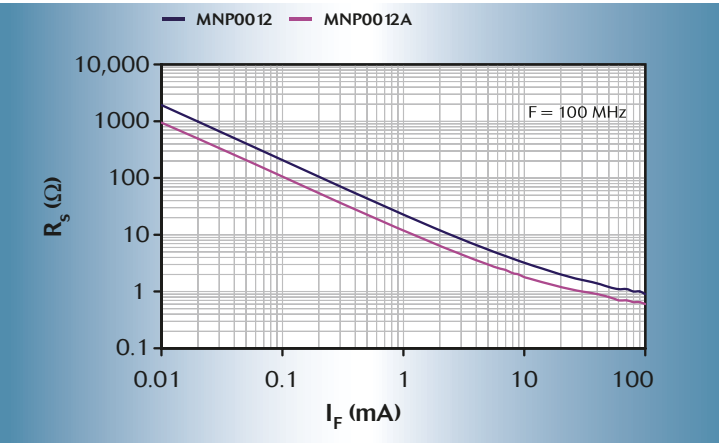
Series Resistance vs. Forward Current



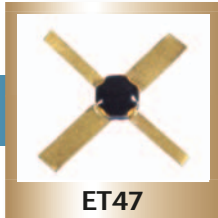
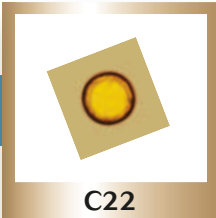
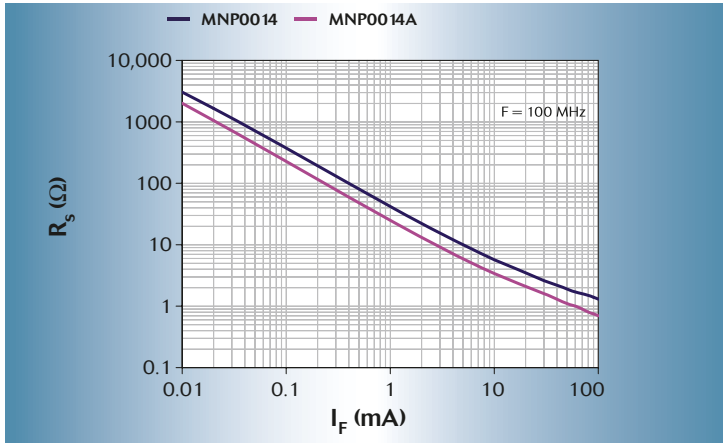
Series Resistance vs. Forward Current



Series Resistance vs. Forward Current



Series Resistance vs. Forward Current



Silicon Step Recovery Diodes

The diodes feature fully passivated, true mesa construction for sharp transitions and improved stability. The Beam lead SRDs have the industry's fastest transition times for millimeter wave multiplication and pico second pulse forming.

Chip and Beam Lead

Model	V_{BR} MIN V	C_J		τ		t_t		F_{CO} TYP GHz	θ_{JC} MAX °C/W	Package
		MIN pF	MAX pF	MIN ns	TYP ns	TYP ps	MAX ps			
MMDB30-B11	14	0.15	0.25	1.0	4.0	30	38	530	600	B11
MMDB35-B11	16	0.13	0.20	1.0	4.0	35	45	482	600	B11
MMDB45-B11	25	0.11	0.20	3.0	8.0	45	58	410	600	B11
MMD805-C12	60	2.5	3.5	80	100	250	300	130	15	C12
MMD810-C12	50	1.5	2.5	40	70	200	250	200	22	C12
MMD820-C12	40	1.0	1.7	30	60	80	100	390	25	C12
MMD830-C11	25	0.5	1.0	15	30	60	80	700	45	C11
MMD832-C11	20	0.4	0.8	10	15	60	80	660	50	C11
MMD835-C11	15	0.3	0.7	10	20	60	70	800	60	C11
MMD837-C11	20	0.2	0.4	5	10	60	70	1,300	60	C11
MMD840-C11	15	0.2	0.4	7	15	60	70	880	60	C11
Test Conditions	$I_R = 10 \mu A$	$V_R = 6 V$ $F = 1 \text{ MHz}$		$I_F = 10 \text{ mA}$ $I_R = 6 \text{ mA}$ Measured at 50% Recovery		$I_F = 3 \text{ mA}$ $V_R = 7 V$ $I_F = 10 \text{ mA}$ $V_R = 10 V$		$F_{CO} = 1 / 2\pi R_S$		

Glass Packaged

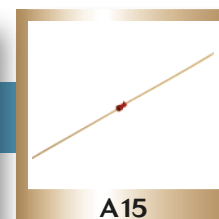
Model	V_{BR} MIN V	C_J	C_T	τ		t_t		C_P TYP pF	L_P TYP nH	Package
		MAX pF	TYP pF	MIN ns	TYP ns	TYP ps	MAX ps			
MMD0151	15	0.65	0.55	10	15	100	---	0.15	2.5	A15
MMD0153	25	0.40	0.40	10	15	95	---	0.15	2.5	A15
MMD0803	70	6.0	4.0	200	250	275	400	0.15	2.5	A15
MMD0815	50	4.0	3.0	100	135	180	320	0.15	2.5	A15
MMD0825	45	2.0	1.0	30	50	130	160	0.15	2.5	A15
MMD0833	25	1.6	1.65	10	15	90	---	0.15	2.5	A15
MMD0840	15	0.60	0.60	10	20	75	---	0.15	2.5	A15
Test Conditions	$I_R = 10 \mu A$	$V_R = 6 V$ $V_R = 10 V$ $F = 1 \text{ MHz}$		$I_F = 10 \text{ mA}$ $I_R = 6 \text{ mA}$ Measured at 50% Recovery		$I_F = 10 \text{ mA}$ $V_R = 10 V$ Chip data, package limited to 100 ps		$F = 1 \text{ MHz}$		



B11



C12

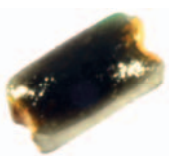


A15

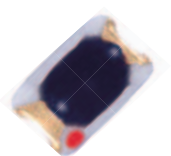
Silicon Step Recovery Diodes

Ceramic Packaged

Model	V _{BR} MIN V	C _T		τ		t _t		C _P TYP pF	L _P TYP nH	Package
		MIN pF	MAX pF	MIN ns	TYP ns	TYP ps	MAX ps			
MMD805-E28 / 28X	60	3.1	3.6	80	100	250	300	0.08	0.4	E28 / 28X
MMD805-H20	60	3.2	3.7	80	100	250	300	0.18	0.5	H20
MMD805-T86	60	3.2	3.7	80	100	250	300	0.18	1.0	T86
MMD805-T89	60	3.3	3.8	80	100	250	300	0.25	0.4	T89
MMD805-0805-2	60	3.1	3.6	80	100	250	300	0.06	0.4	0805-2
MMD810-E28 / 28X	50	2.1	2.6	40	70	200	250	0.08	0.4	E28 / 28X
MMD810-H20	50	2.2	2.7	40	70	200	250	0.18	0.5	H20
MMD810-T86	50	2.2	2.7	40	70	200	250	0.18	1.0	T86
MMD810-T89	50	2.3	2.8	40	70	200	250	0.25	0.4	T89
MMD820-E28 / 28X	40	1.4	1.8	30	60	80	100	0.08	0.4	E28 / 28X
MMD820-H20	40	1.5	1.9	30	60	80	100	0.18	0.5	H20
MMD820-T86	40	1.5	1.9	30	60	80	100	0.18	1.0	T86
MMD820-0805-2	40	1.4	1.8	30	60	80	100	0.06	0.4	805-2
MMD830-E28 / 28X	25	0.83	1.1	15	30	60	80	0.08	0.4	E28 / 28X
MMD830-H20	25	0.93	1.2	15	30	60	80	0.18	0.5	H20
MMD830-T86	25	0.93	1.2	15	30	60	80	0.18	1.0	T86
MMD830-0805-2	25	0.81	1.1	15	30	60	80	0.06	0.4	805-2
MMD832-E28 / 28X	20	0.68	0.9	10	15	60	80	0.08	0.4	E28 / 28X
MMD832-H20	20	0.78	1.0	10	15	60	80	0.18	0.5	H20
MMD832-T86	20	0.78	1.0	10	15	60	80	0.18	1.0	T86
MMD832-0805-2	20	0.66	0.88	10	15	60	80	0.06	0.4	805-2
MMD835-E28 / 28X	15	0.58	0.81	10	20	50	70	0.08	0.4	E28 / 28X
MMD835-H20	15	0.62	0.85	10	20	50	70	0.12	0.4	H27
MMD835-T86	15	0.68	0.91	10	20	50	70	0.18	1.0	T86
MMD835-0805-2	15	0.56	0.78	10	20	50	70	0.06	0.4	805-2
MMD837-E28 / 28X	20	0.38	0.51	5	10	50	70	0.08	0.4	E28 / 28X
MMD837-H27	20	0.42	0.55	5	10	50	70	0.12	0.4	H27
MMD837-T86	20	0.48	0.61	5	10	50	70	0.18	1.0	T86
MMD837-0805-2	20	0.36	0.48	5	10	50	70	0.06	0.4	805-2
MMD840-E28 / 28X	15	0.38	0.51	7	15	50	70	0.08	0.4	E28 / 28X
MMD840-H27	15	0.42	0.55	7	15	50	70	0.12	0.4	H27
MMD840-T86	15	0.48	0.61	7	15	50	70	0.18	1.0	T86
MMD840-0805-2	15	0.36	0.48	7	15	50	70	0.06	0.4	0805-2
MMDB30-E28 / 28X	14	0.28	0.36	1.0	4.0	30*	38*	0.08	0.4	E28 / 28X
MMDB30-0402	14	0.25	0.32	1.0	4.0	30*	38*	0.05	0.2	0402
MMDB30-0805-2	14	0.26	0.33	1.0	4.0	30*	38*	0.06	0.4	0805-2
MMDB35-E28 / 28X	16	0.25	0.31	1.0	4.0	35*	45*	0.08	0.4	E28 / 28X
MMDB35-0402	16	0.22	0.28	1.0	4.0	35*	45*	0.05	0.2	0402
MMDB35-0805-2	16	0.23	0.29	1.0	4.0	35*	45*	0.06	0.4	0805-2
MMDB45-E28 / 28X	25	0.24	0.31	3.0	8.0	45*	58*	0.08	0.4	E28 / 28X
MMDB45-0402	25	0.21	0.28	3.0	8.0	45*	58*	0.05	0.2	0402
MMDB45-0805-2	25	0.22	0.29	3.0	8.0	45*	58*	0.06	0.4	0805-2
Test Conditions		I _R = 10 μ A		V _R = 6 V F = 1 MHz		I _F = 10 mA I _R = 6 mA Measured at 50% Recovery		I _F = 10 mA V _R = 10 V *I _F = 3 mA *V _R = 7 V		



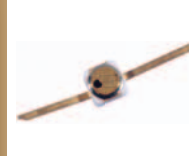
0402



0805-2



E28



H20



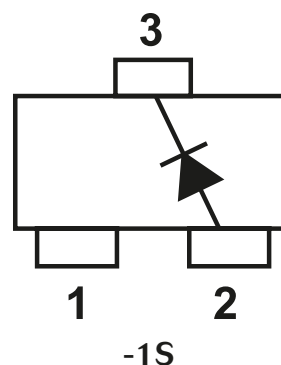
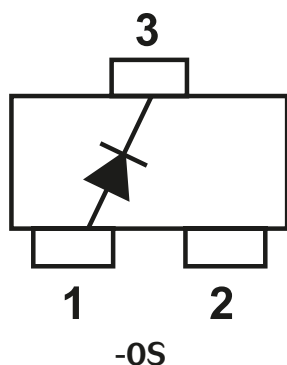
T86



T89

Silicon Step Recovery Diodes

Configuration Codes



Plastic Packaged

Model	Configuration	V _{BR} MIN V	C _T		τ		t _t		Package
			TYP pF	MAX pF	MIN ns	TYP ns	TYP ps	MAX ps	
SMMD805-SOT23	-0S, 1S	60	2.5	3.5	80	100	250	300	SOT23
SMMD810-SOT23	-0S, 1S	50	1.5	2.5	40	70	200	250	SOT23
SMMD820-SOT23	-0S, 1S	40	1.0	1.7	30	60	110	125	SOT23
SMMD830-SOT23	-0S, 1S	25	0.5	1.0	15	30	90	110	SOT23
SMMD832-SOT23	-0S, 1S	20	0.4	0.8	10	20	85	100	SOT23
SMMD835-SOT23	-0S, 1S	20	0.3	0.7	10	15	80	100	SOT23
SMMD837-SOT23	-0S, 1S	20	0.2	0.4	5	12	75	90	SOT23
SMMD840-SOT23	-0S, 1S	15	0.2	0.4	5	10	70	90	SOT23
SMMD805-SOD323	---	60	2.5	3.5	80	100	250	300	SOD323
SMMD810-SOD323	---	50	1.5	2.5	40	70	200	250	SOD323
SMMD820-SOD323	---	40	1.0	1.7	30	60	110	125	SOD323
SMMD830-SOD323	---	25	0.5	1.0	15	30	90	110	SOD323
SMMD832-SOD323	---	20	0.4	0.8	10	20	85	100	SOD323
SMMD835-SOD323	---	20	0.3	0.7	10	15	80	100	SOD323
SMMD837-SOD323	---	20	0.2	0.4	5	12	75	90	SOD323
SMMD840-SOD323	---	15	0.2	0.4	5	10	70	90	SOD323
Test Conditions		I _R = 10 μ A	V _R = 6 V F = 1 MHz		I _F = 10 mA I _R = 6 mA 50% Recovery		I _F = 10 mA V _R = 10 V		



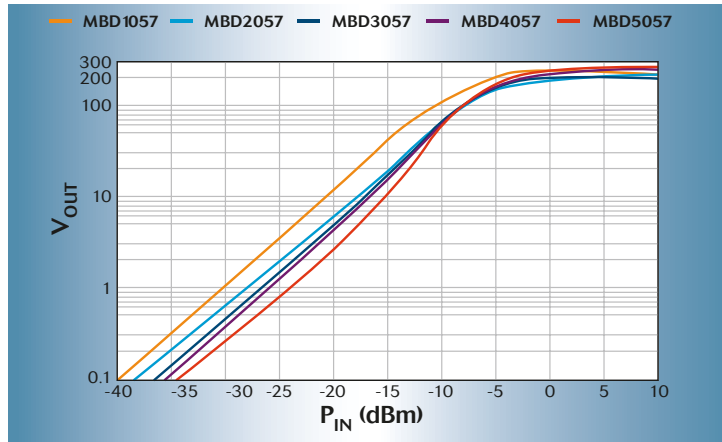
Planar Back (Tunnel) Diodes

The MBD series of tunnel (back) diodes are fabricated on germanium substrates with passivated, planar construction and all gold metallization for reliable operation up to +115 °C. Unlike the standard tunnel diode I_p is minimized for detector operation and binned in five values offering varying degrees of sensitivity and video impedance. The back detector is generally operated with zero bias and is known for its excellent temperature stability and fast video rise times.

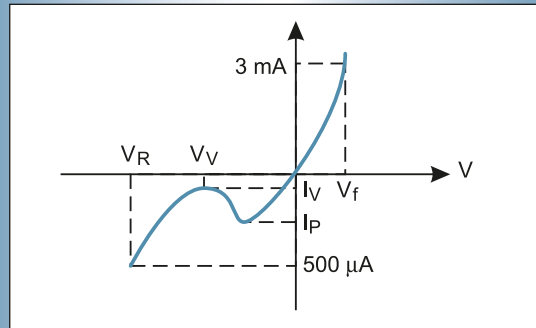
Chips

Model	I_p		C_j	γ	R_v	I_p / I_v	V_R	V_F	Package
	MIN μA	MAX pF							
MBD1057-C18	100	200	0.30	1,000	180	2.5	420	135	C18
MBD2057-C18	200	300	0.30	750	130	2.5	410	130	C18
MBD3057-C18	300	400	0.30	500	80	2.5	400	125	C18
MBD4057-C18	400	500	0.30	275	65	2.5	400	120	C18
MBD5057-C18	500	600	0.30	250	60	2.5	400	110	C18
Test Conditions			$V_R = V_V$ $F = 100 \text{ MHz}$	$P_{IN} = -20 \text{ dBm}$ $R_L = 10 \text{ K}\Omega \quad F = 10 \text{ GHz}$			$I_R = 500 \mu A$	$I_F = 3 \text{ mA}$	

Detected Output vs. RF Input Power



Back Diode Paramaters



BOTTOM METALIZATION IS CATHODE
BONDING PAD IS ANODE



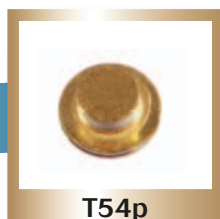
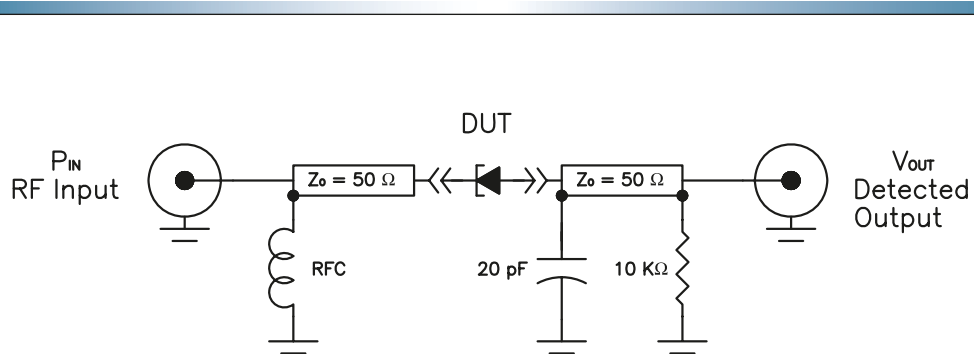
C18

Planar Back (Tunnel) Diodes

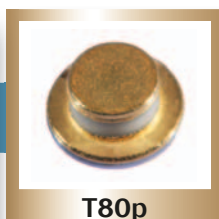
Packaged

Model	I_P		C_T MAX pF	γ TYP mV / mW	R_V TYP Ω	I_P / I_V MIN	V_R MIN mV	V_F MAX mV	Package
	MIN μA	MAX pF							
MBD1057-E28 / 28X	100	200	0.40	1,000	180	2.5	420	135	E28 / 28X
MBD1057-H20	100	200	0.50	1,000	180	2.5	420	135	H20
MBD1057-T54	100	200	0.55	1,000	180	2.5	420	135	T54p
MBD1057-T80	100	200	0.65	1,000	180	2.5	420	135	T80p
MBD2057-E28 / 28X	200	300	0.40	750	130	2.5	410	130	E28 / 28X
MBD2057-H20	200	300	0.50	750	130	2.5	410	130	H20
MBD2057-T54	200	300	0.55	750	130	2.5	410	130	T54p
MBD2057-T80	200	300	0.65	750	130	2.5	410	130	T80p
MBD3057-E28 / 28X	300	400	0.45	500	80	2.5	400	125	E28 / 28X
MBD3057-H20	300	400	0.55	500	80	2.5	400	125	H20
MBD3057-T54	300	400	0.60	500	80	2.5	400	125	T54p
MBD3057-T80	300	400	0.70	500	80	2.5	400	125	T80p
MBD4057-E28 / 28X	400	500	0.50	275	65	2.5	400	120	E28 / 28X
MBD4057-H20	400	500	0.60	275	65	2.5	400	120	H20
MBD4057-T54	400	500	0.65	275	65	2.5	400	120	T54p
MBD4057-T80	400	500	0.75	275	65	2.5	400	120	T80p
MBD5057-E28 / 28X	500	600	0.55	250	60	2.5	400	110	E28 / 28X
MBD5057-H20	500	600	0.65	250	60	2.5	400	110	H20
MBD5057-T54	500	600	0.70	250	60	2.5	400	110	T54p
MBD5057-T80	500	600	0.80	250	60	2.5	400	110	T80p
Test Conditions			$V_R = V_V$ $F = 30 \text{ MHz}$		$P_{IN} = -20 \text{ dBm}$ $R_L = 10 \text{ K}\Omega \quad F = 10 \text{ GHz}$		$I_R =$ 500 μA	$I_F = 3 \text{ mA}$	

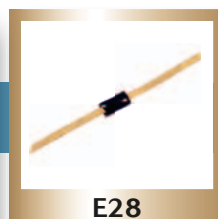
10 GHz RF Detector Test Circuit



T54p



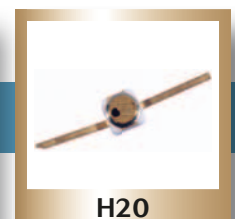
T80p



E28



E28X



H20

MIS / MOS Capacitors

Aeroflex / Metelics MIS capacitors utilize a silicon nitride dielectric over a thermally grown silicon dioxide base. The resultant composite dielectric exhibits low leakage current and insertion loss with excellent long-term stability. The temperature coefficient of capacitance is typically +55 ppm / °C.

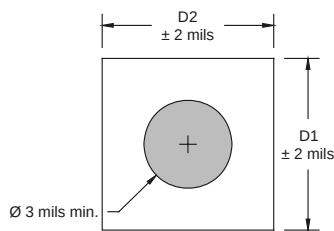
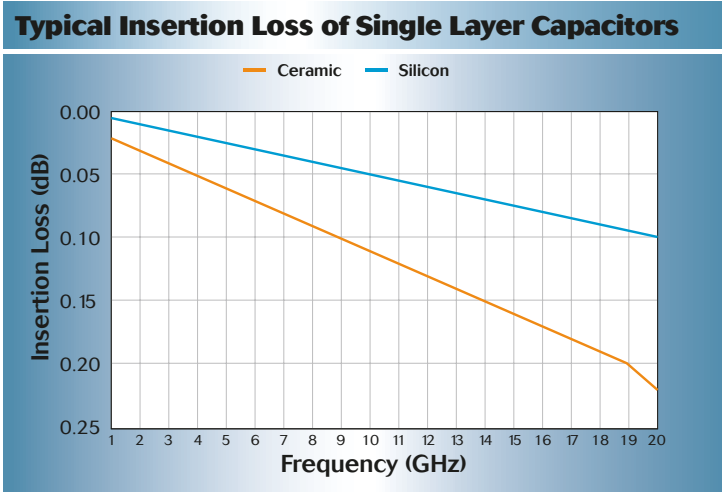


Figure 1

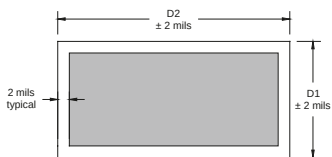


Figure 2

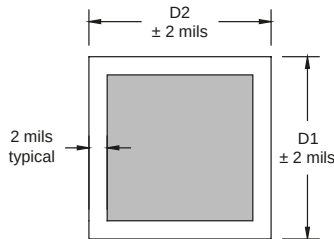


Figure 3

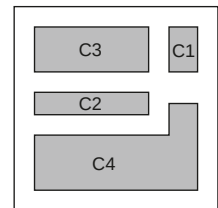


Figure 4

Chips - Figure 1 (xxx = Three digit capacitance code, ex. 005 = 5 pF, 082 = 82 pF, 1.5 = 1.5 pF)

Model	Capacitance Range		DWV	IR	T _{cc}	Dimensions	
	MIN pF	MAX pF	MIN V	MIN MΩ	TYP ppm / °C	D1 mils	D2 mils
MC2Dxxx010-010	0.10	5.0	50	1,000	+55	10	10
MC2Dxxx015-015	1.5	15	50	1,000	+55	15	15
MC2Dxxx020-020	5.0	50	50	1,000	+55	20	20
Test Conditions	F = 1 MHz			V = 25 V	-55 °C to +200 °C		



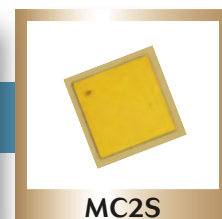
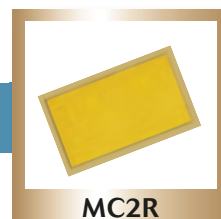
MIS / MOS Capacitors

Chips - Figure 2 (xxx = Three or four digit capacitance code, ex. 005 = 5 pF, 082 = 82 pF, 2.5 = 2.5 pF)

Model	Capacitance Range		DWV	IR	T _{cc}	Dimensions	
	MIN pF	MAX pF	MIN V	MIN MΩ	TYP ppm / °C	D1 mils	D2 mils
MC2Rxxx010-015	2.0	20	50	1,000	+55	10	15
MC2Rxxx015-020	5.0	42	50	1,000	+55	15	20
MC2Rxxx015-032	5.0	62	50	1,000	+55	15	32
MC2Rxxx022-042	15	120	50	1,000	+55	22	42
MC2Rxxx097-107	100	999	50	1,000	+55	97	107
MC2Rxxx099-138	100	999	50	1,000	+55	99	138
MC2Rxxxx127-145	200	1,800	50	1,000	+55	127	145
MC2Rxxxx142-160	200	2,200	50	1,000	+55	142	160
Test Conditions	F = 1 MHz			V = 25 V	-55 °C to +200 °C		

Chips - Figure 3 (xxx = Three digit capacitance code, ex. 005 = 5 pF, 082 = 82 pF)

Model	Capacitance Range		DWV	IR	T _{cc}	Dimensions	
	MIN pF	MAX pF	MIN V	MIN MΩ	TYP ppm / °C	D1 mils	D2 mils
MC2Sxxx010-010	0.25	8.0	50	1,000	+55	10	10
MC2Sxxx011-011	1.0	12	50	1,000	+55	11	11
MC2Sxxx015-015	3.0	30	50	1,000	+55	15	15
MC2Sxxx016-016	3.0	35	50	1,000	+55	16	16
MC2Sxxx020-020	5.0	55	50	1,000	+55	20	20
MC2Sxxx022-022	5.0	60	50	1,000	+55	22	22
MC2Sxxx025-025	10	100	50	1,000	+55	25	25
MC2Sxxx030-030	10	120	50	1,000	+55	30	30
MC2Sxxx035-035	15	150	50	1,000	+55	35	35
MC2Sxxx040-040	20	200	50	1,000	+55	40	40
MC2Sxxx050-050	25	250	50	1,000	+55	50	50
MC2Sxxx055-055	25	300	50	1,000	+55	55	55
MC2Sxxx060-060	35	375	50	1,000	+55	60	60
MC2Sxxx070-070	50	550	50	1,000	+55	70	70
MC2Sxxx080-080	70	700	50	1,000	+55	80	80
MC2Sxxx100-100	100	999	50	1,000	+55	100	100
Test Conditions	F = 1 MHz			V = 25 V	-55 °C to +200 °C		



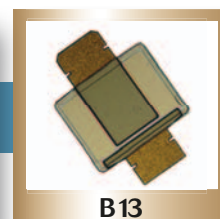
MIS / MOS Capacitors

Binary Chips - Figure 4

Model	Capacitance Range					DWV MIN V	IR MIN MΩ	T _{cc} TYP ppm / °C	Package
	C _T ±20% pF	C1 NOM pF	C2 NOM pF	C3 NOM pF	C4 NOM pF				
MC2B0.8020-020	1.5	0.1	0.2	0.4	0.8	50	1,000	+55	C20
MC2B002020-020	3.75	0.25	0.5	1.0	2.0	50	1,000	+55	C20
MC2B004020-020	8.0	0.5	1.0	2.0	4.0	50	1,000	+55	C20
MC2B008020-020	15	1.0	2.0	4.0	8.0	50	1,000	+55	C20
MC2B016020-020	30	2.0	4.0	8.0	16	50	1,000	+55	C20
Test Conditions	F = 1 MHz						V = 25 V	-55 °C to +200 °C	

Beam Lead

Model	C _T ±20% pF	DWV MIN V	IR MIN mΩ	T _{cc} TYP ppm / °C	Package
MBC50-1B12	1.0	50	1,000	+55	B12
MBC50-2B12	2.0	50	1,000	+55	B12
MBC50-3B12	3.0	50	1,000	+55	B12
MBC50-4B12	4.0	50	1,000	+55	B12
MBC50-6B12	6.0	50	1,000	+55	B12
MBC50-8B12	8.0	50	1,000	+55	B12
MBC50-10B12	10	50	1,000	+55	B12
MBC50-15B12	15	50	1,000	+55	B12
MBC50-20B12	20	50	1,000	+55	B12
MBC50-33B13	33	50	1,000	+55	B13
MBC50-47B13	47	50	1,000	+55	B13
MBC50-68B13	68	50	1,000	+55	B13
MBC50-82B13	82	50	1,000	+55	B13
MBC50-100B13	100	50	1,000	+55	B13
MBC50-0.2B14	0.2	50	1,000	+55	B14
MBC50-1.0B14	1.0	50	1,000	+55	B14
MBC50-1.5B14	1.5	50	1,000	+55	B14
MBC50-2.0B14	2.0	50	1,000	+55	B14
Test Conditions	F = 1 MHz		V = 25 V	-55 °C to +200 °C	



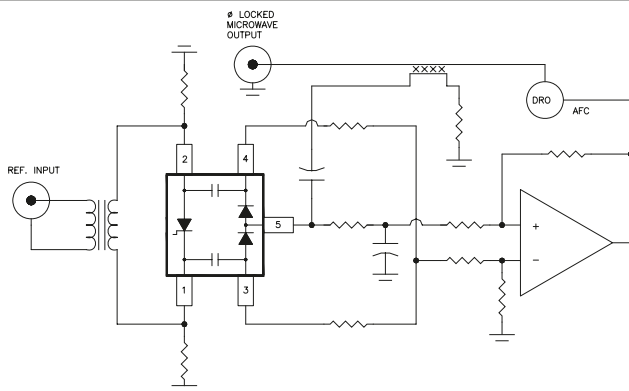
Sampling Phase Detector

The MSPD Series Integrates an SRD reference frequency multiplier, coupling capacitors and a Schottky diode microwave sampler / phase detector in a 0.075" by 0.100" hybrid. They are used to phase lock microwave oscillators up to 20 GHz to a much lower frequency reference by deriving a locking voltage from the sampled RF and the multiplied reference.

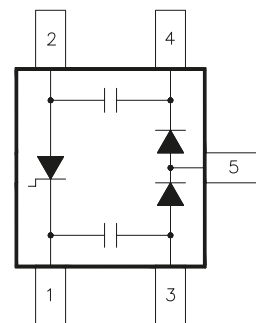
Packaged

Model	Step Recovery Diode				Cap.	Schottky Diode			F_{MAX} TYP GHz	Package
	V_{BR} MIN V	C_J TYP pF	τ TYP ns	t_t MAX ps	C_T NOM pF	C_J TYP pF	V_F TYP mV	R_D TYP Ω		
MSPD1000-E50 / E50SM	15	1.0	35	95	20	0.4	270	7.0	0.50	E50 / E50SM
MSPD1000-H50	15	1.0	35	95	20	0.4	270	7.0	0.50	H50
MSPD1002-E50 / E50SM	15	0.5	20	70	3.5	0.22	270	8.0	2.0	E50 / E50SM
MSPD1002-H50	15	0.5	20	70	3.5	0.22	270	8.0	2.0	H50
MSPD1012-E50 / E50SM	15	0.5	10	70	2.5	0.18	270	9.0	12	E50 / E50SM
MSPD1012-H50	15	0.5	10	70	2.5	0.18	270	9.0	12	H50
MSPD2018-E50 / E50SM	15	0.35	5	55	0.6	0.10	430	16.0	22	E50 / E50SM
MSPD2018-H50	15	0.35	5	55	0.6	0.10	430	16.0	22	H50
Test Conditions	$I_R = 10 \mu A$	$V_R = 6 V$ $F = 1 MHz$	$I_F = 10 mA$ $I_R = 6 mA$	$I_F = 10 mA$ $V_R = 10 V$	$F = 1 MHz$	$V_R = 0 V$ $F = 1 MHz$	$I_R = 1 mA$	$I_R = 5 mA$		

Typical Circuit Application



Schematic



E50



E50SM



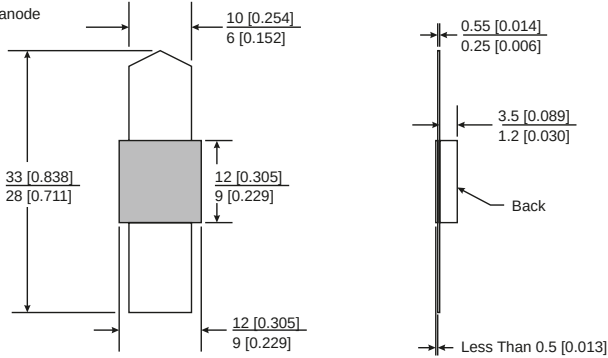
H50

Outline Drawings

Beam Lead

B10B

Cut lead is anode

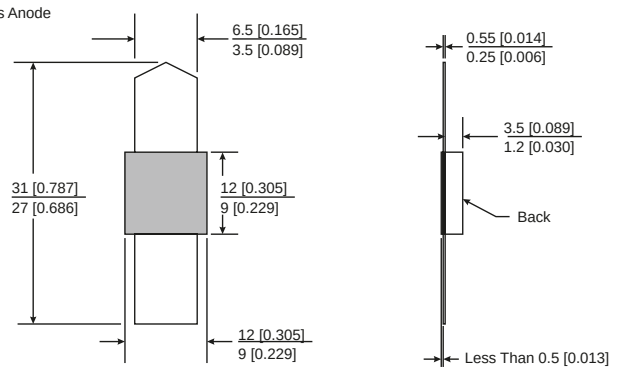


Back View

mils (mm)

B10D

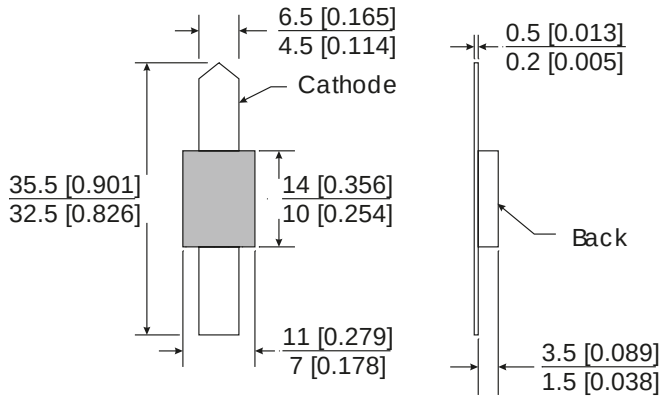
Cut lead is Anode



Back View

mils (mm)

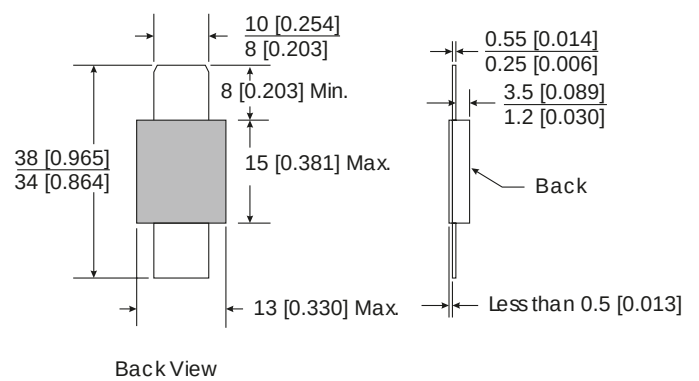
B11



Back View

mils (mm)

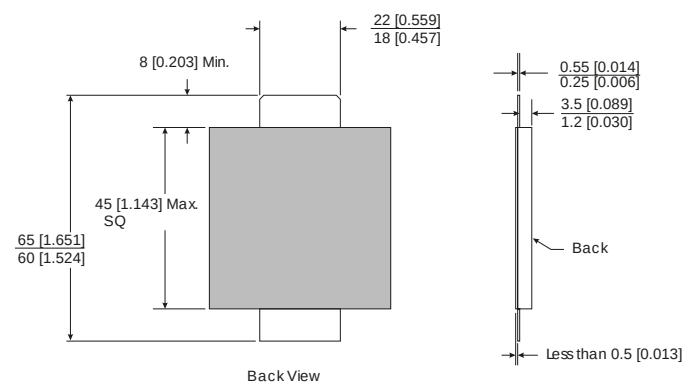
B12



Back View

mils (mm)

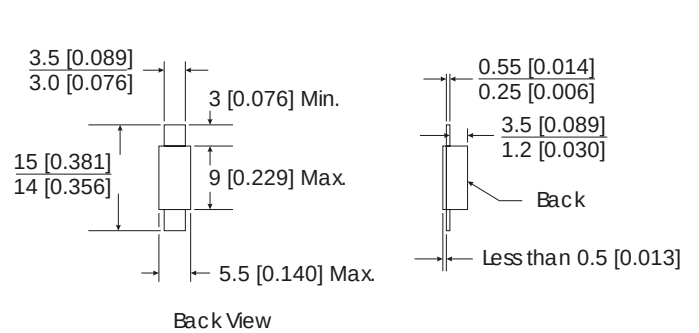
B13



Back View

mils (mm)

B14



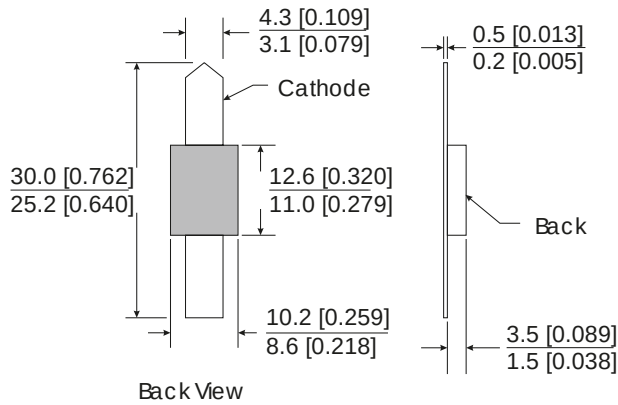
Back View

mils (mm)

Outline Drawings

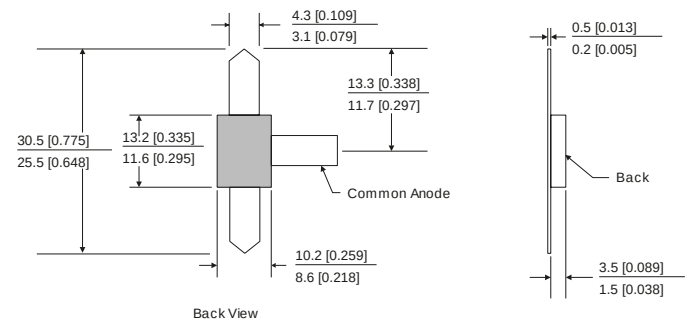
Beam Lead

B15



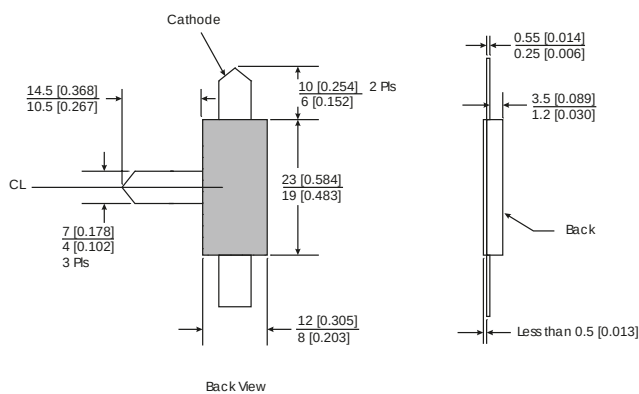
mils (mm)

B16



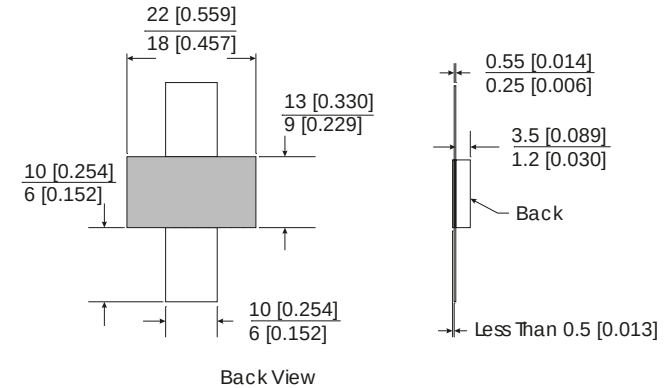
mils (mm)

B20



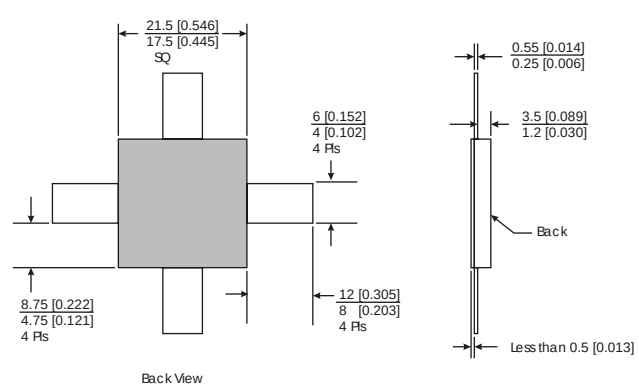
mils (mm)

B21



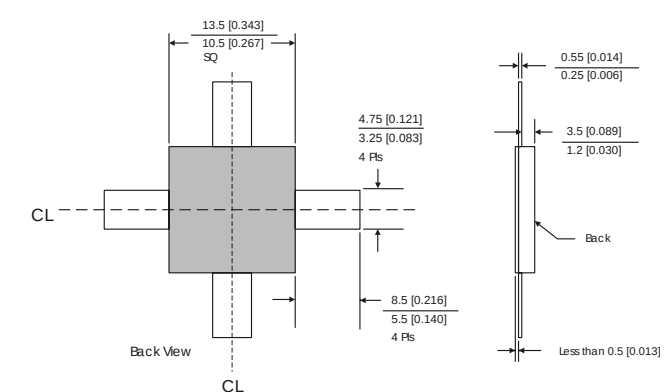
mils (mm)

B40



mils (mm)

B41

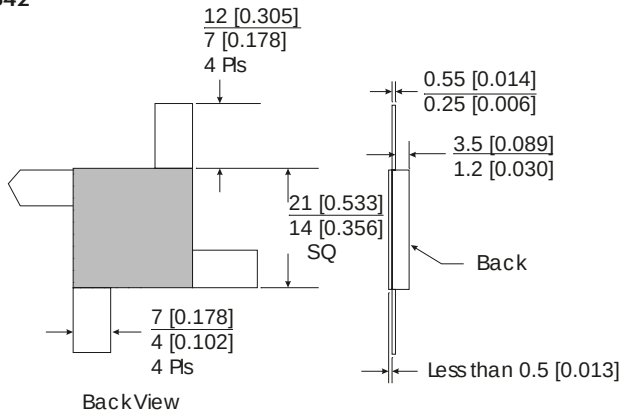


mils (mm)

Outline Drawings

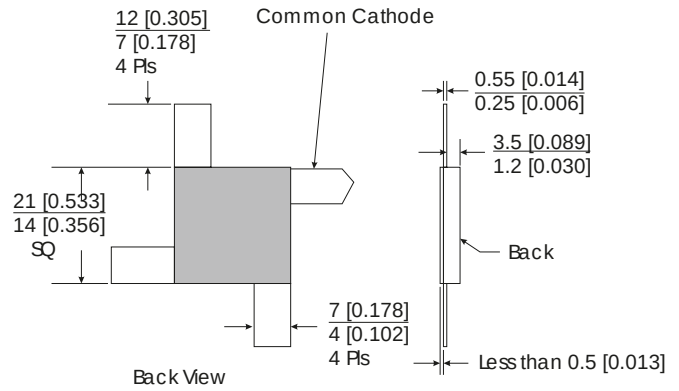
Beam Lead

B42



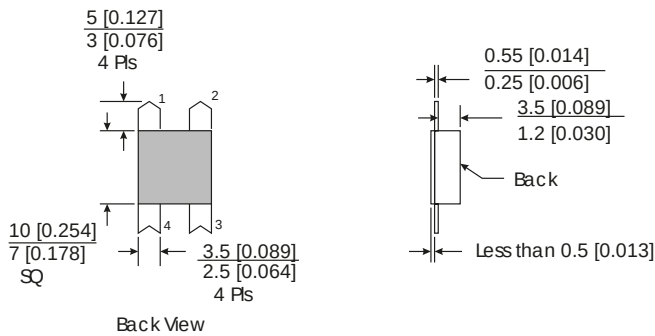
mils (mm)

B45



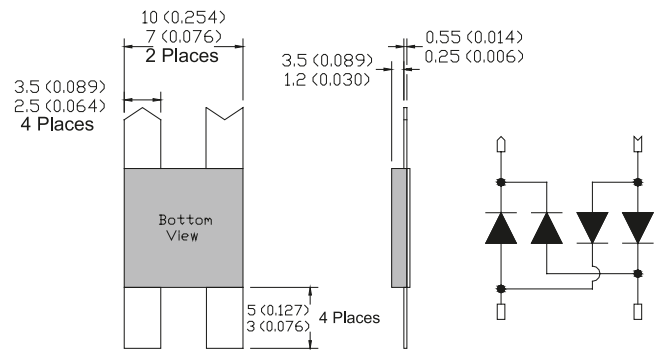
mils (mm)

B47



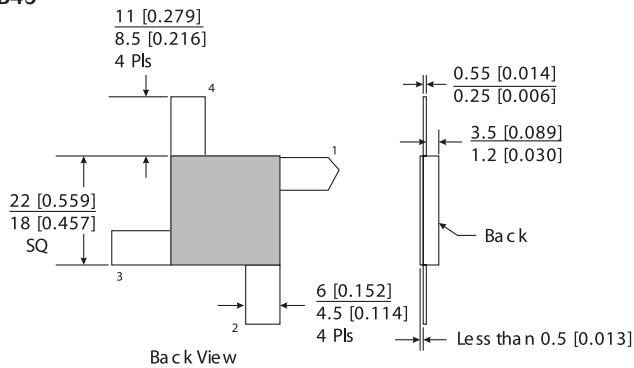
mils (mm)

B48



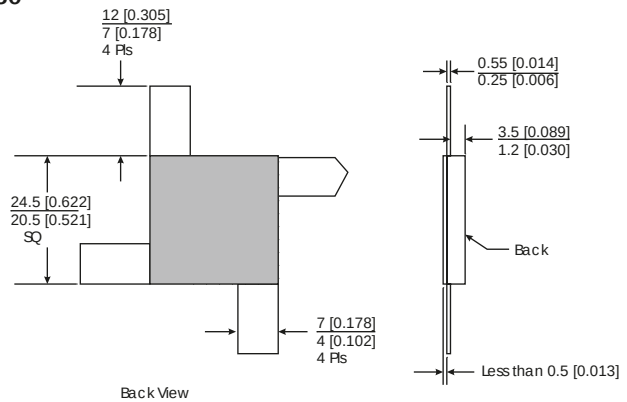
mils (mm)

B49



mils (mm)

B80

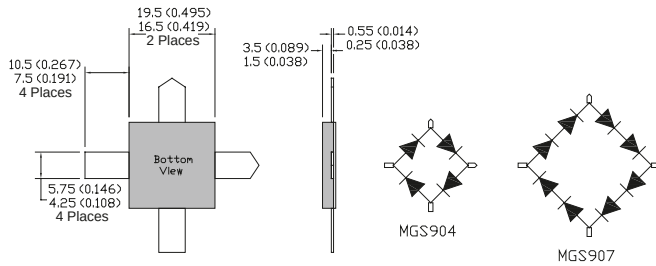


mils (mm)

Outline Drawings

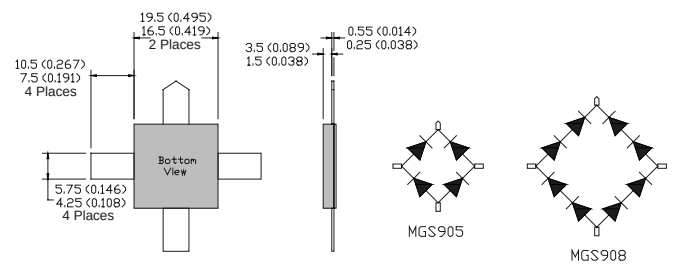
Beam Lead

B85



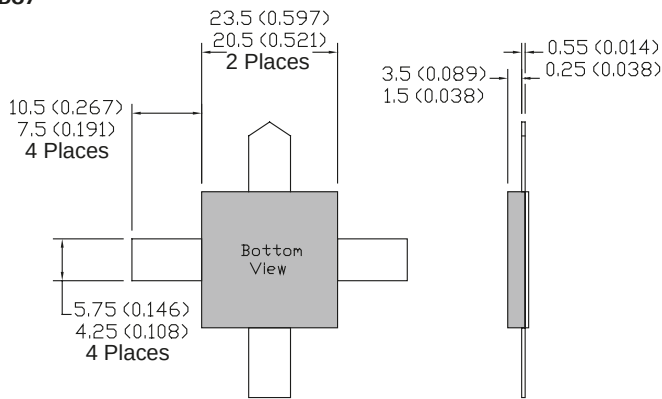
mils (mm)

B86



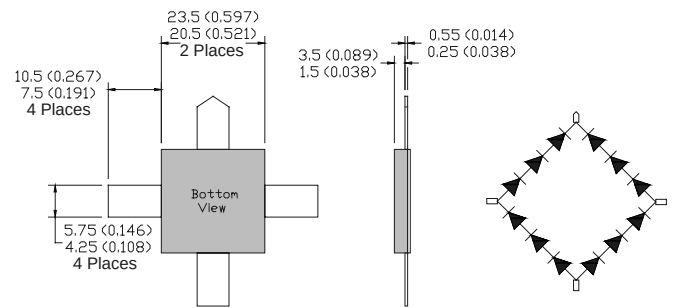
mils (mm)

B87



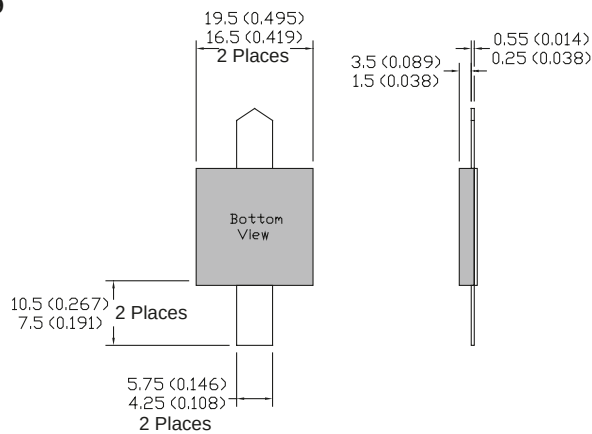
mils (mm)

B88



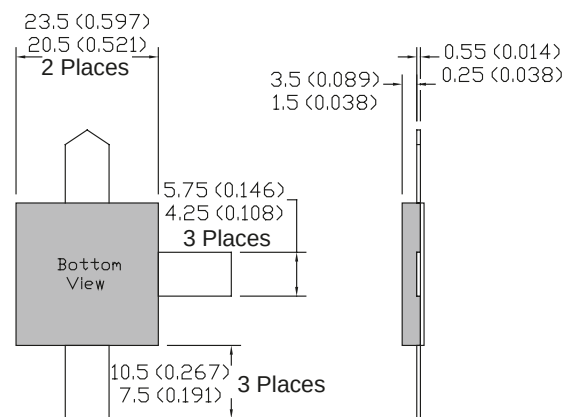
mils (mm)

B89



mils (mm)

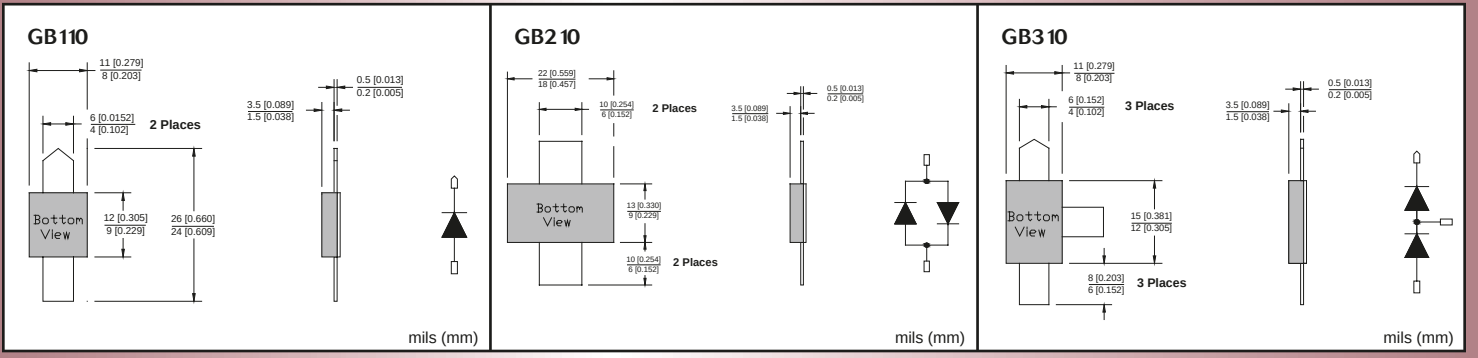
B90



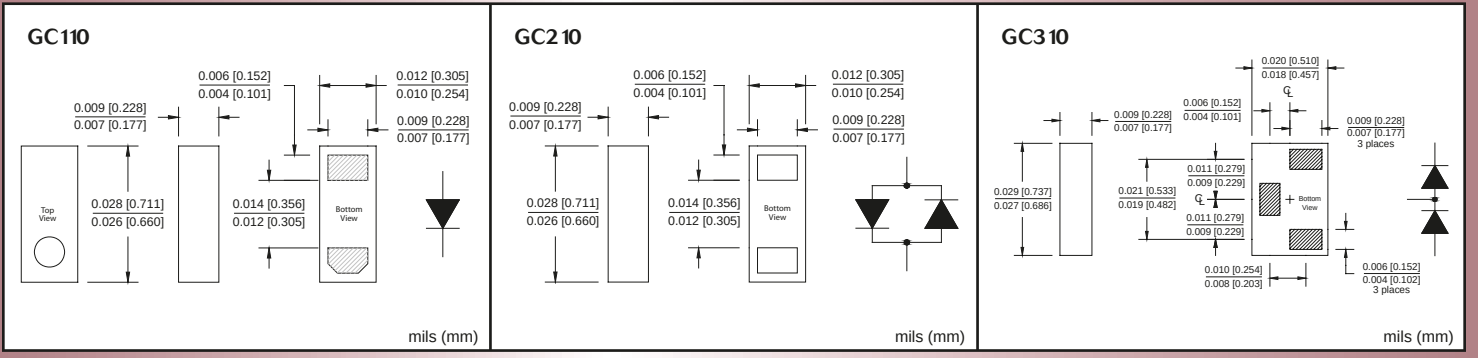
mils (mm)

Outline Drawings

Beam Lead



Flip Chip



Outline Drawings

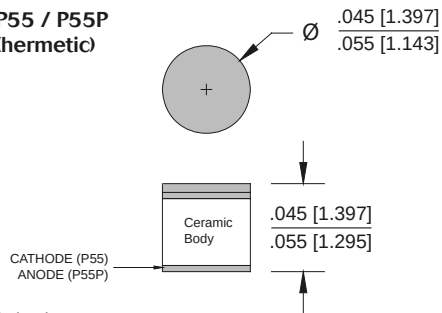
Chip

C11 / C12 ANODE (C11,C12) CATHODE (C11P,C12P) Ø 0.0009 (0.023) MIN. (C11,C11P) Ø 0.002 (0.051) MIN. (C12,C12P) 0.017 (0.432) 0.013 (0.330) 0.017 (0.432) 0.013 (0.330) 0.004 (0.102) 0.006 (0.152) CATHODE (C11,C12) ANODE (C11P,C12P) inches (mm)	C15 / C16 ANODE (C15,C16) CATHODE (C15P,C16P) Ø 0.0009 (0.023) MIN. Ø 0.002 (0.051) MIN. 0.017 (0.432) 0.013 (0.330) 0.017 (0.432) 0.013 (0.330) 0.004 (0.102) 0.006 (0.152) CATHODE (C15,C16) ANODE (C15P,C16) inches (mm)	C18 Bonding Pad 4 Pls 1 [0.025] Bond only on crosshatched area 16 [0.406] 14 [0.356] SQ. 6 [0.152] 4 [0.102] Back Contact mils (mm)
C20 11.2 [0.284] 2.8 [0.071] 4.4 [0.112] 2.2 [0.056] 5.4 [0.137] 21 [0.533] SQ. 19 [0.483] 7 [0.178] 3 [0.076] mils (mm)	C22 ANODE (C22) CATHODE (C22P) Ø 0.002 (0.050) MINIMUM 0.018 [0.965] 0.022 [0.558] 0.018 [0.965] 0.022 [0.558] 0.004 [0.101] 0.006 [0.101] CATHODE (C22) ANODE (C22P) inches (mm)	C26 ANODE (C26) CATHODE (C26P) Ø 0.003 (0.076) MIN. 0.008 (0.203) 0.012 (0.305) 0.008 (0.203) 0.012 (0.305) 0.004 (0.102) 0.006 (0.152) CATHODE (C26) ANODE (C26P) inches (mm)
C40 ANODE Ø 0.010 (0.254) MIN. 0.027 (0.686) 0.023 (0.584) 0.027 (0.686) 0.024 (0.584) 0.006 (0.152) 0.004 (0.102) CATHODE inches (mm)	C32 ANODE (C22) CATHODE (C22P) Ø 0.002 (0.050) MINIMUM 0.028 [0.711] 0.032 [0.813] 0.028 [0.711] 0.032 [0.813] 0.004 [0.101] 0.006 [0.152] CATHODE (C22) ANODE (C22P) inches (mm)	C37 0.035/0.039 Ø 0.020 MIN. 0.035/0.037 0.004/0.008 inches (mm)
C01A Ø 0.0015 [0.038] MIN. 0.012 [0.305] 0.008 [0.203] 0.012 [0.305] 0.008 [0.203] 0.006 [0.152] 0.004 [0.102] inches (mm)	C50 ANODE 0.047 (1.19) 0.043 (1.09) 0.022 (0.559) 0.018 (0.457) 0.003 (0.076) NOM. CATHODE 0.006 (0.152) 0.004 (0.102) inches (mm)	C51 ANODE 0.152 (3.86) 0.148 (3.76) Ø 0.142 (3.61) NOM. 0.022 (0.559) 0.018 (0.457) 0.003 (0.076) NOM. CATHODE 0.006 (0.152) 0.004 (0.102) inches (mm)

Outline Drawings

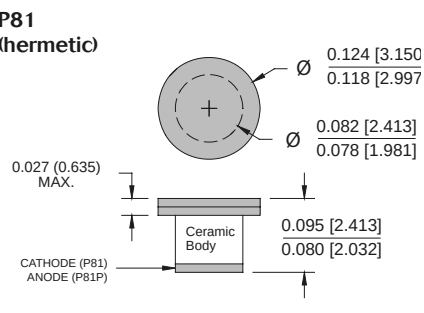
Coaxial

**P55 / P55P
(hermetic)**



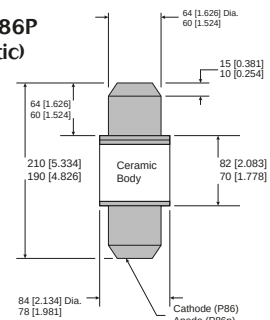
mils (mm)

**P81
(hermetic)**



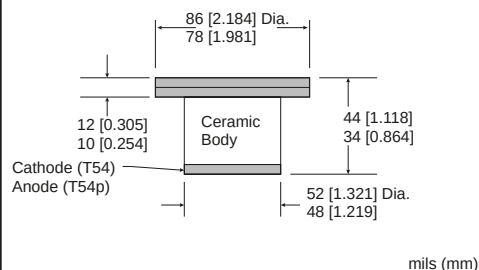
mils (mm)

**P86 / P86P
(hermetic)**



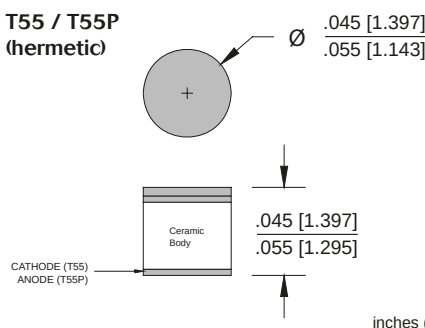
mils (mm)

**T54 / T54P
(hermetic)**



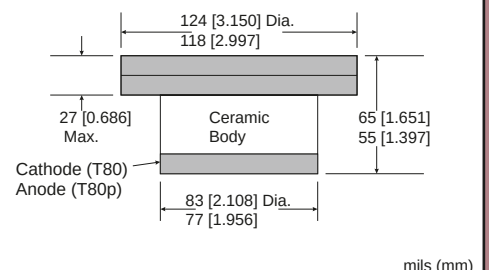
mils (mm)

**T55 / T55P
(hermetic)**



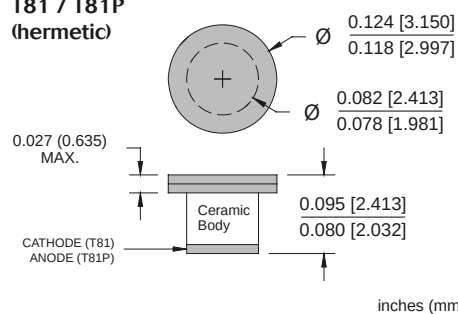
inches (mm)

**T80 / T80P
(hermetic)**



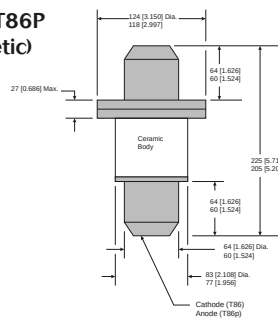
mils (mm)

**T81 / T81P
(hermetic)**



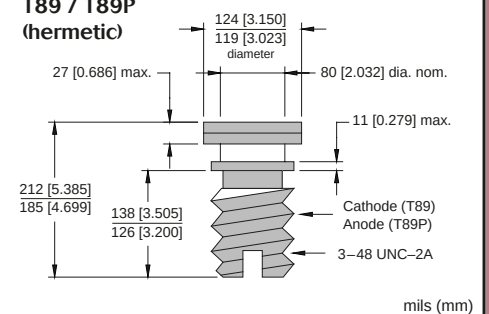
inches (mm)

**T86 / T86P
(hermetic)**



mils (mm)

**T89 / T89P
(hermetic)**

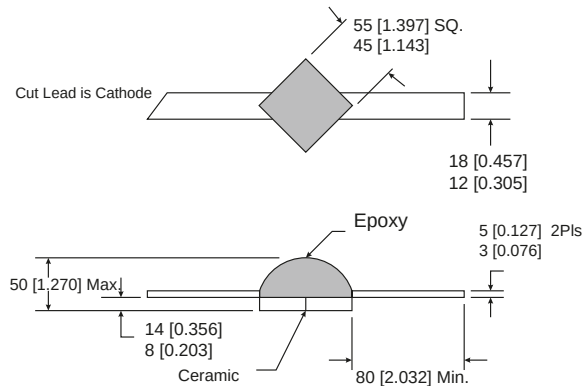


mils (mm)

Outline Drawings

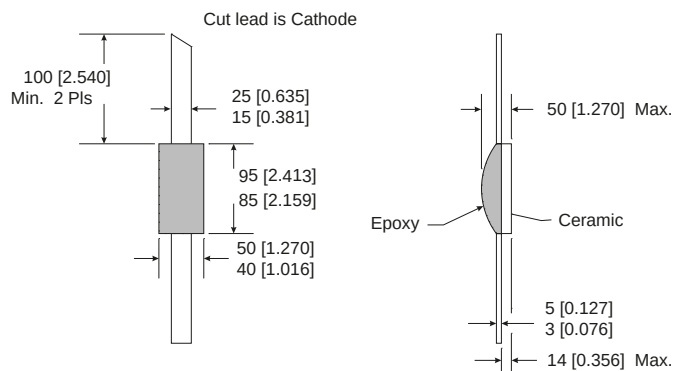
Epoxy

E25



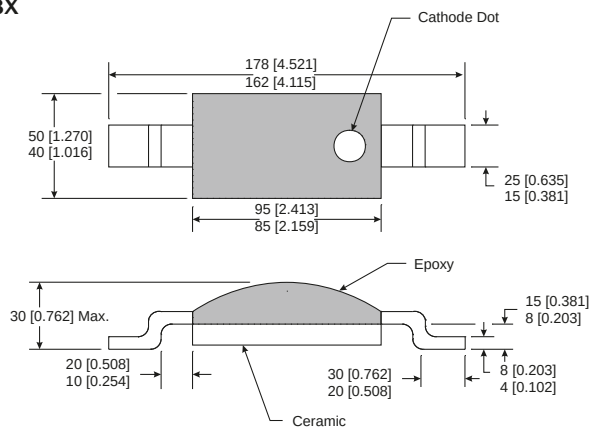
mils (mm)

E28



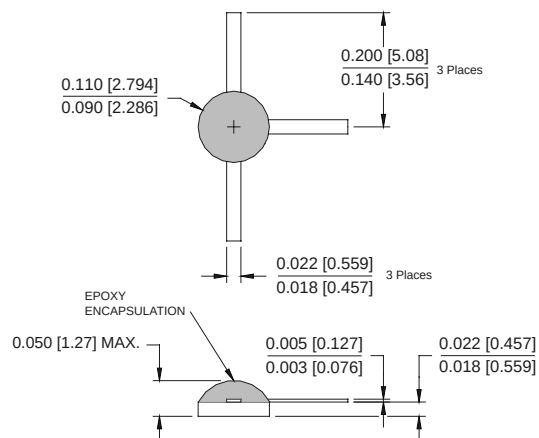
mils (mm)

E28X



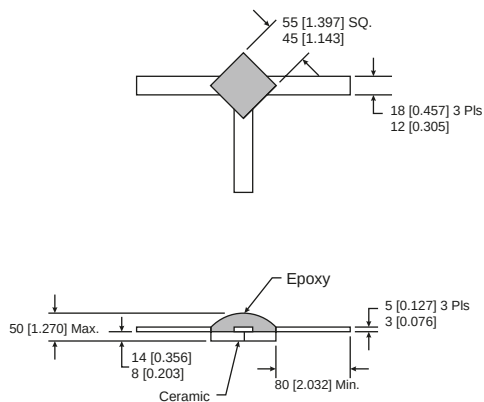
mils (mm)

E30



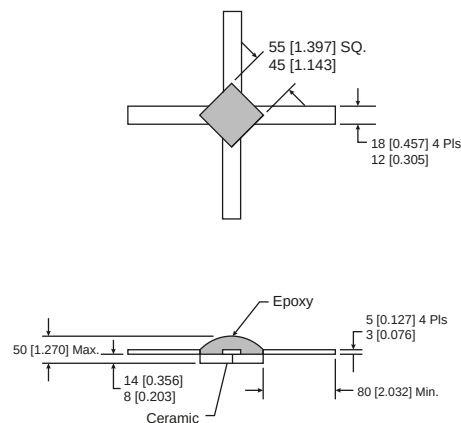
inches (mm)

E35



mils (mm)

E45

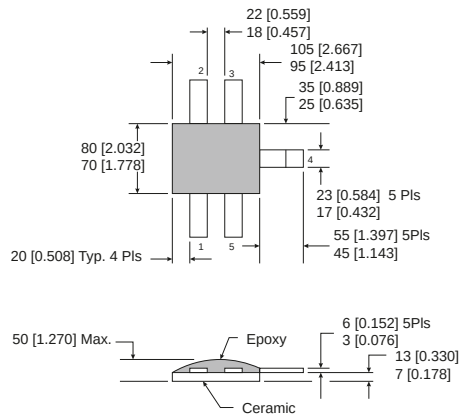


mils (mm)

Outline Drawings

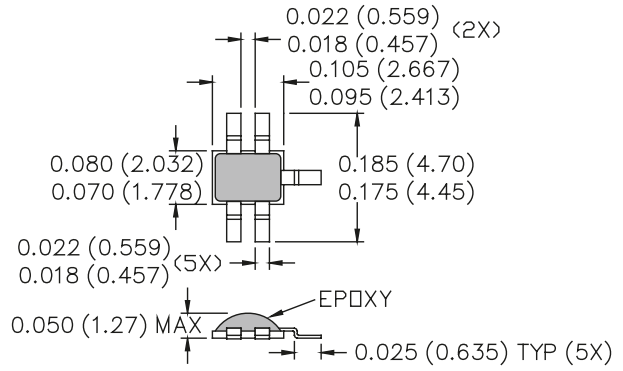
Epoxy

E50



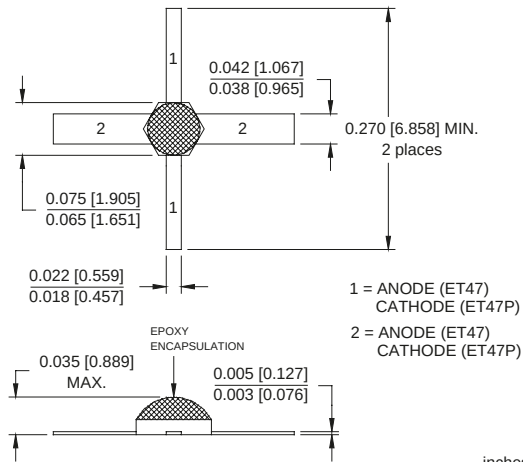
mils (mm)

E50SM



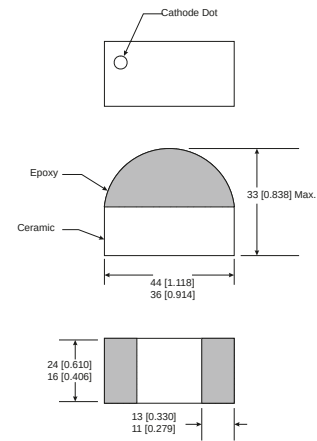
inches (mm)

ET47



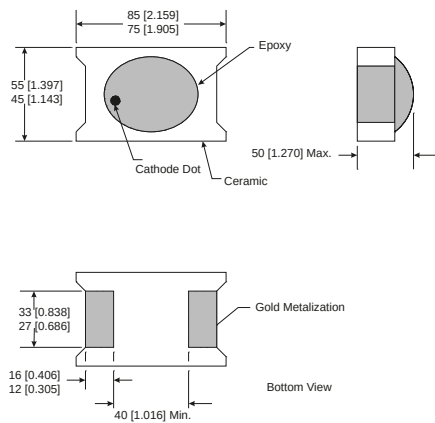
inches (mm)

0402



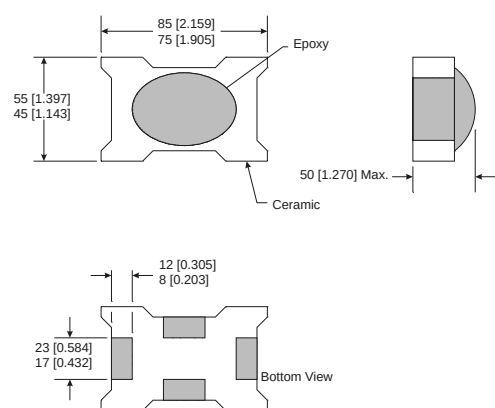
mils (mm)

0805-2



mils (mm)

0805-4

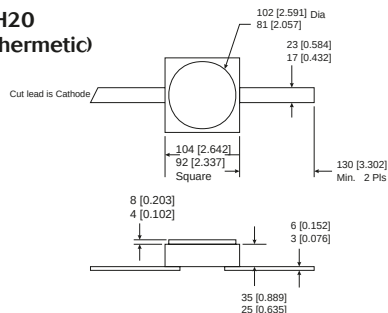


mils (mm)

Outline Drawings

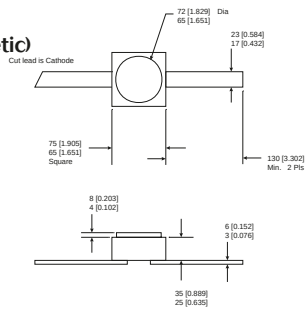
Hermetic

**H20
(hermetic)**



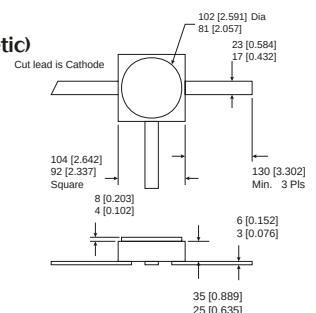
mils (mm)

**H27
(hermetic)**



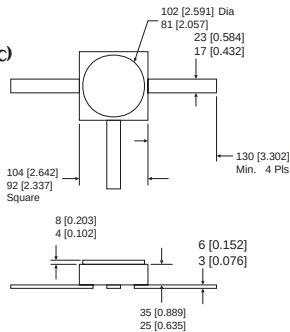
mils (mm)

**H30
(hermetic)**



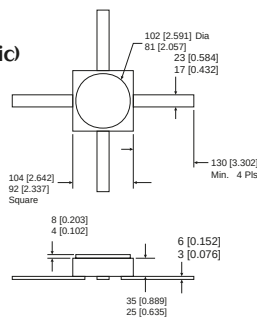
mils (mm)

**H30X
(hermetic)**



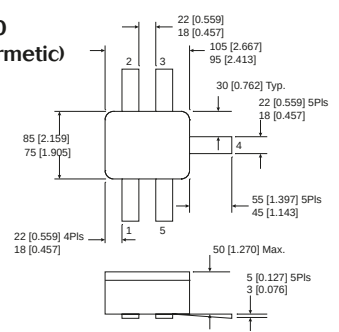
mils (mm)

**H40
(hermetic)**



mils (mm)

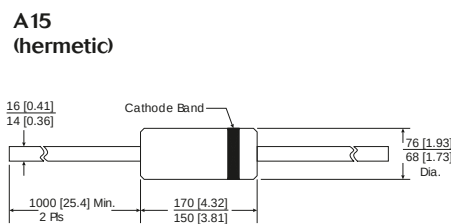
**H50
(hermetic)**



mils (mm)

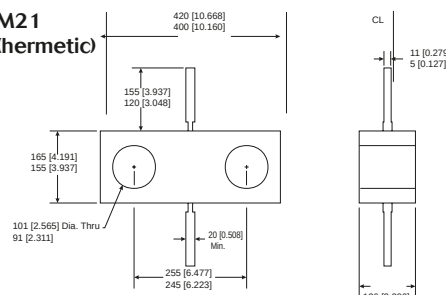
Misc

**A15
(hermetic)**



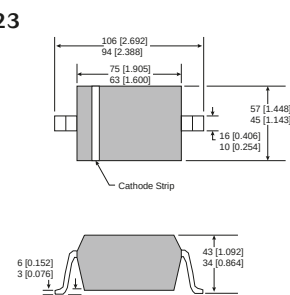
mils (mm)

**M21
(hermetic)**



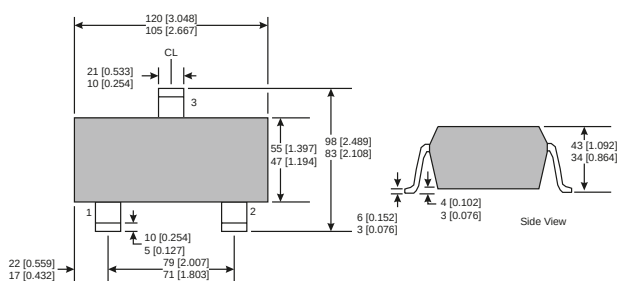
mils (mm)

SOD323



mils (mm)

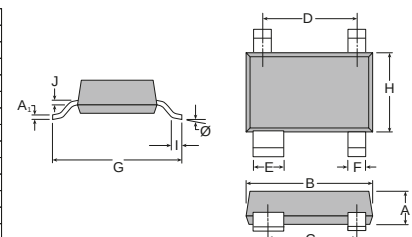
SOT23



mils (mm)

SOT143

	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.79	1.02	0.031	0.040
A ₁	0.02	0.10	0.001	0.004
B	2.67	3.05	0.105	0.120
C	1.78	2.03	0.070	0.080
D	1.80	2.00	0.071	0.079
E	0.77	0.94	0.030	0.037
F	0.38	0.54	0.015	0.021
G	2.10	2.50	0.083	0.098
H	1.20	1.40	0.047	0.065
I	0.13	0.25	0.005	0.010
J	0.89	0.15	0.0035	0.0059
Ø	0.0	8.0	0.0	0.8



Index

Part Number	Page	Part Number	Page	Part Number	Page
1N5719	31	MBD5057-T54	39	MGS903	18
1N5767	31	MBD5057-T80	39	MGS904	18
MBC50-1B12	42	MBP1030-B11	26	MGS904A	18
MBC50-2B12	42	MBP1033-B11	26	MGS905	18
MBC50-3B12	42	MBP1034-B11	26	MGS906	18
MBC50-4B12	42	MBP1035-B11	26	MGS907	18
MBC50-6B12	42	MBP1036-B11	26	MGS907A	18
MBC50-8B12	42	MBP2030-B11	26	MGS907B	18
MBC50-10B12	42	MBP2034-B11	26	MGS908	18
MBC50-15B12	42	MC2B0.8020-020	42	MGS909	18
MBC50-20B12	42	MC2B002020-020	42	MGS910	18
MBC50-33B13	42	MC2B004020-020	42	MGS911	18
MBC50-47B13	42	MC2B008020-020	42	MGS912	18
MBC50-68B13	42	MC2B016020-020	42	MGV050-18	19
MBC50-82B13	42	MC2DXXX010-010	40	MGV050-18-E28	19
MBC50-100B13	42	MC2DXXX015-015	40	MGV050-18-E28X	19
MBC50-0.2B14	42	MC2DXXX020-020	40	MGV050-18-H20	19
MBC50-1.0B14	42	MC2RXXX010-015	41	MGV050-18-0805-2	19
MBC50-1.5B14	42	MC2RXXX015-020	41	MGV050-20	19
MBC50-2.0B14	42	MC2RXXX015-032	41	MGV050-20-E28	19
MBD1057-C18	38	MC2RXXX022-042	41	MGV050-20-E28X	19
MBD1057-E28	39	MC2RXXX097-107	41	MGV050-20-H20	19
MBD1057-E28X	39	MC2RXXX099-138	41	MGV050-20-0805-2	19
MBD1057-H20	39	MC2RXXX127-145	41	MGV050-22	19
MBD1057-T54	39	MC2RXXX142-160	41	MGV050-22-E28	19
MBD1057-T80	39	MC2SXXX010-010	41	MGV050-22-E28X	19
MBD2057-C18	38	MC2SXXX011-011	41	MGV050-22-H20	19
MBD2057-E28	39	MC2SXXX015-015	41	MGV050-22-0805-2	19
MBD2057-E28X	39	MC2SXXX016-016	41	MGV050-24	19
MBD2057-H20	39	MC2SXXX020-020	41	MGV050-24-E28	19
MBD2057-T54	39	MC2SXXX022-022	41	MGV050-24-E28X	19
MBD2057-T80	39	MC2SXXX025-025	41	MGV050-24-H20	19
MBD3057-C18	38	MC2SXXX030-030	41	MGV050-24-0805-2	19
MBD3057-E28	39	MC2SXXX035-035	41	MGV050-26	19
MBD3057-E28X	39	MC2SXXX040-040	41	MGV050-26-E28	19
MBD3057-H20	39	MC2SXXX050-050	41	MGV050-26-E28X	19
MBD3057-T54	39	MC2SXXX055-055	41	MGV050-26-H20	19
MBD3057-T80	39	MC2SXXX060-060	41	MGV050-26-0805-2	19
MBD4057-C18	38	MC2SXXX070-070	41	MGV075-08	20
MBD4057-E28	39	MC2SXXX080-080	41	MGV075-09	20
MBD4057-E28X	39	MC2SXXX100-100	41	MGV075-10	20
MBD4057-H20	39	MGS801	18	MGV075-11	20
MBD4057-T54	39	MGS801A	18	MGV075-12	20
MBD4057-T80	39	MGS802	18	MGV075-13	20
MBD5057-C18	38	MGS802A	18	MGV075-14	20
MBD5057-E28	39	MGS803	18	MGV075-15	20
MBD5057-E28X	39	MGS901	18	MGV075-16	20
MBD5057-H20	39	MGS902	18	MGV075-17	20

Part Number	Page	Part Number	Page	Part Number	Page
MGV100-08	20	MMD830-H20	36	MNP0008-T89P	33
MGV100-09	20	MMD830-T86	36	MNP0010	33
MGV100-20	20	MMD830-0805-2	36	MNP0010-ET47P	33
MGV100-21	20	MMD832-C11	35	MNP0010-T54P	33
MGV100-22	20	MMD832-E28	36	MNP0010-T55P	33
MGV100-23	20	MMD832-E28X	36	MNP0010-T89P	33
MGV100-24	20	MMD832-H20	36	MNP0012	33
MGV100-25	20	MMD832-T86	36	MNP0012-ET47P	33
MGV100-26	20	MMD832-0805-2	36	MNP0012-T54P	33
MGV100-27	20	MMD835-C11	35	MNP0012-T55P	33
MGV125-08	20	MMD835-E28	36	MNP0012-T89P	33
MGV125-09	20	MMD835-E28X	36	MNP0012A	33
MGV125-20	20	MMD835-H20	36	MNP0012A-ET47P	33
MGV125-21	20	MMD835-T86	36	MNP0012A-T54P	33
MGV125-22	20	MMD835-0805-2	36	MNP0012A-T55P	33
MGV125-23	20	MMD837-C11	35	MNP0012A-T89P	33
MGV125-24	20	MMD837-E28	36	MNP0014	33
MGV125-25	20	MMD837-E28X	36	MNP0014-ET47P	33
MGV125-26	20	MMD837-H27	36	MNP0014-T54P	33
MMD0151	35	MMD837-T86	36	MNP0014-T55P	33
MMD0153	35	MMD837-0805-2	36	MNP0014-T89P	33
MMD0803	35	MMD840-C11	35	MNP0014A	33
MMD0815	35	MMD840-E28	36	MPN3001	31
MMD0825	35	MMD840-E28X	36	MPN3002	31
MMD0833	35	MMD840-H27	36	MPN3080	31
MMD0840	35	MMD840-T86	36	MPN3081	31
MMD805-C12	35	MMD840-0805-2	36	MPN4165	31
MMD805-E28	36	MMDB30-B11	35	MPN4166	31
MMD805-E28X	36	MMDB30-E28	36	MPN7302	26
MMD805-H20	36	MMDB30-E28X	36	MPN7302-E28	27
MMD805-T86	36	MMDB30-0402	36	MPN7302-E28X	27
MMD805-T89	36	MMDB30-0805-2	36	MPN7302-H20	27
MMD805-0805-2	36	MMDB35-B11	35	MPN7302-0805-2	27
MMD810-C12	35	MMDB35-E28	36	MPN7304	26
MMD810-E28	36	MMDB35-E28X	36	MPN7304-E28	27
MMD810-E28X	36	MMDB35-0402	36	MPN7304-E28X	27
MMD810-H20	36	MMDB35-0805-2	36	MPN7304-H20	27
MMD810-T86	36	MMDB45-B11	35	MPN7304-0805-2	27
MMD810-T89	36	MMDB45-E28	36	MPN7304A	26
MMD820-C12	35	MMDB45-E28X	36	MPN7304A-E28	27
MMD820-E28	36	MMDB45-0402	36	MPN7304A-E28X	27
MMD820-E28X	36	MMDB45-0805-2	36	MPN7304A-H20	27
MMD820-H20	36	MMPN-080045	29	MPN7304A-0805-2	27
MMD820-T86	36	MMPN-080150	29	MPN7306	26
MMD820-0805-2	36	MNP0008	33	MPN7306-E28	27
MMD830-C11	35	MNP0008-ET47P	33	MPN7306-E28X	27
MMD830-E28	36	MNP0008-T54P	33	MPN7306-H20	27
MMD830-E28X	36	MNP0008-T55P	33	MPN7306-0805-2	27

Index

Part Number	Page	Part Number	Page	Part Number	Page
MPN7310	26	MPN7620-ET47	28	MSS20,051-E25	5
MPN7310-E28	27	MPN7620-T55	28	MSS20,051-H27	5
MPN7310-E28X	27	MPN7630	28	MSS20,051-T86	5
MPN7310-H20	27	MPN7630-ET47	28	MSS20,051-0805-2	5
MPN7310-0805-2	27	MPN7630-T55	28	MSS20,054-C15	4
MPN7310A	26	MPN7640	28	MSS20,054-E25	5
MPN7310A-E28	27	MPN7640-ET47	28	MSS20,054-H27	5
MPN7310A-E28X	27	MPN7640-T55	28	MSS20,054-T86	5
MPN7310A-H20	27	MPN7650	28	MSS20,054-0805-2	5
MPN7310A-0805-2	27	MPN7650-ET47	28	MSS20,055-C15	4
MPN7312A	26	MPN7650-T55	28	MSS20,055-E25	5
MPN7312A-E28	27	MPN7660	28	MSS20,055-H27	5
MPN7312A-E28X	27	MPN7660-T55	28	MSS20,055-T86	5
MPN7312A-H20	27	MPN7660A	28	MSS20,055-0805-2	5
MPN7312A-0805-2	27	MPN7660A-T55	28	MSS20,140-B10D	4
MPN7312B	26	MPN7670	28	MSS20,140-0402	5
MPN7312B-E28	27	MPN7670-T55	28	MSS20,141-B10D	4
MPN7312B-E28X	27	MPND4005-B15	26	MSS20,141-0402	5
MPN7312B-H20	27	MPND4005-B16	26	MSS20,142-B10D	4
MPN7312B-0805-2	27	MPND4005-0402	26	MSS20,142-0402	5
MPN7315	26	MSPD1000-E50	43	MSS20,143-B10D	4
MPN7315-E28	27	MSPD1000-E50SM	43	MSS20,143-0402	5
MPN7315-E28X	27	MSPD1000-H50	43	MSS20,145-B10D	4
MPN7315-H20	27	MSPD1002-E50	43	MSS20,145-0402	5
MPN7315-0805-2	27	MSPD1002-E50SM	43	MSS20,146-B10D	4
MPN7320	26	MSPD1002-H50	43	MSS20,146-0402	5
MPN7320-E28	27	MSPD1012-E50	43	MSS30,046-C15	8
MPN7320-E28X	27	MSPD1012-E50SM	43	MSS30,046-P55	9
MPN7320-H20	27	MSPD1012-H50	43	MSS30,046-P86	9
MPN7320-0805-2	27	MSPD2018-E50	43	MSS30,050-C15	8
MPN7330	30	MSPD2018-E50SM	43	MSS30,050-P55	9
MPN7345	30	MSPD2018-H50	43	MSS30,050-P86	9
MPN7360	30	MSS20,046-C15	4	MSS30,142-B10B	8
MPN7370	30	MSS20,046-E25	5	MSS30,142-E25	9
MPN7380	30	MSS20,046-H27	5	MSS30,142-H20	9
MPN73100	30	MSS20,046-T86	5	MSS30,148-B10B	8
MPN73120	30	MSS20,046-0805-2	5	MSS30,148-E25	9
MPN7420	30	MSS20,047-C15	4	MSS30,148-H20	9
MPN7453A	30	MSS20,047-E25	5	MSS30,154-B10B	8
MPN7453B	30	MSS20,047-H27	5	MSS30,154-E25	9
MPN7453C	30	MSS20,047-T86	5	MSS30,154-H20	9
MPN7610	28	MSS20,047-0805-2	5	MSS30,242-B20	8
MPN7610-ET47	28	MSS20,050-C15	4	MSS30,242-E35	9
MPN7610-T55	28	MSS20,050-E25	5	MSS30,242-H30	9
MPN7610A	28	MSS20,050-H27	5	MSS30,248-B20	8
MPN7610A-ET47	28	MSS20,050-T86	5	MSS30,248-E35	9
MPN7610A-T55	28	MSS20,050-0805-2	5	MSS30,248-H30	9
MPN7620	28	MSS20,051-C15	4	MSS30,254-B20	8

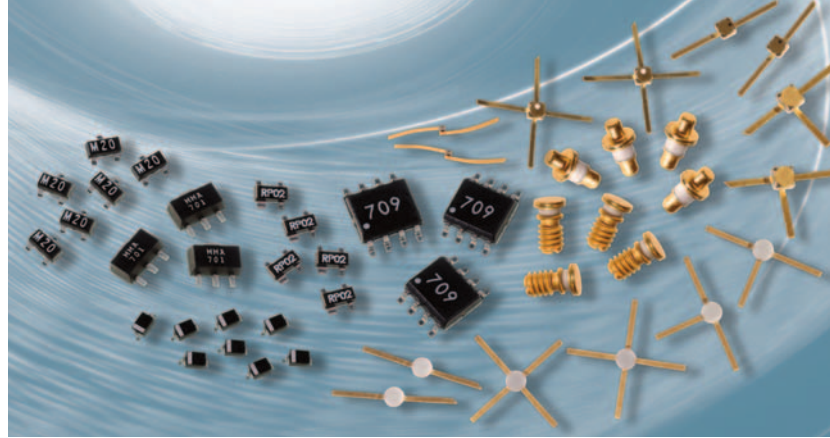
Part Number	Page	Part Number	Page	Part Number	Page
MSS30,254-E35	9	MSS39,148-0805-2	7	MSS40,PCB46-B48	10
MSS30,254-H30	9	MSS39,152-E25	7	MSS40,PCR53-B47	10
MSS30,346-B21	8	MSS39,152-H20	7	MSS40,CR53-H40	11
MSS30,346-E25	9	MSS39,152-0402	7	MSS50,048-C15	12
MSS30,346-H20	9	MSS39,152-0805-2	7	MSS50,048-P55	13
MSS30,442-B42	8	MSS40,045-C15	10	MSS50,048-P86	13
MSS30,442-E45	9	MSS40,045-P55	11	MSS50,062-C16	12
MSS30,442-H40	9	MSS40,045-P86	11	MSS50,062-P55	13
MSS30,448-B42	8	MSS40,048-C15	10	MSS50,062-P86	13
MSS30,448-E45	9	MSS40,048-P55	11	MSS50,146-B10B	12
MSS30,448-H40	9	MSS40,048-P86	11	MSS50,146-E25	13
MSS30,454-B40	8	MSS40,141-B10B	10	MSS50,146-H20	13
MSS30,454-E45	9	MSS40,141-E25	11	MSS50,146-0402	13
MSS30,454-H40	9	MSS40,141-H20	11	MSS50,146-0805-2	13
MSS30,B46-B45	8	MSS40,141-0402	11	MSS50,155-B10B	12
MSS30,B46-E45	9	MSS40,148-B10B	10	MSS50,155-E25	13
MSS30,B46-H40	9	MSS40,148-E25	11	MSS50,155-H20	13
MSS30,B53-B45	8	MSS40,148-H20	11	MSS50,155-0402	13
MSS30,B53-E45	9	MSS40,148-0402	11	MSS50,155-0805-2	13
MSS30,B53-H40	9	MSS40,155-B10B	10	MSS50,244-B20	12
MSS30,CR46-B49	8	MSS40,155-E25	11	MSS50,244-E35	13
MSS30,CR46-E45	9	MSS40,155-H20	11	MSS50,244-H30	13
MSS30,CR46-H40	9	MSS40,155-0402	11	MSS50,244-0805-4	13
MSS30,CR53-B49	8	MSS40,244-B20	10	MSS50,341-B21	12
MSS30,CR53-E45	9	MSS40,244-E35	11	MSS50,341-E25	13
MSS30,CR53-H40	9	MSS40,244-0805-4	11	MSS50,341-H20	13
MSS30,PCB46-B48	8	MSS40,248-B20	10	MSS50,448-B40	12
MSS30,PCR46-B47	8	MSS40,248-E35	11	MSS50,448-E45	13
MSS30,PCR53-B47	8	MSS40,248-0805-4	11	MSS50,448-H40	13
MSS39,045-C15	6	MSS40,255-B20	10	MSS50,448-0805-4	13
MSS39,048-C15	6	MSS40,255-E35	11	MSS50,B46-B45	12
MSS39,144-B10B	6	MSS40,255-0805-4	11	MSS50,B46-E45	13
MSS39,146-B10B	6	MSS40,448-B42	10	MSS50,B46-H40	13
MSS39,148-B10B	6	MSS40,448-E45	11	MSS50,B53-B45	12
MSS39,152-B10B	6	MSS40,448-H40	11	MSS50,B53-E45	13
MSS39,045-P55	7	MSS40,455-B40	10	MSS50,B53-H40	13
MSS39,045-P86	7	MSS40,455-E45	11	MSS50,CR46-B49	12
MSS39,048-P55	7	MSS40,455-H40	11	MSS50,CR46-E45	13
MSS39,048-P86	7	MSS40,B46-B45	10	MSS50,CR46-H40	13
MSS39,144-H27	7	MSS40,B46-E45	11	MSS50,CR53-B49	12
MSS39,144-0402	7	MSS40,B53-B45	10	MSS50,CR53-E45	13
MSS39,144-0805-2	7	MSS40,B53-E45	11	MSS50,CR53-H40	13
MSS39,146-H27	7	MSS40,CR46-B49	10	MSS50,PCB46-B48	12
MSS39,146-0402	7	MSS40,CR46-E45	11	MSS50,PCR46-B47	12
MSS39,146-0805-2	7	MSS40,CR46-H40	11	MSS50,PCR53-B48	12
MSS39,148-E25	7	MSS40,CR53-B49	10	MSS60,144-B10B	14
MSS39,148-H20	7	MSS40,CR53-E45	11	MSS60,144-E25	15
MSS39,148-0402	7	MSS40,PCR46-B47	10	MSS60,144-H20	15

Index

Part Number	Page	Part Number	Page	Part Number	Page
MSS60,148-B10B	14	MSV34,060-E28X	22	MSV38,060-E28X	23
MSS60,148-E25	15	MSV34,060-H20	22	MSV38,060-H20	23
MSS60,148-H20	15	MSV34,060-T86	22	MSV38,060-T86	23
MSS60,153-B10B	14	MSV34,060-0805-2	22	MSV38,060-0805-2	23
MSS60,153-E25	15	MSV34,064-C12	21	MSV38,064-C12	21
MSS60,153-H20	15	MSV34,064-E28	22	MSV38,064-E28	23
MSS60,244-B20	14	MSV34,064-E28X	22	MSV38,064-E28X	23
MSS60,244-E35	15	MSV34,064-H20	22	MSV38,064-H20	23
MSS60,244-H30	15	MSV34,064-T86	22	MSV38,064-T86	23
MSS60,248-B20	14	MSV34,064-0805-2	22	MSV38,064-0805-2	23
MSS60,248-E35	15	MSV34,067-C12	21	MSV38,067-C12	21
MSS60,248-H30	15	MSV34,067-E28	22	MSV38,067-E28	23
MSS60,253-B20	14	MSV34,067-E28X	22	MSV38,067-E28X	23
MSS60,253-E35	15	MSV34,067-H20	22	MSV38,067-H20	23
MSS60,253-H30	15	MSV34,067-T86	22	MSV38,067-T86	23
MSS60,444-B42	14	MSV34,067-0805-2	22	MSV38,067-0805-2	23
MSS60,444-E45	15	MSV34,069-C12	21	MSV38,069-C12	21
MSS60,444-H40	15	MSV34,069-E28	22	MSV38,069-E28	23
MSS60,448-B42	14	MSV34,069-E28X	22	MSV38,069-E28X	23
MSS60,448-E45	15	MSV34,069-H20	22	MSV38,069-H20	23
MSS60,448-H40	15	MSV34,069-T86	22	MSV38,069-T86	23
MSS60,453-B41	14	MSV34,069-0805-2	22	MSV38,069-0805-2	23
MSS60,453-E45	15	MSV34,075-C12	21	MSV38,075-C12	21
MSS60,453-H40	15	MSV34,075-E28	22	MSV38,075-E28	23
MSS60,841-B80	14	MSV34,075-E28X	22	MSV38,075-E28X	23
MSS60,841-E45	15	MSV34,075-H20	22	MSV38,075-H20	23
MSS60,841-H40	15	MSV34,075-T86	22	MSV38,075-T86	23
MSS60,846-B80	14	MSV34,075-0805-2	22	MSV38,075-0805-2	23
MSS60,846-E45	15	MSV34,082-C12	21	MSV38,082-C12	21
MSS60,846-H40	15	MSV34,082-E28	22	MSV38,082-E28	23
MSS60,848-B80	14	MSV34,082-E28X	22	MSV38,082-E28X	23
MSS60,848-E45	15	MSV34,082-H20	22	MSV38,082-H20	23
MSS60,848-H40	15	MSV34,082-T86	22	MSV38,082-T86	23
MSS60,B46-B45	14	MSV34,082-0805-2	22	MSV38,082-0805-2	23
MSS60,B46-E45	15	MSV34,087-C12	21	MSV38,087-C12	21
MSS60,B46-H40	15	MSV34,087-E28	22	MSV38,087-E28	23
MSS60,B53-B45	14	MSV34,087-E28X	22	MSV38,087-E28X	23
MSS60,B53-E45	15	MSV34,087-H20	22	MSV38,087-H20	23
MSS60,B53-H40	15	MSV34,087-T86	22	MSV38,087-T86	23
MSS60,CR46-B49	14	MSV34,087-0805-2	22	MSV38,087-0805-2	23
MSS60,CR46-E45	15	MSV34,092-C22	21	MSV38,092-C22	21
MSS60,CR53-B49	14	MSV34,092-E28	22	MSV38,092-E28	23
MSS60,CR53-E45	15	MSV34,092-E28X	22	MSV38,092-E28X	23
MSS60,PCB46-B48	14	MSV34,092-H20	22	MSV38,092-H20	23
MSS60,PCR46-B47	14	MSV34,092-T86	22	MSV38,092-T86	23
MSS60,PCR53-B47	14	MSV34,092-0805-2	22	MSV38,092-0805-2	23
MSV34,060-C12	21	MSV38,060-C12	21	MSV40,060-C12	21
MSV34,060-E28	22	MSV38,060-E28	23	MSV40,060-E28	24

Part Number	Page	Part Number	Page	Part Number	Page
MSV40,060-E28X	24	SMMD805-SOD323	37	SMSRQ1500-SOT143	17
MSV40,060-H20	24	SMMD805-SOT23-0S	37	SMSCQ2500-SOT143	17
MSV40,060-T86	24	SMMD805-SOT23-1S	37	SMSRQ2500-SOT143	17
MSV40,060-0805-2	24	SMMD810-SOD323	37	SMSCQ4500-SOT143	17
MSV40,064-C12	21	SMMD810-SOT23-0S	37	SMSRQ4500-SOT143	17
MSV40,064-E28	24	SMMD810-SOT23-1S	37	SMSCQ5500-SOT143	17
MSV40,064-E28X	24	SMMD820-SOD323	37	SMSRQ5500-SOT143	17
MSV40,064-H20	24	SMMD820-SOT23-0S	37	SMTD3001-SOD323	25
MSV40,064-T86	24	SMMD820-SOT23-1S	37	SMTD3002-SOD323	25
MSV40,064-0805-2	24	SMMD830-SOD323	37	SMTD3004-SOD323	25
MSV40,067-C12	21	SMMD830-SOT23-XXX	37	SMTD3006-SOD323	25
MSV40,067-E28	24	SMMD832-SOT23-XXX	37	SMTD3008-SOD323	25
MSV40,067-E28X	24	SMMD835-SOT23-XXX	37	SMTD3010-SOD323	25
MSV40,067-H20	24	SMMD837-SOT23-XXX	37	SMVT3001-SOT23	25
MSV40,067-T86	24	SMMD840-SOT23-XXX	37	SMVT3002-SOT23	25
MSV40,067-0805-2	24	SMMD832-SOD323	37	SMVT3004-SOT23	25
MSV40,069-C12	21	SMMD835-SOD323	37	SMVT3006-SOT23	25
MSV40,069-E28	24	SMMD837-SOD323	37	SMVT3008-SOT23	25
MSV40,069-E28X	24	SMMD840-SOD323	37	SMVT3010-SOT23	25
MSV40,069-H20	24	SMPN7310-SOD323	32		
MSV40,069-T86	24	SMPN7310-SOT23-XXX	32		
MSV40,069-0805-2	24	SMPN7316-SOD323	32		
MSV40,075-C12	21	SMPN7316-SOT23-XXX	32		
MSV40,075-E28	24	SMPN7320-SOD323	32		
MSV40,075-E28X	24	SMPN7320-SOT23-XXX	32		
MSV40,075-H20	24	SMPN7335-SOD323	32		
MSV40,075-T86	24	SMPN7335-SOT23-XXX	32		
MSV40,075-0805-2	24	SMPN7380-SOT23-XXX	32		
MSV40,082-C12	21	SMPN7380-SOD323	32		
MSV40,082-E28	24	SMPN7453-SOT23-XXX	32		
MSV40,082-E28X	24	SMPN7453-SOD323	32		
MSV40,082-H20	24	SMSD3004-SOD323	16		
MSV40,082-T86	24	SMSD3012-SOD323	16		
MSV40,082-0805-2	24	SMSD4004-SOD323	16		
MSV40,087-C12	21	SMSD4012-SOD323	16		
MSV40,087-E28	24	SMSD6004-SOD323	16		
MSV40,087-E28X	24	SMSD6012-SOD323	16		
MSV40,087-H20	24	SMSP3004-SOT143	17		
MSV40,087-T86	24	SMSP3012-SOT143	17		
MSV40,087-0805-2	24	SMST3004-SOT23	16		
MSV40,092-C22	21	SMST3012-SOT23	16		
MSV40,092-E28	24	SMST4004-SOT23	16		
MSV40,092-E28X	24	SMST4012-SOT23	16		
MSV40,092-H20	24	SMST6004-SOT23	16		
MSV40,092-T86	24	SMST6012-SOT23	16		
MSV40,092-0805-2	24	SMSCQ1200-SOT143	17		
SMAP3004-SOT143	17	SMSRQ1200-SOT143	17		
SMAP3012-SOT143	17	SMSCQ1500-SOT143	17		

In addition to our Microwave diodes and capacitors, we manufacture a comprehensive line of innovative, high-performance InGaP HBT amplifiers. All are available in industry standard packages for efficient, low cost improvements of your current designs. We also offer customized, application specific solutions at catalog prices.



PERRY JOHNSON
REGISTRARS, INC.

ISO 9001: 2000